

Semiconductor detector technology for medical and scientific imaging: Quantum processing and Medipix developments in particular



ERIK H.M. HEIJNE

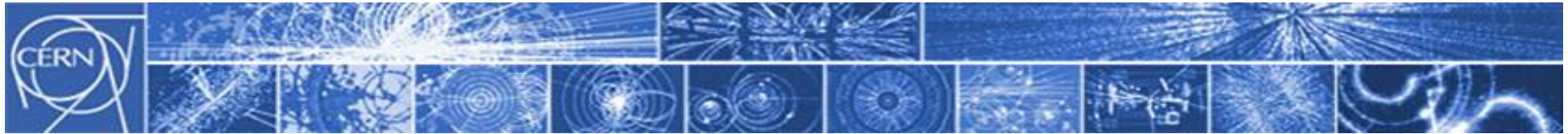


ICFA - EU INFIERI School



Oxford 13 July 2013





Particle physics generates new instrumentation

Silicon microstrip detectors since 1980 replaced
bubble chambers for tracking and vertexing

Heijne NIM 178 (1980) 331, Kemmer IEEE NS-29 (1982) 733

True 2-D pixels much more useful for general imaging

Damerell NIM 185 (1981) 33

In 1987 my 'dream' was the Si 'Micropattern' detector:
not only data acquisition,
but also on-chip information processing

Heijne NIM A273 (1988) 615 (London Conf 1987)

Continuous Issue:
what must be on-chip, what can be off-line?



strong point
in particle physics detectors:
we deal with single quanta

single quantum imaging is hardly known today

move beyond cell structure
towards molecular & atomic level



Si Technology

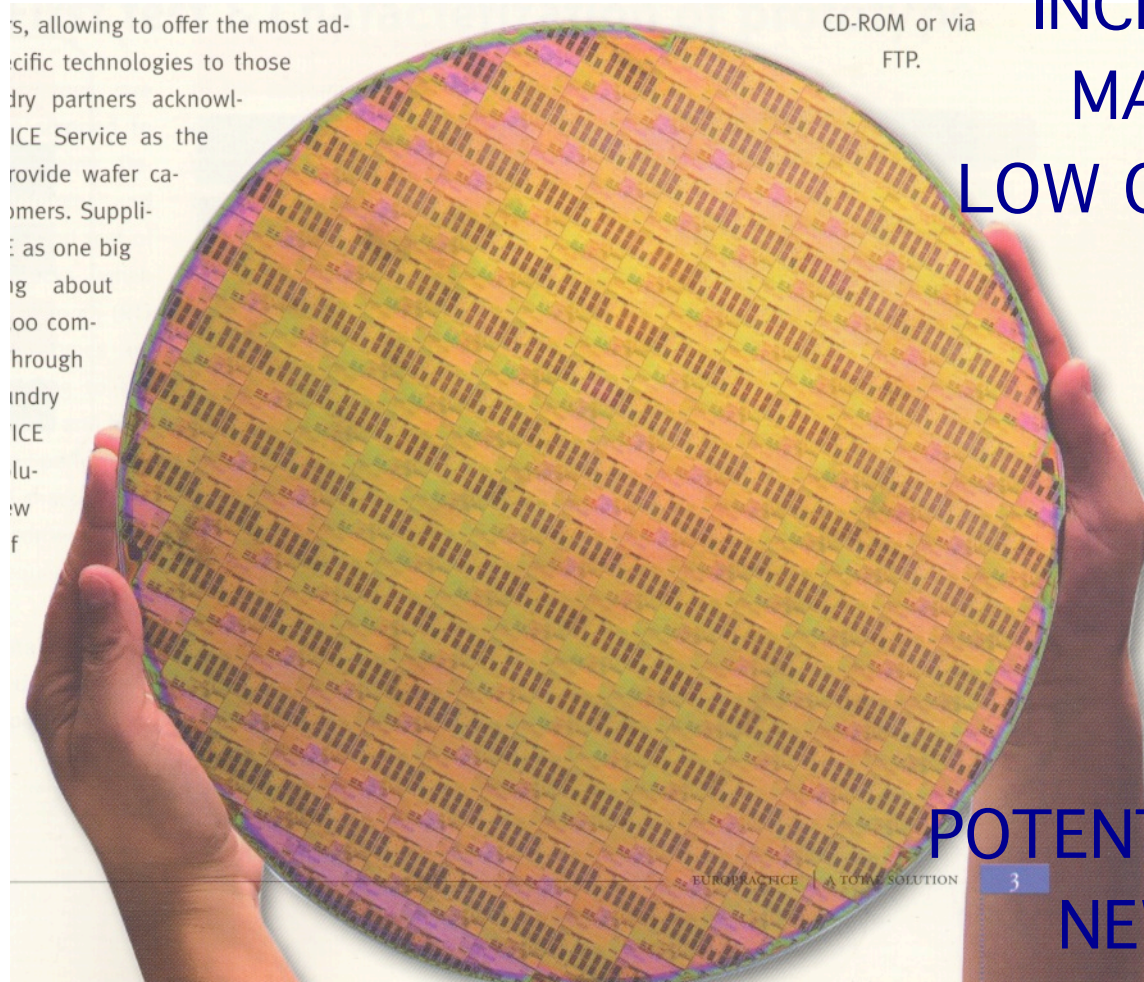


SILICON WAFER MANUFACTURING

s, allowing to offer the most ad-
specific technologies to those
dry partners acknowl-
ICE Service as the
provide wafer ca-
omers. Suppli-
as one big
ig about
oo com-
hrough
ndry
ICE
lu-
w
f

CD-ROM or via
FTP.

INCREASE OF WAFER SIZE
MANY CHIPS PER WAFER
LOW COST IN HIGH VOLUME
SYSTEM INTEGRATION



BUT ALSO:
POTENTIAL FOR COMPLEXITY
NEW MODES OF IMAGING

Si CHIP FOUNDRY

FIND OUT HOW THIS CAN BE USED
for RADIATION IMAGING APPLICATIONS

TYPICAL INVESTMENT 3B\$

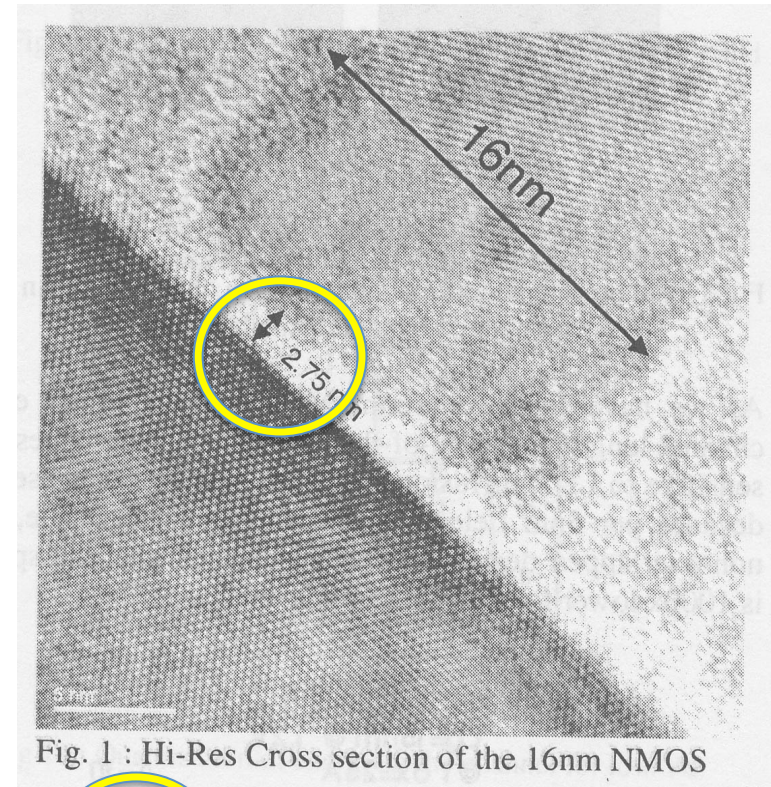
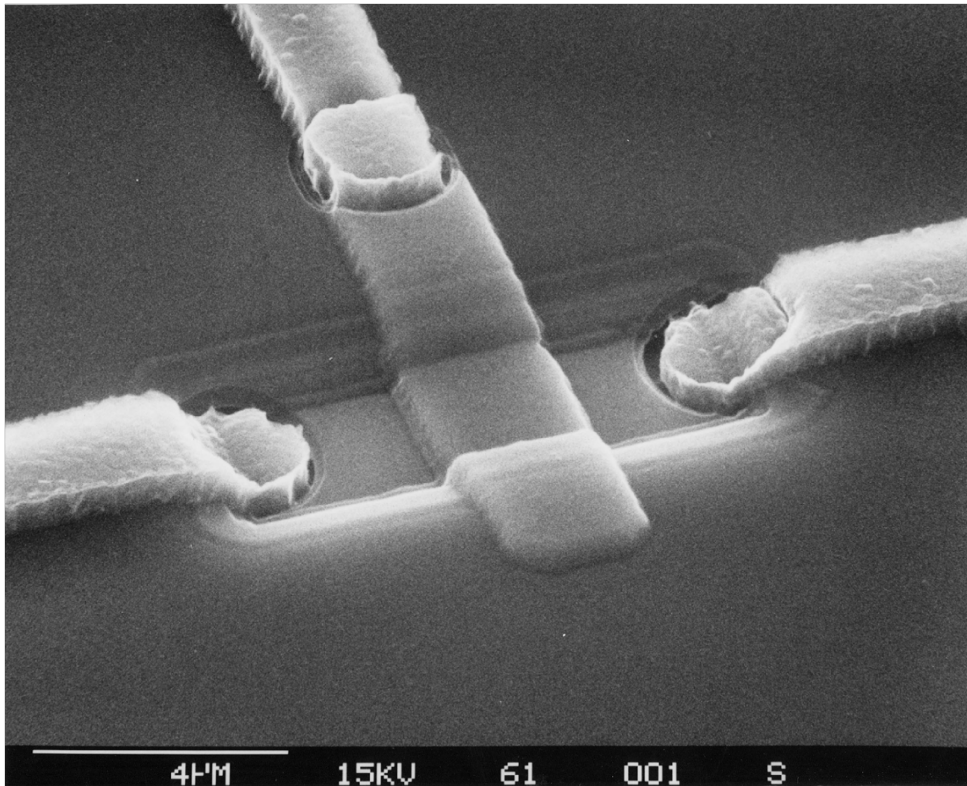
DAILY PRODUCTION
1000-3000 WAFERS
TURNOVER 10M\$ / DAY

July 2013

6



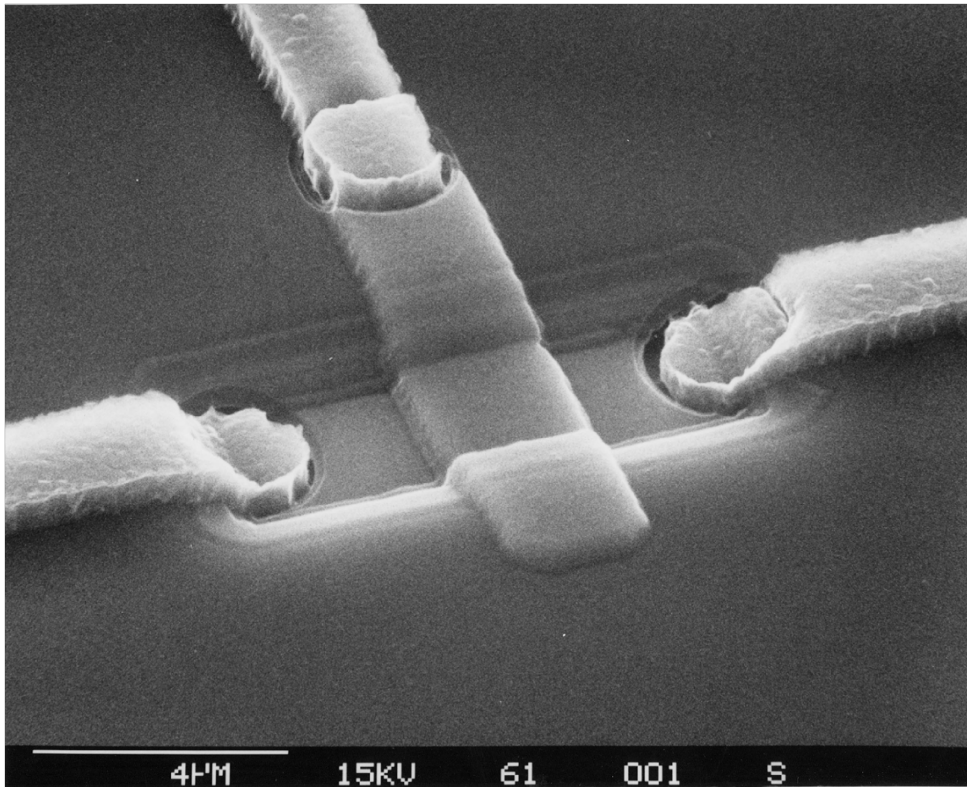
SILICON MOS TRANSISTOR



2 μm TECHNOLOGY

SiO_2 gate 2.75 nm
0.016 μm

SILICON MOS TRANSISTOR



CORRECT SCALE



SiO_2 gate 2.75 nm

2 μm TECHNOLOGY

0.016 μm

SOI TRANSISTOR LETI

LETI-SOITEC 3.4

SOI TRANSISTOR 18 nm
+ EPITAXIAL Si GROWTH

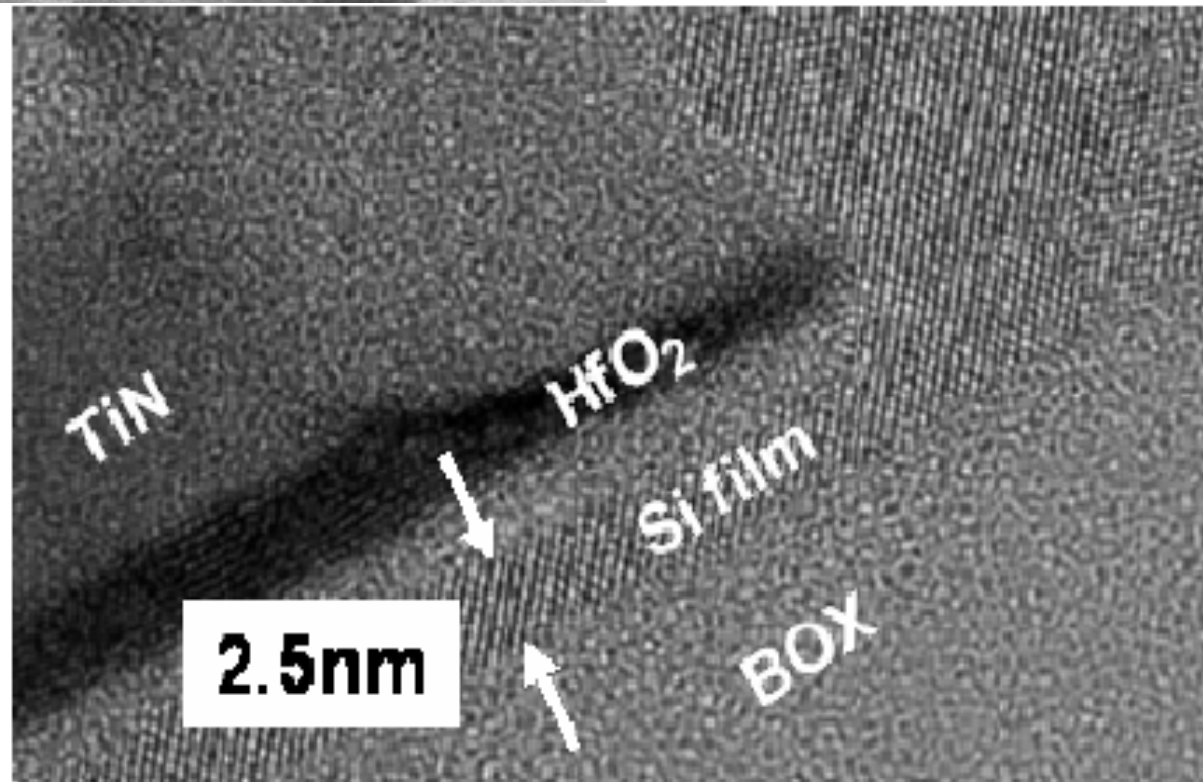
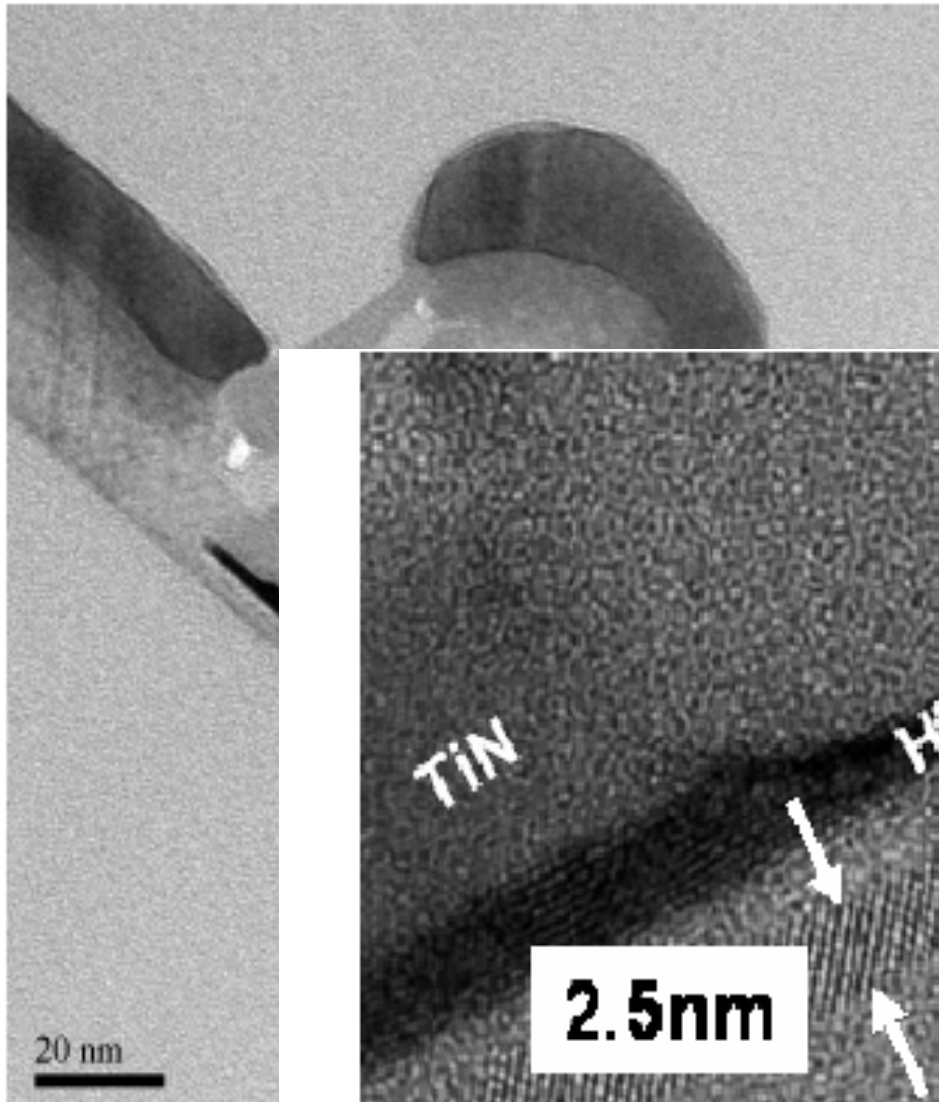


Fig. 1- TEM cross section of

Fig. 2- HRTEM cross-section showing the detail of the channel edge. The Si film thickness is 2.5nm.

FinFET TRANSISTOR

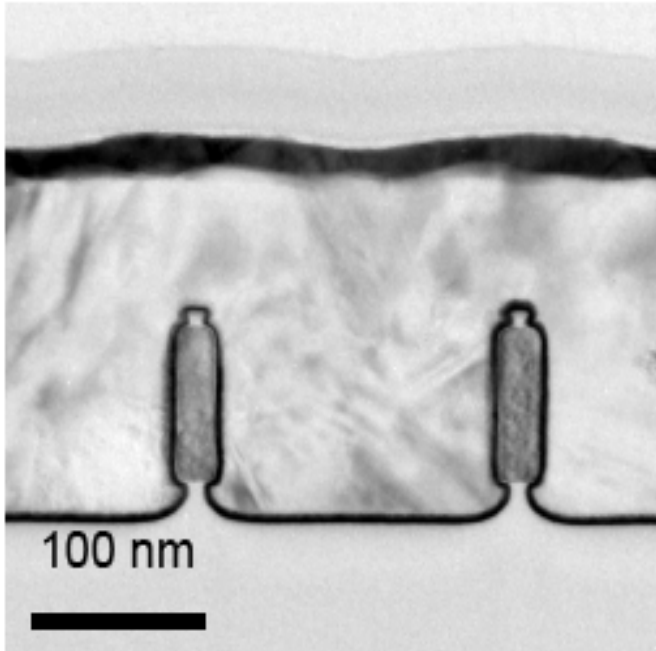


Fig 9. 20 nm FinFETs processed with similar gate dielectric and having $T_{inv}=1.4$ nm with Si(110) orientation.

SEMATECH
paper 3.3

HIGH k and METAL-GATE

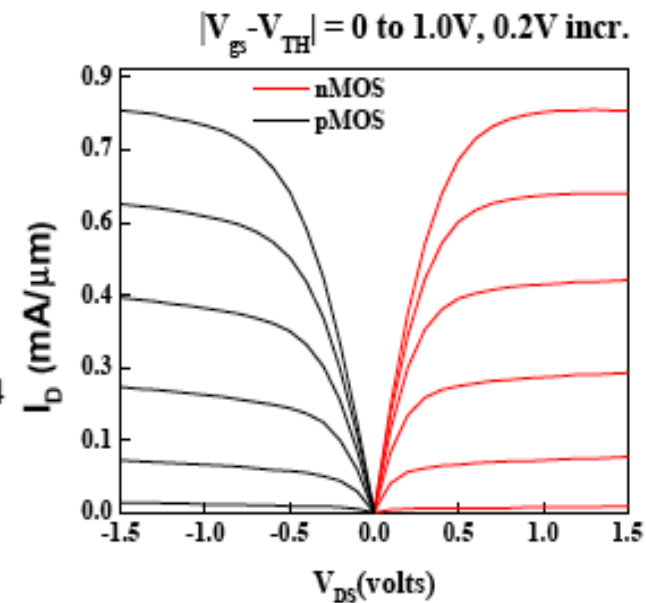


Fig 10. The Si(110) FinFETs ($W_{Fin}=20$ nm and $L_{Drawn}=80$ nm) with high k / metal gate show the same symmetric performance as the planar devices. Short Channel effects are improved due to the intrinsic doping of the channel.

MOORE's TREND for SAMSUNG DRAM

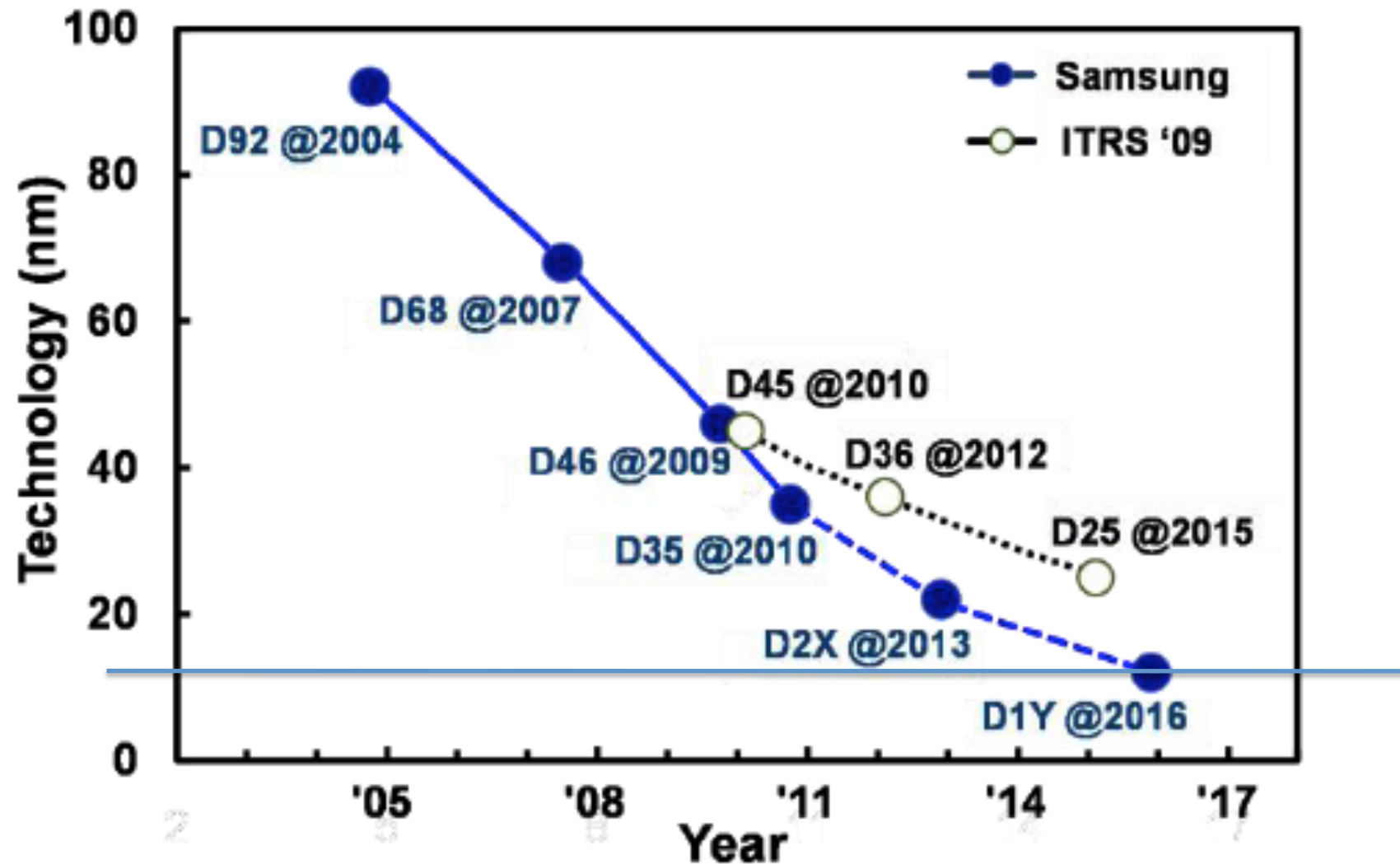


Fig. 1 ITRS & Samsung DRAM technology roadmap

Kinam KIM

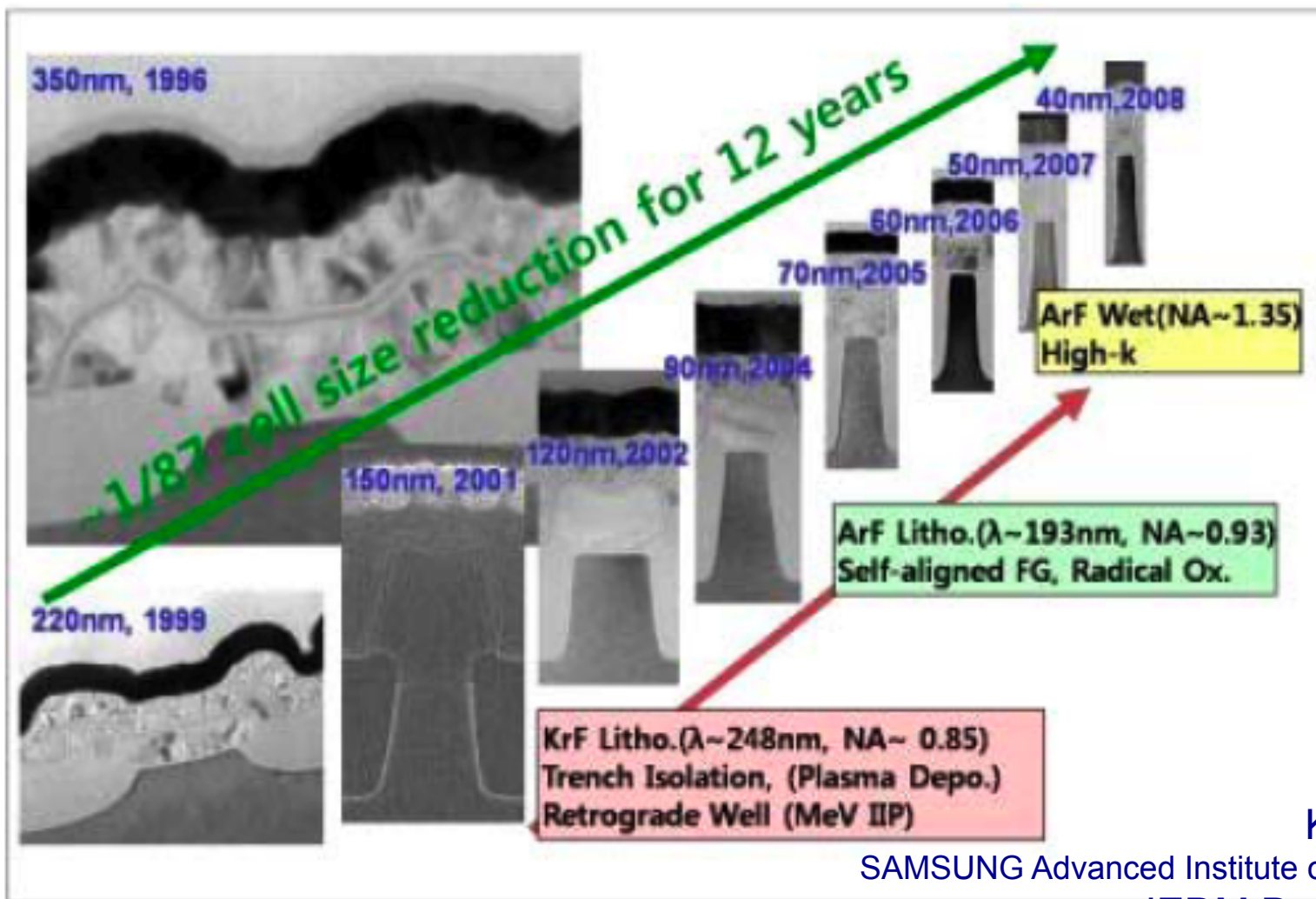
SAMSUNG Advanced Institute of Technology

IEDM Dec 2010 1.1



Erik HEIJNE

TREND in NAND cell 1999-2008



Kinam KIM

SAMSUNG Advanced Institute of Technology

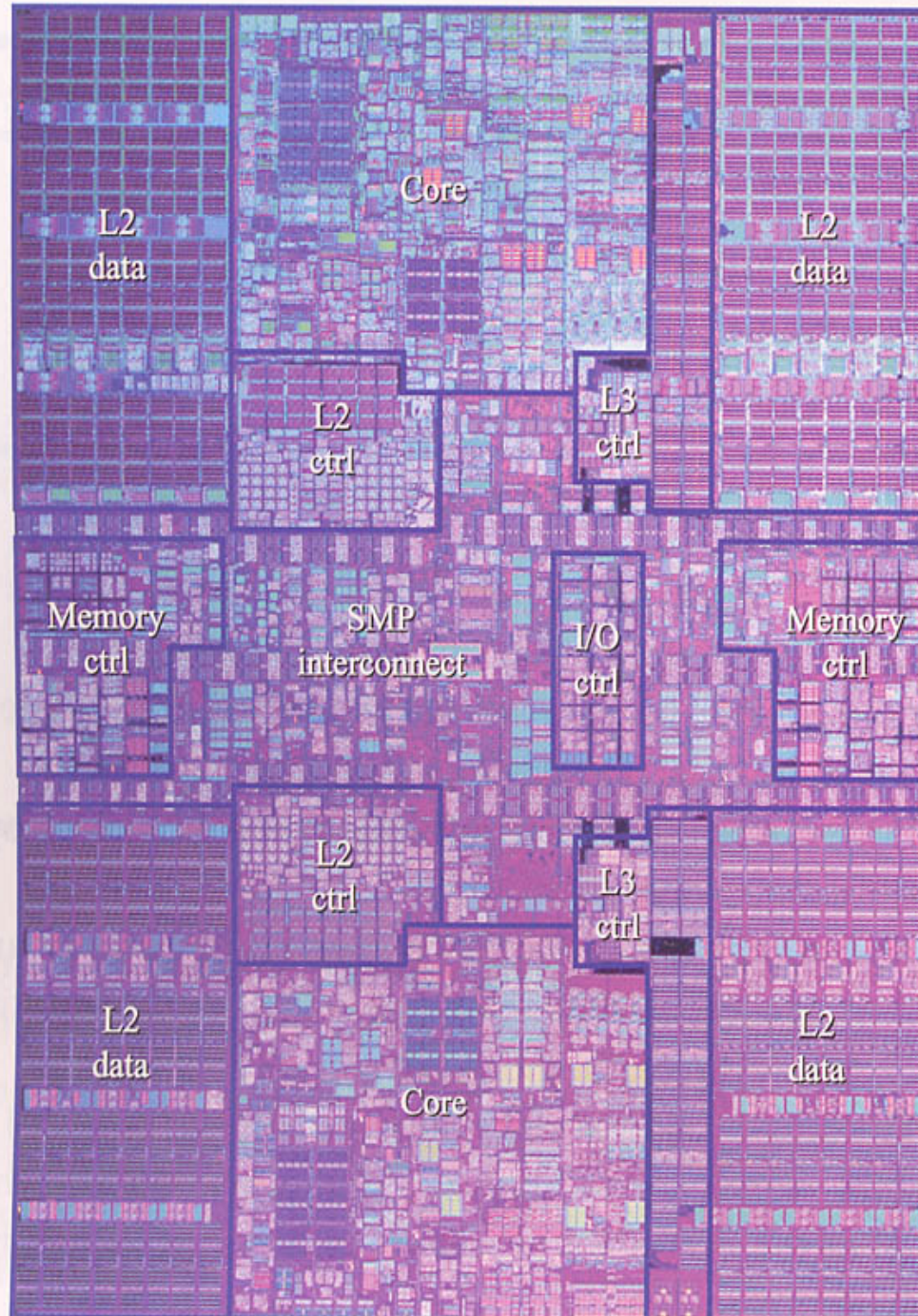
IEDM Dec 2010 1.1

Fig. 3 NAND cell dimensional scaling and related technology evolution

SYSTEM CHIPS



IBM POWER6



DUAL CORE > 4 GHz

0.065 μm SOI n 40nm, p 35 nm

dual gate oxide 1.12 , 2.35 nm

4 V_T levels

10 levels Cu low-k dielectric

pitch 200 nm, 175 nm thick

e-fuse

341 mm², ~16 mm x 21.3 mm

790 M transistors most at 1.15 V

I/O 1953 signal+test, 5399 power

D 64kb + I 96kb L1 in cores

2x2 4Mb L2 (+ 32Mb L3 off-chip)

64 bit, 800 MHz memory access

ERROR RECOVERY

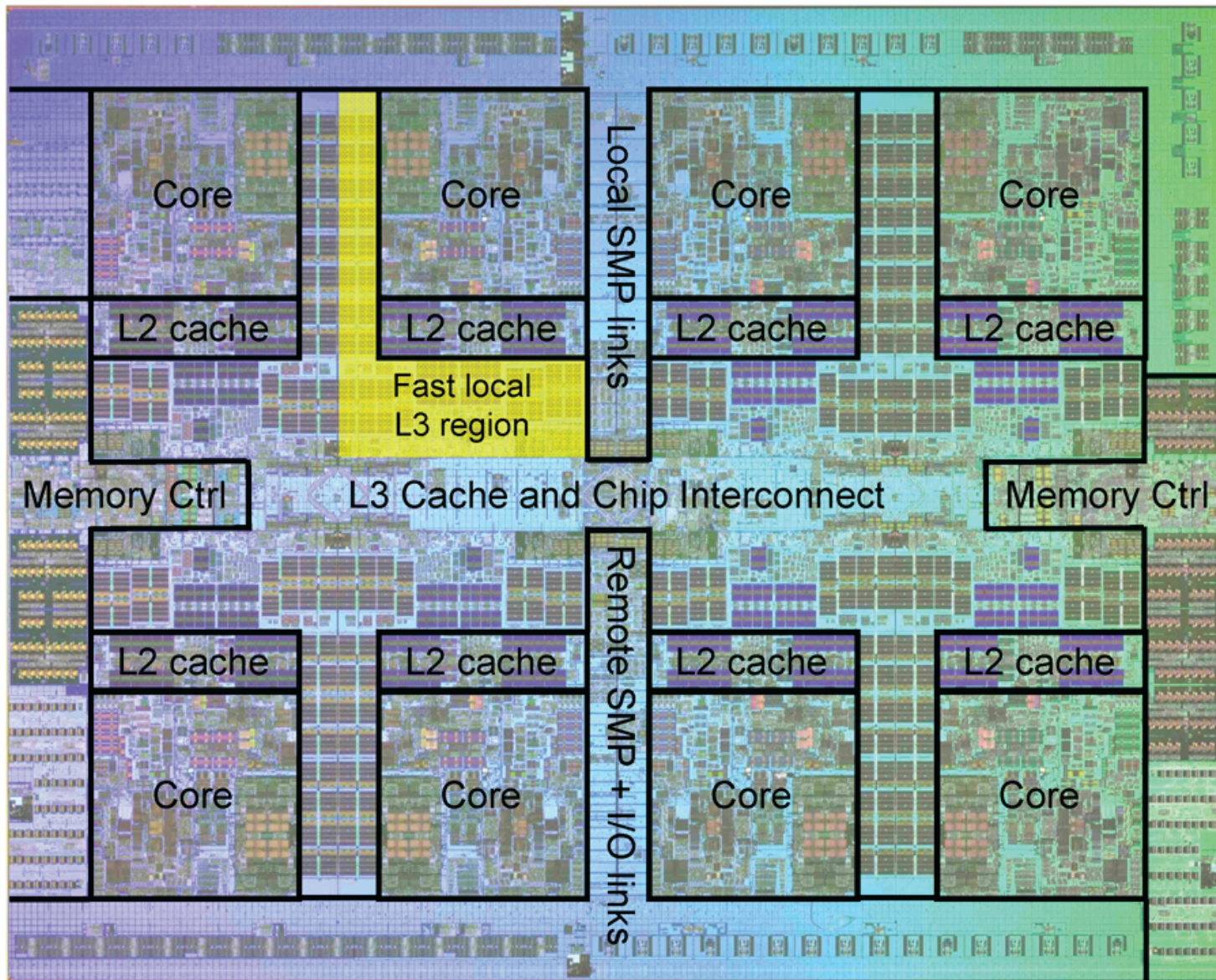
CHECK POINT RETRY

PHOTO of REAL DIE

IBM POWER7

5.67 cm²
1200 M transistors
8 Core Processor
45 nm SOI-CMOS

internal L3 cache
5nm SOI-CMOS



DIE PHOTO

ERROR RECOVERY
CHECK POINT RETRY

PIXEL DETECTORS at CERN INVENTED 1986

HIGH INTENSITY EXPERIMENTS

e.g. HEAVY IONS (Omega ion experiments) and FUTURE LHC

THE MEDIPIX2/3 SYSTEM for X-RAYS

MICROELECTRONICS, Si SENSORS & ASSEMBLY

CHIP DESIGN CERN: Michael Campbell, Xavier Llopart, Rafael Ballabriga

READOUT CARDS & SOFTWARE several Institutes: Pisa, Napoli, NIKHEF, IEAP-CTU (Pixelman), ESRF, Diamond-UK, ...

MEASUREMENTS with OTHER RADIATION QUANTA

DIFFERENT SENSORS (Si, CdTe, GaAs, diamond, gas,...)

DIFFERENT RADIATION ELECTRONS, NEUTRONS, PROTONS, IONS,
VISIBLE LIGHT (gas, +MCP)

MANY DIFFERENT APPLICATIONS in Science and Industry



BASICS of a DETECTOR

SIGNAL if there is PARTICLE

→ DETECTION EFFICIENCY

NO SIGNAL if NO PARTICLE

MUCH MORE DIFFICULT

TAKE ONLY 'GOOD' PARTICLE

EVEN MORE WORK ON TRIGGER CONDITIONS

MICROELECTRONICS and COMPUTERS
ENABLE NEW PARTICLE PHYSICS EXPERIMENTS



BASICS of a DETECTOR

SIGNAL if there is PARTICLE

→ DETECTION EFFICIENCY

usually close to 100%, BUT....

→ LOSSES CAN BE DUE TO

INSENSITIVE AREAS (FRAME, EDGE, DEAD WIRE, ..)

CRYSTAL BOUNDARY or DEFECT

WINDOW ABSORPTION (e.g. for low keV X-rays)

LOSS OF SIGNAL : TRAPS, BALLISTIC DEFICIT

INCLINED TRACKS

SIGNAL SHARING BETWEEN CELLS

PILE-UP/DEAD-TIME at HIGH RATE

OUT-OF-TIMING (for SYNCHRONOUS READOUT)

BOTTLE-NECKS in READOUT SYSTEM

(MEMORY OVERFLOW)

SOME REDUNDANCY is NEEDED

a few % CAN USUALLY BE TOLERATED

NOISE and RISETIME (τ_s 'speed') in PREAMPLIFIER

Series Noise: $ENC_d^2 \propto \frac{C_t^2}{g_m \tau_s}$ Capacitance, Speed

Parallel noise: $ENC_o^2 \propto I_o \tau_s$ Dark current I_0

Preamp rise time: $t_r \propto \frac{C_t}{g_m} \frac{(C_L + C_f)}{C_f}$

In general C_t should be as low as possible and g_m high, but more g_m implies more power

from Michael CAMPBELL
see also Seminar Ratti

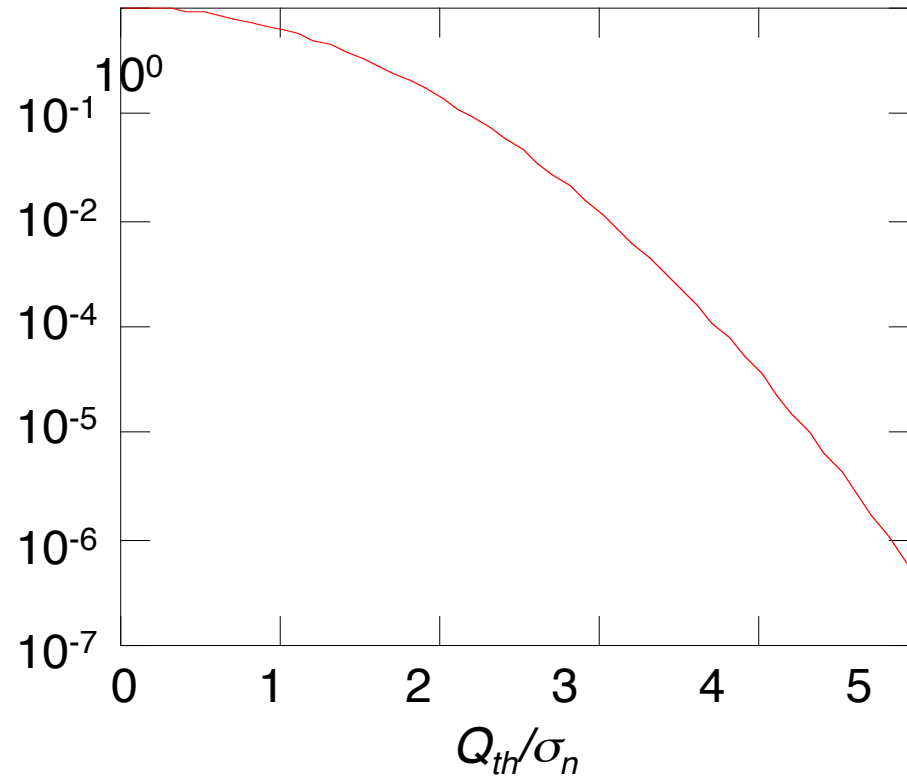
RANDOM NOISE RATE

discriminator
bandwidth, f_b

$$f_n = \frac{1}{\sqrt{3}} f_b \exp\left(\frac{-Q_{th}^2}{2\sigma_n^2}\right)$$

f_n/f_b

Q_{th} = threshold
 σ_n = noise rms



In a large bandwidth system (such as an HEP experiment) noise and threshold variation must be kept very far from the threshold and the signal to produce clean event information

from Michael CAMPBELL

'NOISE' in a DETECTOR

SPURIOUS SIGNALS if there is NO PARTICLE :

MANY CAUSES in DETECTOR and READOUT

e.g. AFTERPULSES from ION-FEEDBACK
in GASEOUS WIRECHAMBERS
SCINTILLATOR + PM USUALLY LOTS of NOISE
NEED for COINCIDENCES
Si APD MHz RANDOM PULSES
ELECTRICAL NOISE from DARK CURRENT, CAPACITANCE,

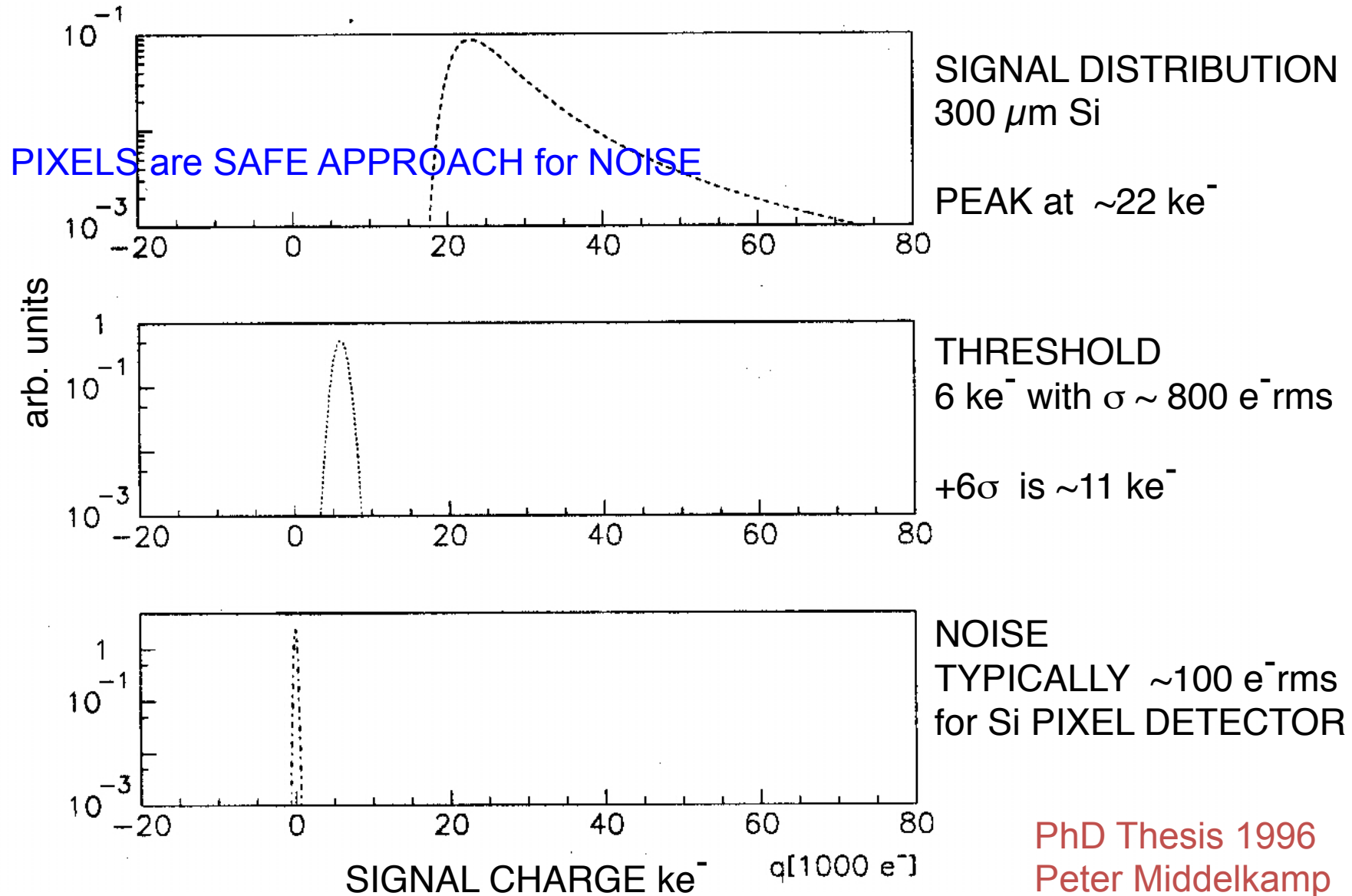
WIDTH of NOISE DISTRIBUTION IF GAUSSIAN

99.7% CONTAINED in $\pm 3\sigma$

with 6σ THRESHOLD one can have as low as 10^{-7} PROBABILITY
BUT watch out: in LHC $4 \cdot 10^7$ measurements/ s



CHARACTERISTICS for BINARY PIXEL SYSTEM



PhD Thesis 1996
Peter Middelkamp
fig.36

RELATIONS BETWEEN CAPACITANCE, SPEED, NOISE and POWER

In the first approximation all characteristics are dominated by the input transistor of the front-end amplifier.

Transistor transconductance g_m

$$g_m = \frac{q}{kT} I \quad \text{in weak inversion CMOS and in bipolar}$$

I is transistor current $\frac{kT}{q} \sim 0.025 \text{ eV}$

Noise (series noise) is dominated by detector capacitance C_d

$$\text{ENC}^2 = \frac{2 kT C_d^2}{g_m \tau} = \frac{2 k^2 T^2 C_d^2}{I \tau} = \frac{2 k^2 T^2 C_d^2 V}{P \tau}$$

approximation

RELATIONS BETWEEN CAPACITANCE, SPEED, NOISE and POWER (2)

Express the power P_d for detector readout as a function of noise and capacitance

$$P_d = \frac{2k^2 T^2 C_d^2 V}{ENC_d^2 \tau}$$

Power increases with square of capacitance, therefore it would be useful

to work with as small C_d as possible: **SEGMENTATION**

$$P_s = \frac{2k^2 T^2 C_s^2 V}{ENC_s^2 \tau}$$

for segmentation in n sensors $C_d = n \times C_s$

RELATIONS BETWEEN CAPACITANCE, SPEED, NOISE and POWER : SEGMENTATION (3)

for segmentation in n sensors $C_d = n \times C_s$

$$P_s = \frac{2k^2 T^2 C_s^2 V}{ENC_s^2 \tau}$$

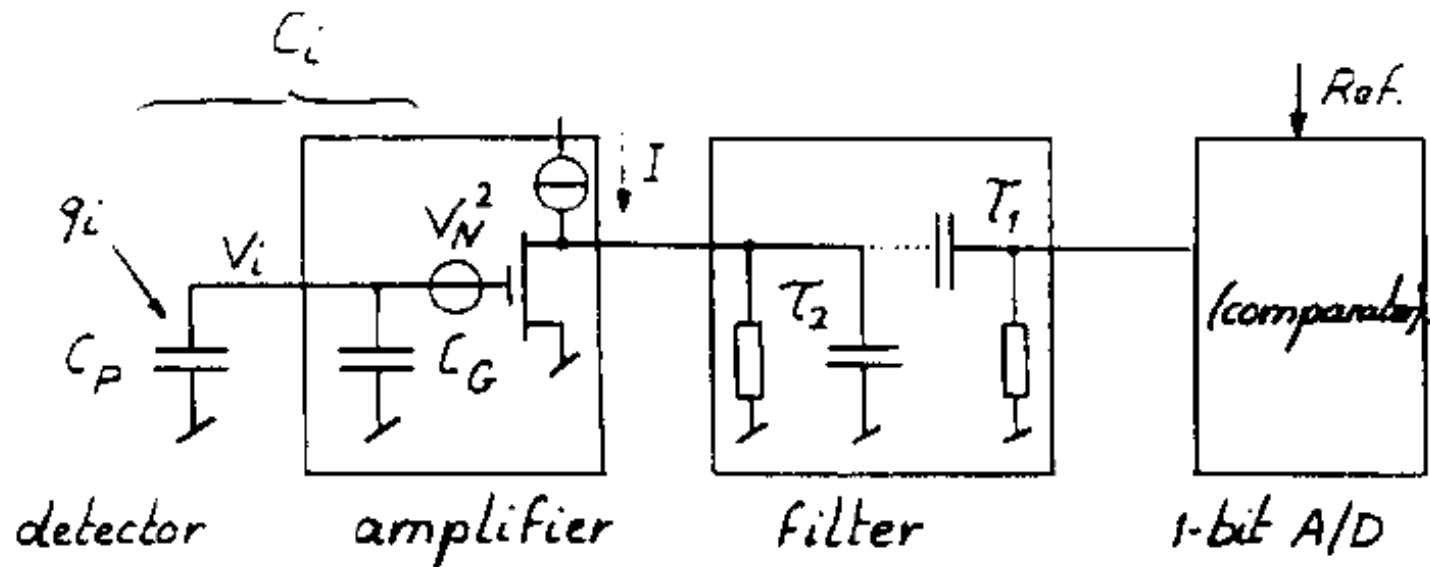
Power for all segments together P'_d is original/n
(in first approximation)

$$P'_d = n \times P_s = \frac{2k^2 T^2 C_d^2 V}{ENC_d^2 n \tau} = \frac{P_d}{n}$$

The invention of the pixel micropattern detector



Electronics Circuit in each Pixel 1988

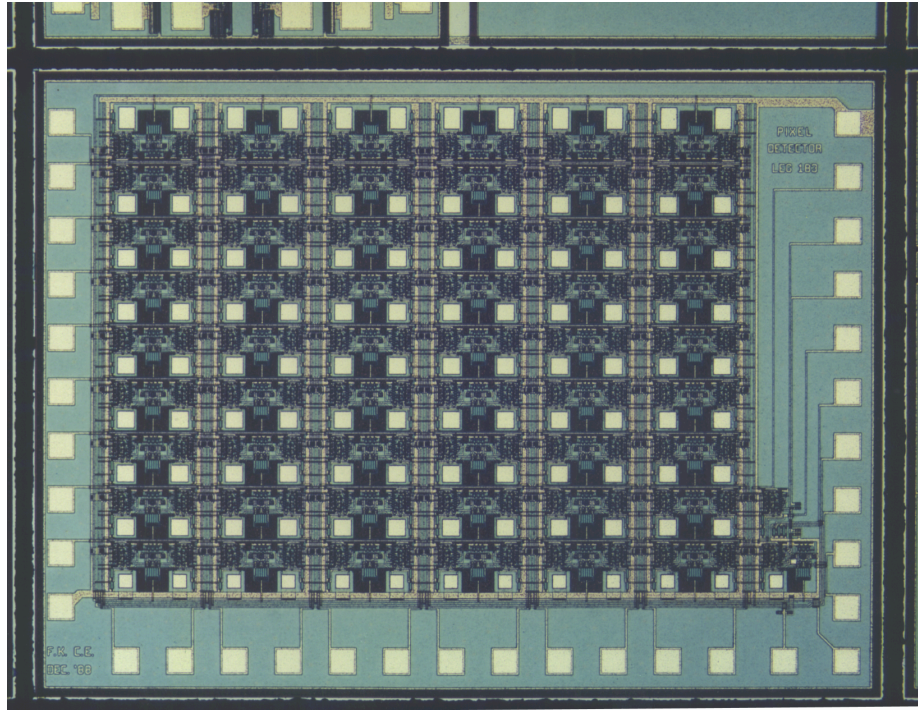


Schematic Diagram

worked out by prof Eric Vittoz, for 1988 Leuven Pixel Workshop

NIM A275 (1989) 472

First Pixel Detector Prototype 1989



Krummenacher et al. NIM A288 (1990) 176
(presented at Munich Symp Feb 1989)
circuit description

Campbell et al. NIM A290 (1990) 149
(presented at IEEE Nucl Sc. Symp. 1989)
results including spectra
taken with radioactive sources

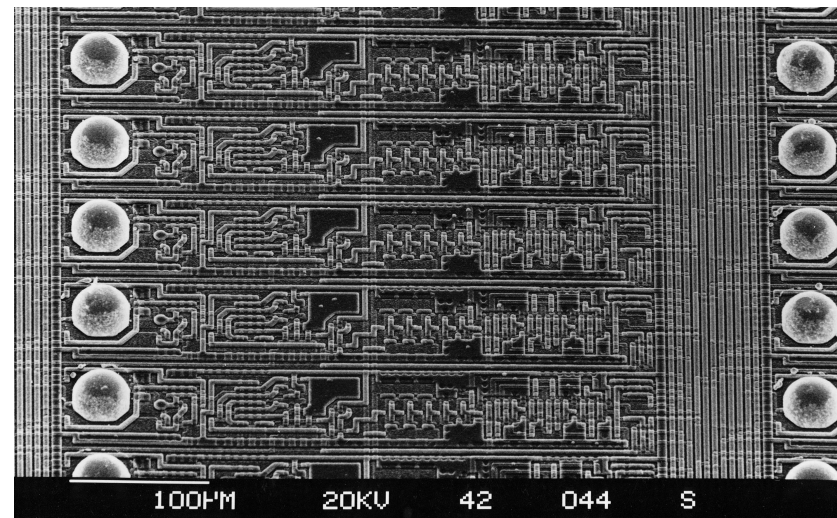
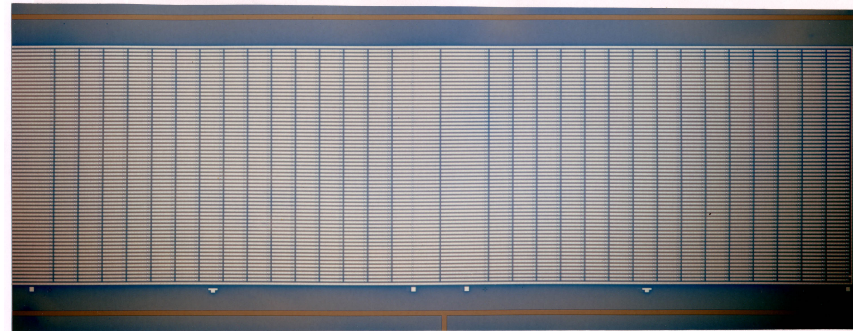
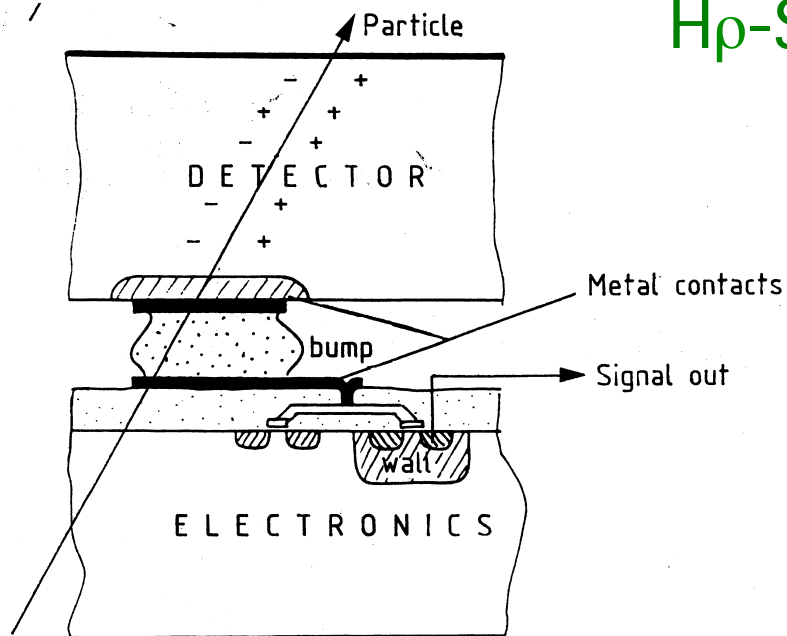
Pixel readout test chip 12x9 pixels, synchronous operation
designed Dec 1988 by Christian Enz and François Krummenacher,
in collaboration with CERN (Heijne, Jarron) and ETHZ (Viertel)

HYBRID Si PIXEL SENSOR 1991

CERN : CAMPBELL, HEIJNE

SENSOR MATRIX TRUE 2 - D

H_p -Si

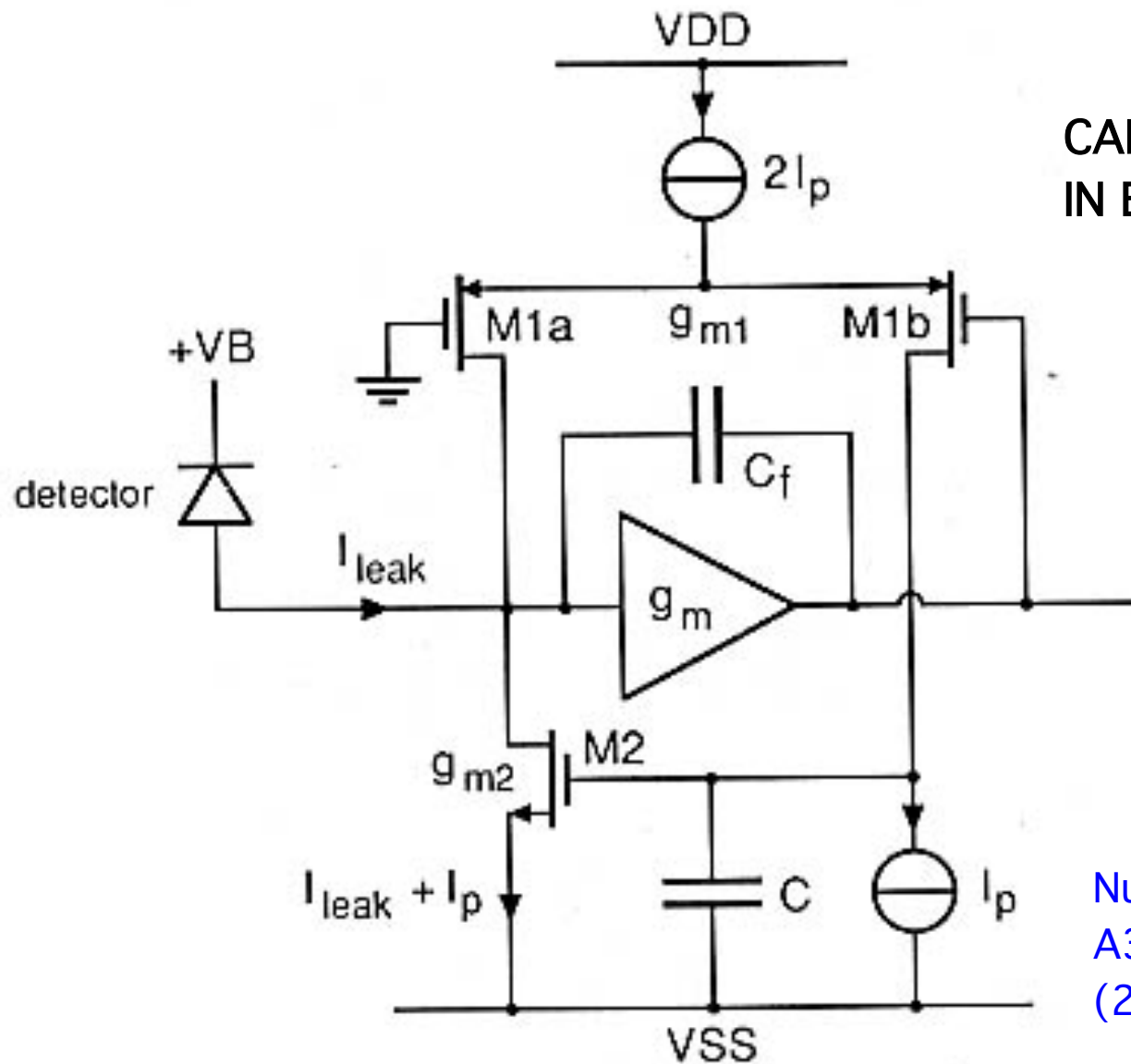


BUMPS

+

CMOS READOUT ELECTRONICS

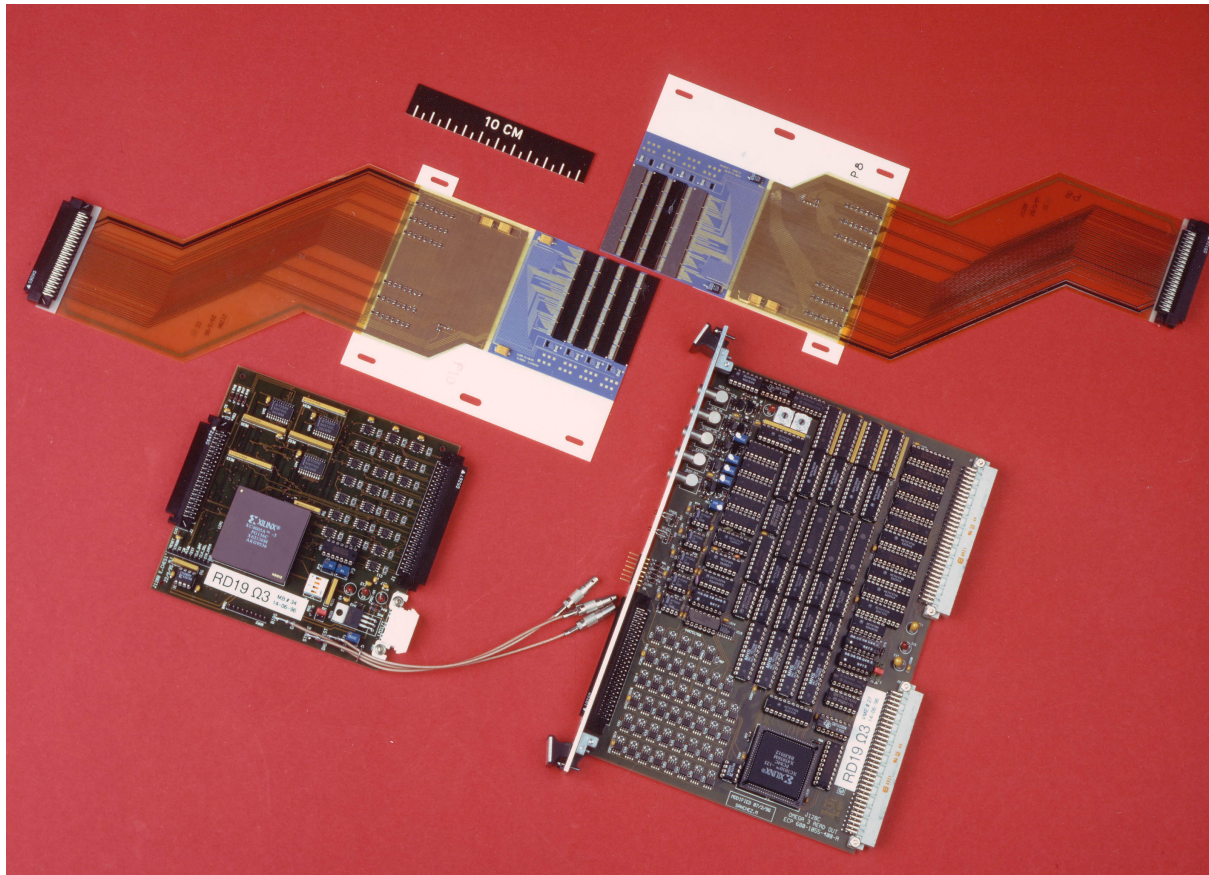
LEAKAGE CURRENT COMPENSATION KRUMMENACHER 1989



CAN BE IMPLEMENTED
IN EACH PIXEL CELL

Nucl. Instr. Meth.
A305 (1991) 527
(2nd Leuven Pixel Workshop)

LHC1 PIXEL ARRAYS 1995



2 x 4 LADDERS
with OVERLAP
COVER 5 x 5 cm²

14 PLANES
BUILT 1992 - 97

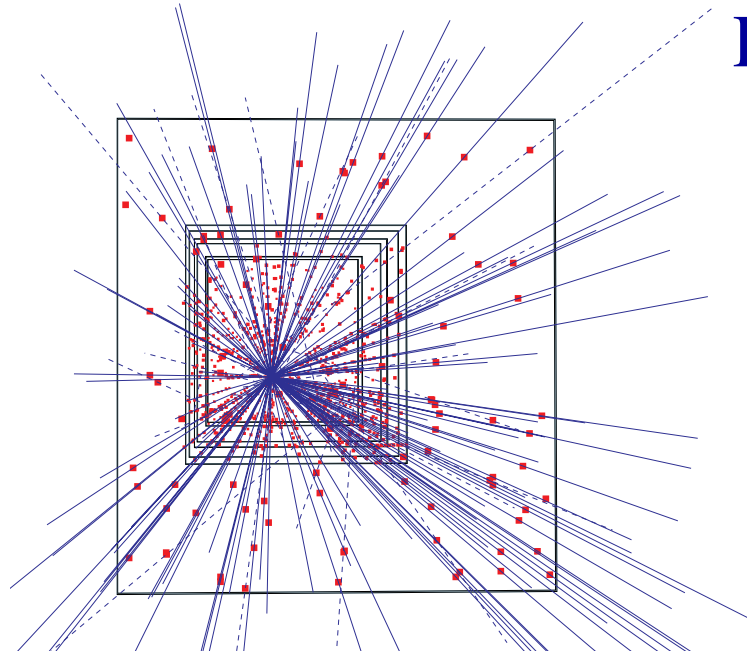
PIXEL TELESCOPE USED in Omega Spectrometer at CERN

RD19 collaboration at CERN for LHC detector R&D

➔ this pixel chip first presented in Hiroshima Symposium 1995
NIM A383 (1996) 55

TRACKING with PIXELS at CERN

WA97



RD19

1995

7 PLANES
1.1 M pixels

153 tracks

B-field OFF

^{208}Pb ion at 158 A GeV/c on Pb target

Millions of EVENTS ANALYZED

SPACE POINTS

NOISE-FREE

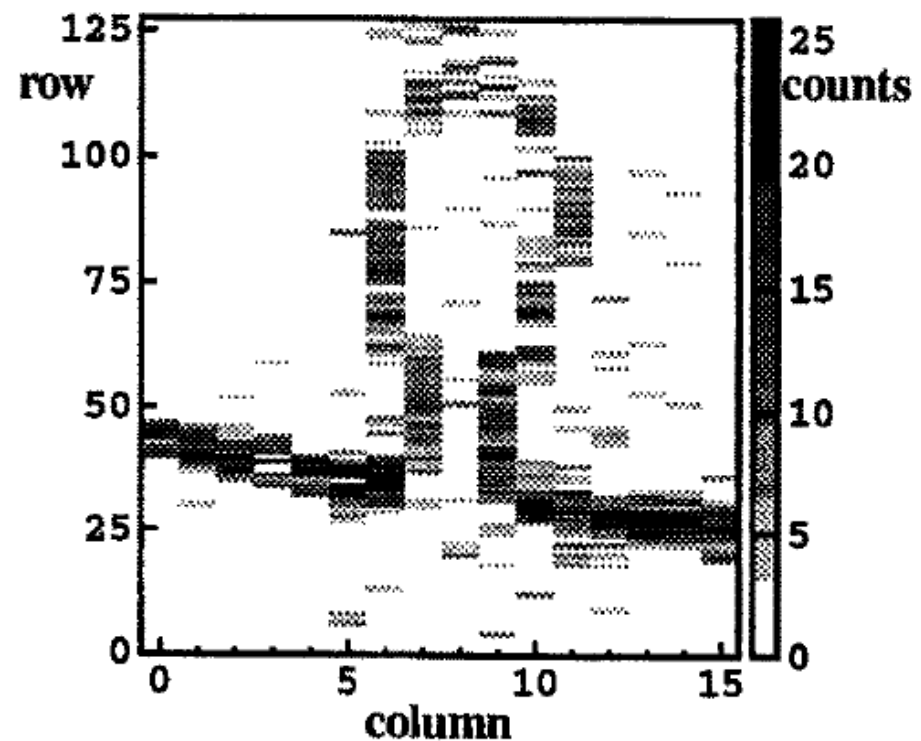


Ideas for imaging were around since the beginning

Image made with GaAs assembly by Cinzia da Via
and by Peter Middelkamp in 1996

Medipix effort really started at CERN
in 1998 after the
Trieste meeting by INFN

NIM A395 (1997) 148
PhD Thesis P. Middelkamp WUB-DIS 96-23
PhD Thesis C. Da Via Glasgow 1997



Medipix Pixel Detectors for X-ray imaging



Chips Designed in Framework of Medipix

Medipix1 (1998)	1 μ m SACMOS, 64x64 pixels, 170x170 μ m ² PC / Frame based readout
Medipix2 (2001)	0.25 μ m CMOS, 256x256 pixels, 55x55 μ m ² PC / Frame based readout
Timepix (2006)	0.25 μ m CMOS, 256x256 pixels, 55x55 μ m ² PC, ToT, ToA / Frame based readout
Medipix3 (2009)	0.13 μ m CMOS, 256x256 pixels, 55x55 μ m ² PC / Frame based readout Event by event charge reconstruction and allocation
Dosepix (2011)	0.13 μ m CMOS, 16x16 pixels, 220x220 μ m ² ToT, PC / Rolling shutter (programmable column readout) Event by event binning of energy spectra (16 digital thrs)
Timepix3 (2013)	0.13 μ m CMOS, 256x256 pixels, 55x55 μ m ² PC; ToT, ToA (simultaneous)/ Data driven readout
Smallpix	0.13 μ m CMOS, 512x512 pixels, 40x40 μ m ² (TBD) PC, iToT; ToA, ToT1 (simultaneous)/ Frame based (ZC) TSV compatible design
Clickpix prototype	65nm CMOS, 64x64 pixels, 25x25 μ m ² ToA, ToT1 (simultaneous)/ Frame based (ZC)

Acknowledgement

Presented work is done by
many other people in the Medipix Collaboration

Several slides have been taken from their presentations

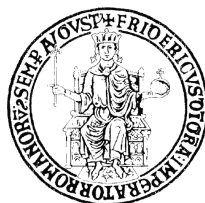
Information on Medipix:

<http://medipix.web.cern.ch/medipix/>



MEDIPIX2 PARTNERS

- U INFN Cagliari
- CEA-LIST Saclay
- CERN Genève
- U d'Auvergne Clermont
- U Erlangen
- ESRF Grenoble
- U Freiburg
- U Glasgow
- IFAE Barcelona
- Mid-Sweden University
- MRC-LMB Cambridge
- U INFN Napoli
- NIKHEF Amsterdam
- U INFN Pisa
- FZU CAS Prague
- IEAP CTU in Prague
- SSL Berkeley
- University Houston



ALBERT-LUDWIGS-
UNIVERSITÄT-FREIBURG



Friedrich-Alexander-Universität
Erlangen-Nürnberg



UNIVERSITY
of
GLASGOW



SPOKESMAN Michael CAMPBELL





The Medipix3 Consortium

AMOLF, Amsterdam, The Netherlands (alphabetic by city)

NIKHEF, Amsterdam, The Netherlands

Space Sciences Lab, University of California, Berkeley, USA

Universidad de los Andes, Bogota, Colombia

University of Bonn, Germany

Brazilian Light Source, Campinas, Brazil

University of Canterbury, Christchurch, New Zealand

Universität Erlangen-Nürnberg, Erlangen, Germany

VTT, Information Technology, Espoo, Finland

Albert-Ludwigs-Universität, Freiburg, Germany

CERN, Geneva, Switzerland,

University of Glasgow, Scotland, UK

ESRF, Grenoble, France

DESY, Hamburg, Germany

University of Houston, USA

ISS, Forschungszentrum Karlsruhe, Germany

Leiden University, The Netherlands

Technical University of Munich, Germany

Diamond Light Source, Oxfordshire, England, UK

CEA-LIST, Paris, France

IEAP, Czech Technical University, Prague, Czech Republic

Mid Sweden University, Sundsvall, Sweden

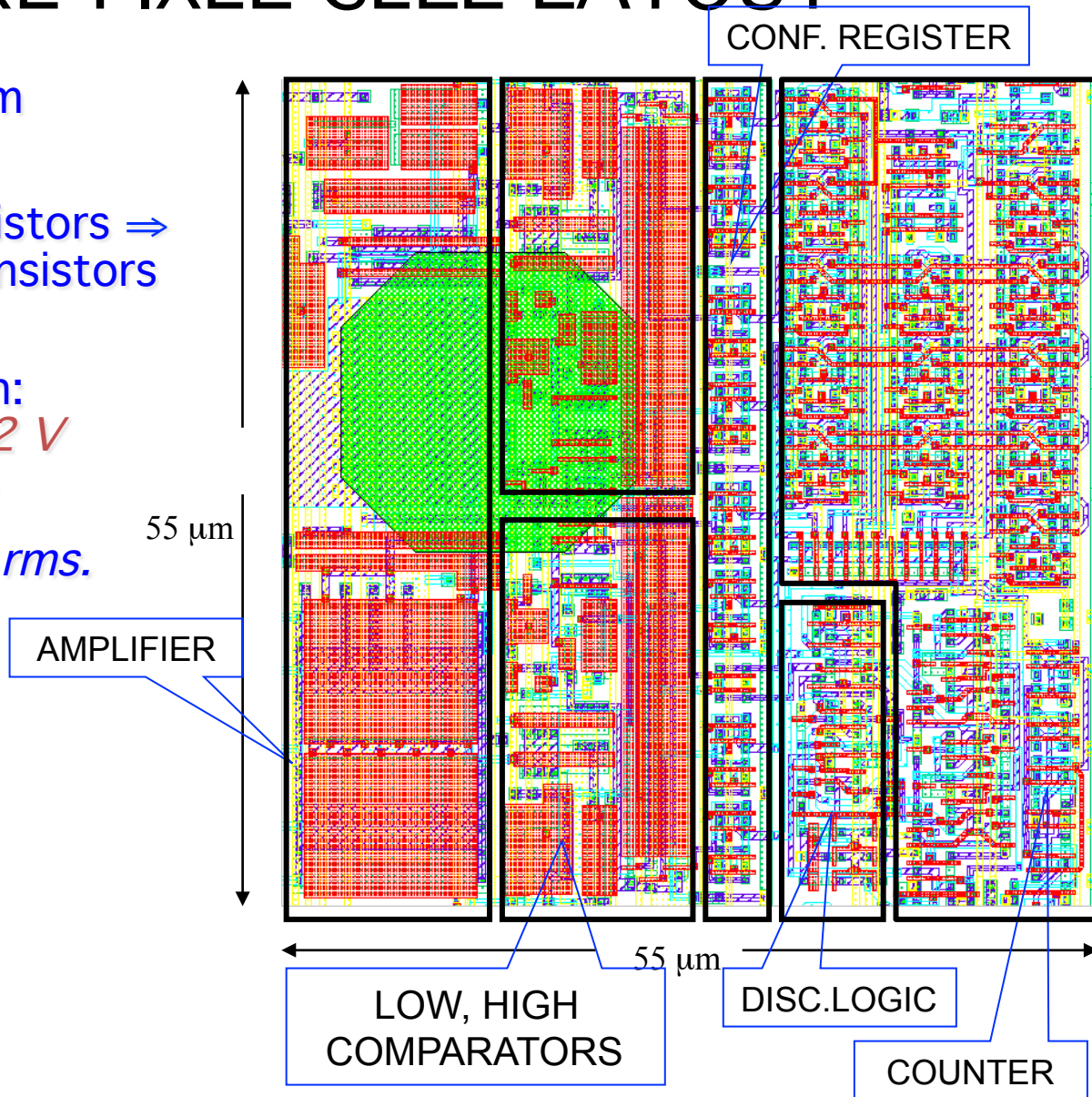
Medipix2 PIXEL CELL LAYOUT

CMOS technology $0.25\mu\text{m}$
6 metal layers
pixel cell has ~ 500 transistors \Rightarrow
chip ~ 33 million transistors

Static power consumption:
 $\sim 8\mu\text{W}/\text{channel}$ @ 2.2 V

Amplifier Gain: $\sim 11\mu\text{V}/e^-$

Electronic Noise: $\sim 100 e^- \text{ rms.}$



MEDIPIX2 pixel schematic block diagram

accepts positive and negative input → different detector materials

charge sensitive preamplifier with individual leakage current compensation

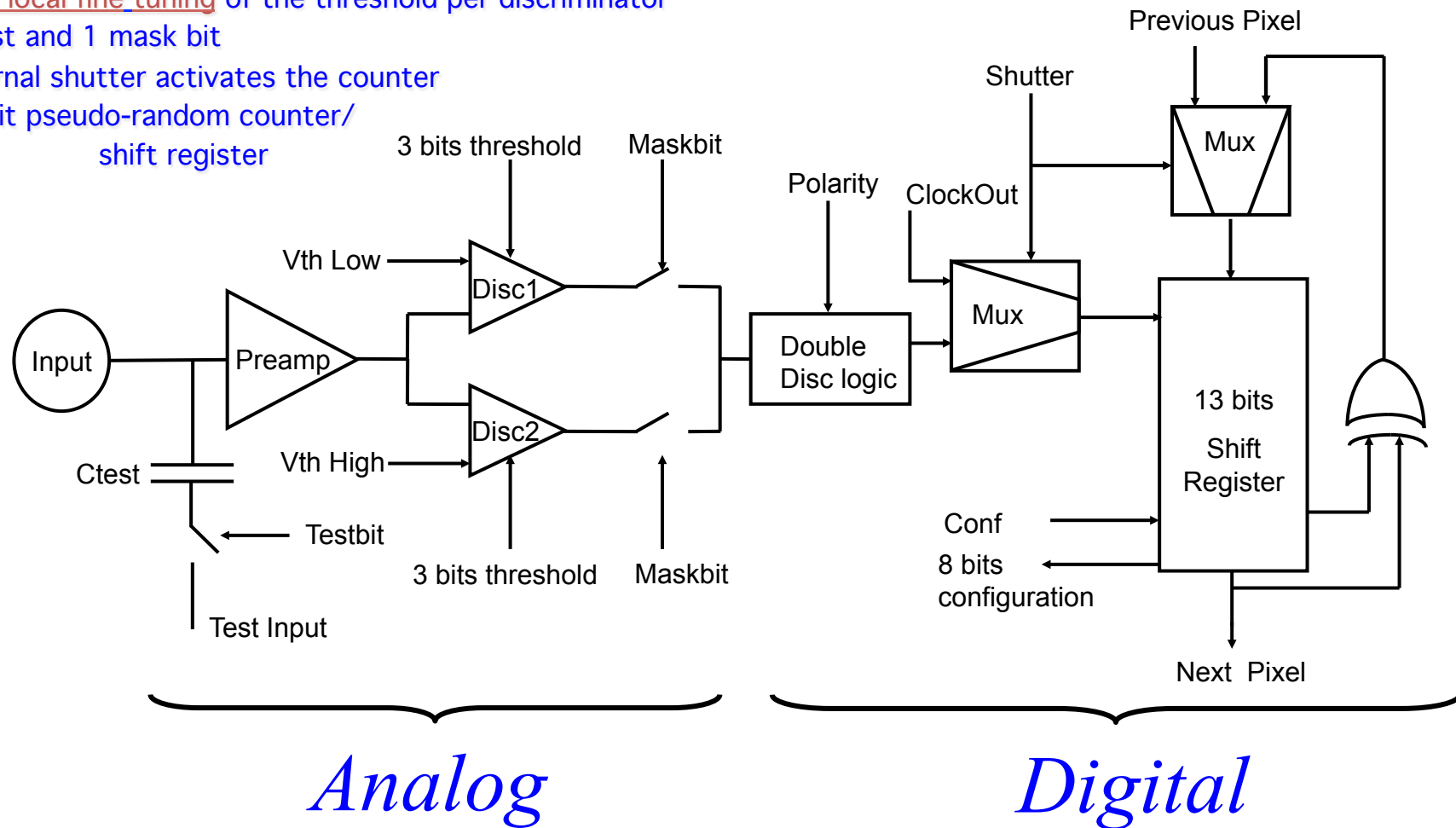
2 discriminators with globally adjustable threshold

3-bit local fine tuning of the threshold per discriminator

1 test and 1 mask bit

external shutter activates the counter

13-bit pseudo-random counter/
shift register



MEDIPIX as RADIATION MONITOR

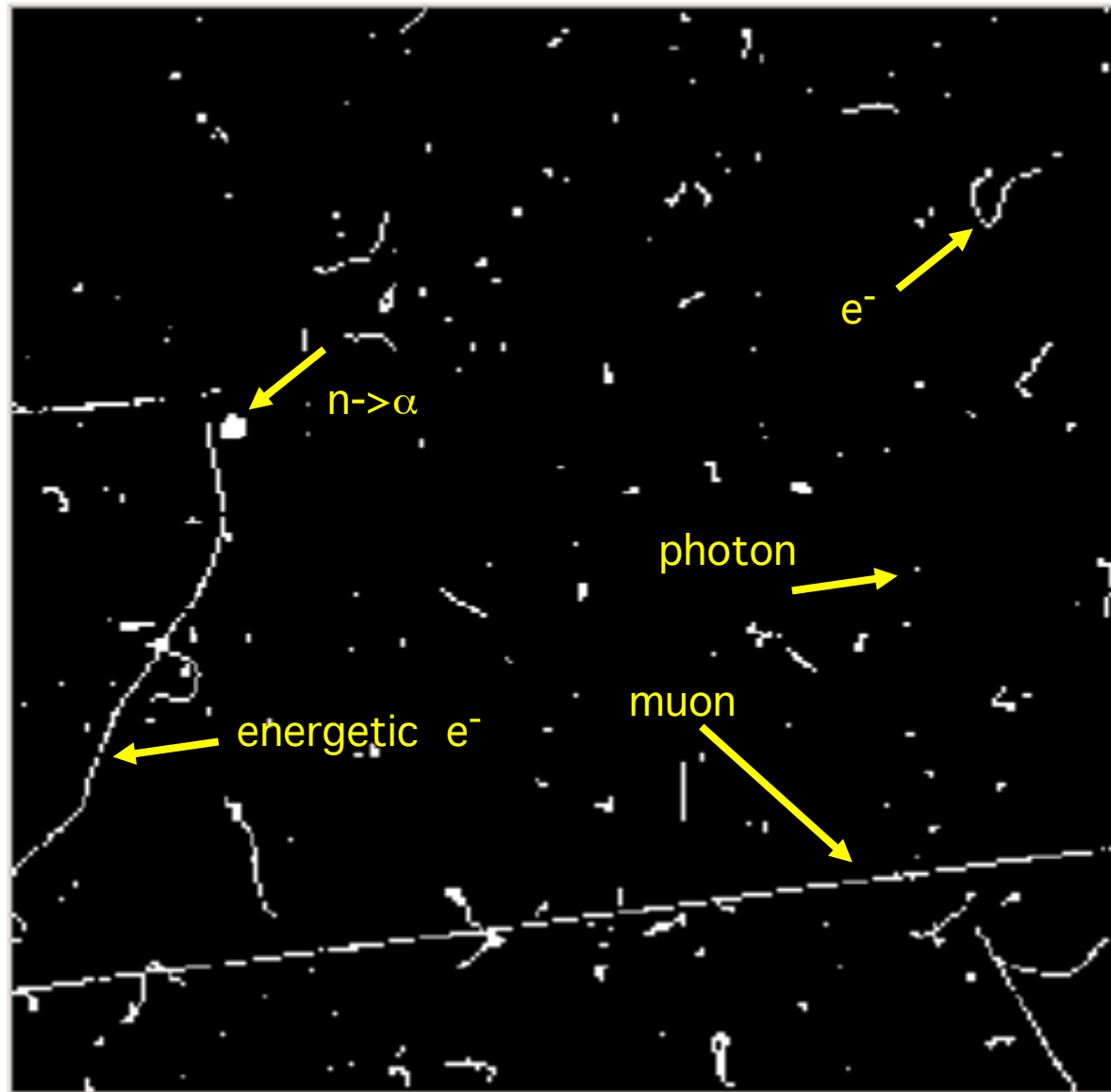
256 x 256 PIXELS
300 μm THICK Si

IDENTIFY SPECIFIC QUANTA
ELECTRONS
PHOTONS
MIPs
NEUTRONS \rightarrow ALPHAS



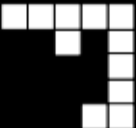
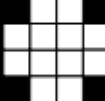
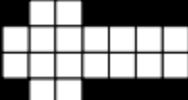

ADJUSTABLE EXPOSURE
ms – hours
LARGE DYNAMIC RANGE
few ns precision

Miniature
electronic version of
tracking in
nuclear emulsion or
bubble chamber

typical frame
IEAP CTU Prague



Characteristic cluster patterns in Medipix

1) Dot		Photons and electrons (10keV)
2) Small blob		Photons and electrons (~100keV)
3) Curly track		Electrons (MeV range)
4) Heavy blob		Heavy ionizing particles with short range (alpha particles,...)
5) Heavy track		Heavy ionizing particles (protons,nuclei, Fe, ...)
6) Straight track		Energetic light charged particles (MIP, Muons,...)



COSMIC RAYS

EFFECTS on ELECTRONICS
Ziegler, IBM J Res & Dev 1998

INCOMING FLUX $\sim 10^3 \text{ m}^{-2} \text{ s}^{-1}$

13 km HEIGHT $\sim 10^6 \text{ m}^{-2} \text{ s}^{-1}$

SEA LEVEL $\sim 10^4 \text{ m}^{-2} \text{ s}^{-1}$

Ziegler,
IBM J Res & Dev 1998
mostly neutrons

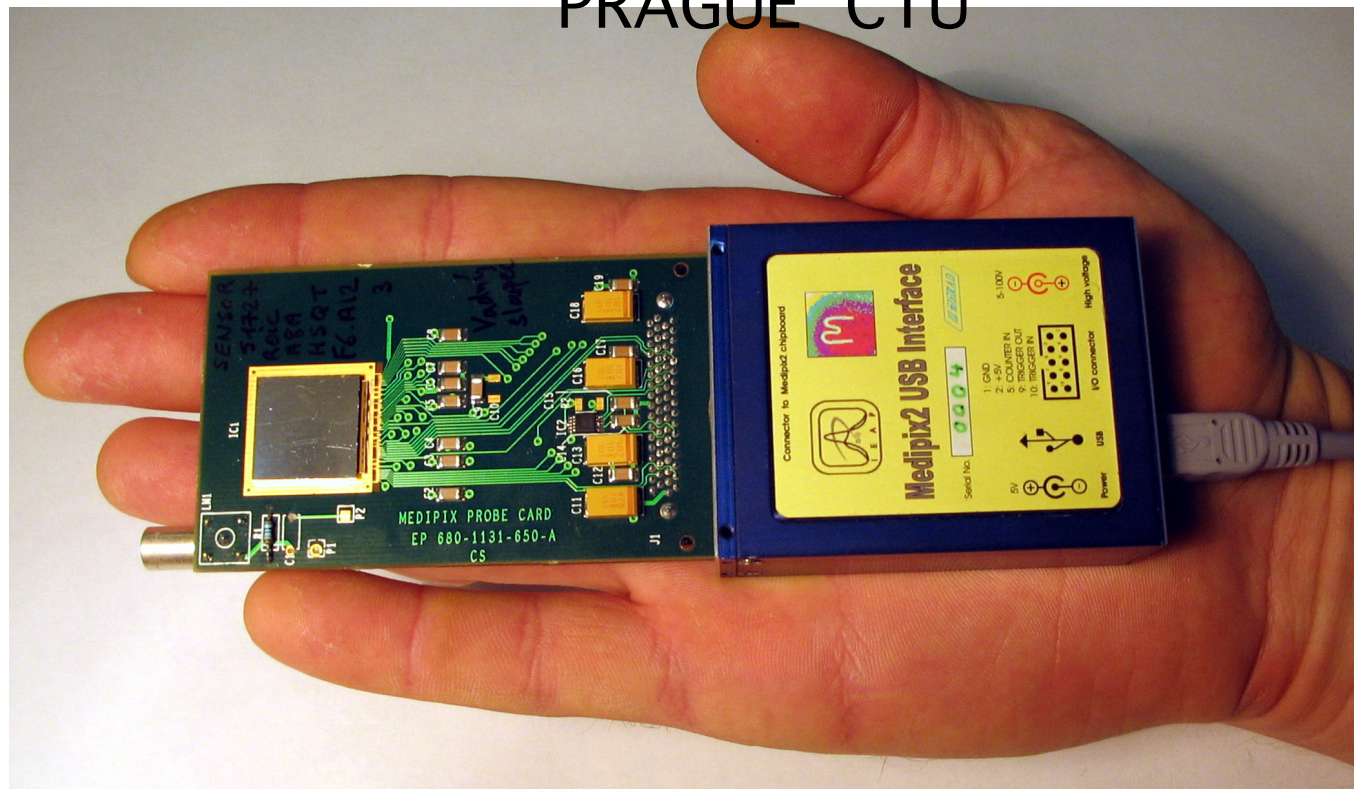


RULE of THUMB $\sim 1 \text{ cm}^{-2} \text{ s}^{-1}$

MEDIPIX USB

USED and POWERED from PORTABLE

PIXELMAN SOFTWARE
PRAGUE CTU



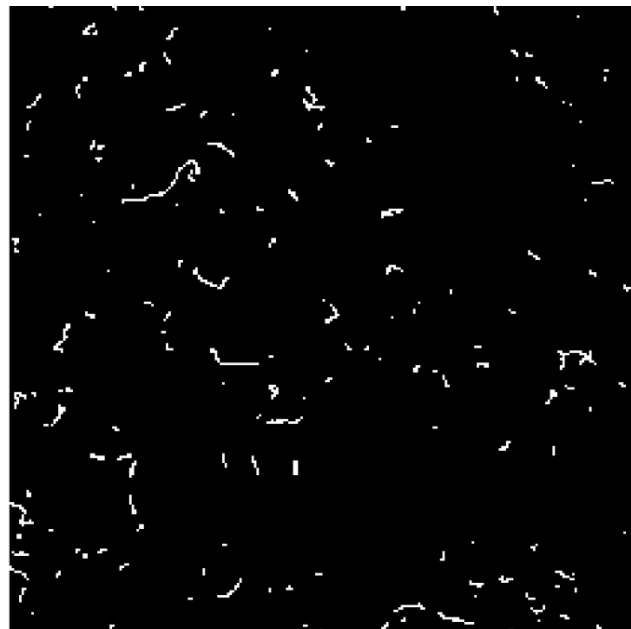
Integrating cosmic rays at sea level



Dosimetry with Medipix

- Two approaches:
- classification + counting of quantum-induced clusters
 - sum of deposited energy in all hit pixels

comparison with standard sources ^{60}Co and ^{137}Cs
photon energies 1173 & 1333keV resp. 662keV



^{60}Co

many
long trails

$2.26 \cdot 10^{-10}$ Sv
per cluster

± 0.19



^{137}Cs
shorter
trails

$1.71 \cdot 10^{-10}$ Sv
per cluster

± 0.07

Dosimetry with Medipix

- clustercounting: assign $2 \cdot 10^{-10}$ Sv per cluster
normalize exposure time to 1 h or 1y (8760h)
- energy deposit: $1\text{Sv} = 1\text{Gy} \times \text{quality } Q = 1 \text{ J/kg} \times Q$ ($Q=1$)
sensor chip is 0.137 g : normalize per kg of Si
mean deposit 30keV/pixel $1 \text{ keV} = 1.6 \cdot 10^{-16} \text{ J}$
use 'typical' calibration curve for Medipix-T assembly
with TOT (time-over-threshold ADC)
normalize exposure time to 1 h or 1y (8760h)

both methods fairly coherent:

cluster with 10 pixels $\rightarrow \sim 300\text{keV} \rightarrow 3.5 \cdot 10^{-10} \text{ Sv}$

clusters from alpha or long muon trails have to be treated separately with different algorithm. Also then $Q \neq 1$

Dosimetry with Medipix

some examples:

dosimetry in airplane above Groenland

dosimetry in Atlas

dosimetry at home

educational tool: make radiation visible in school

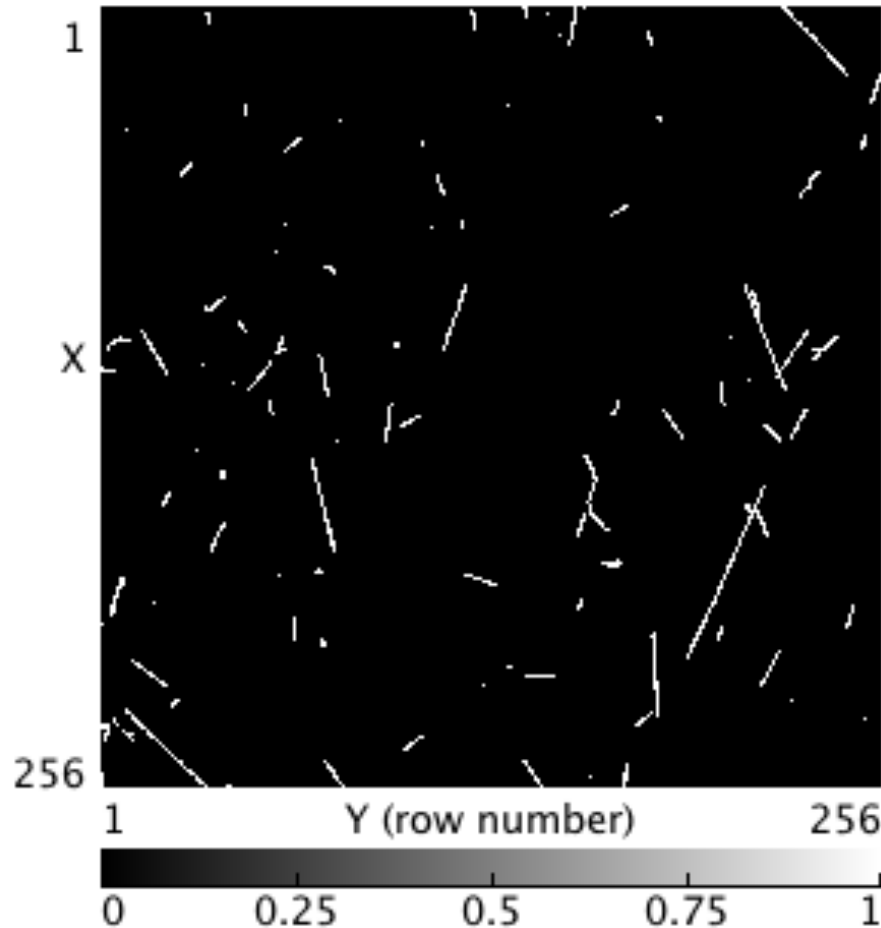
amateur physics

easy measurements when something happens

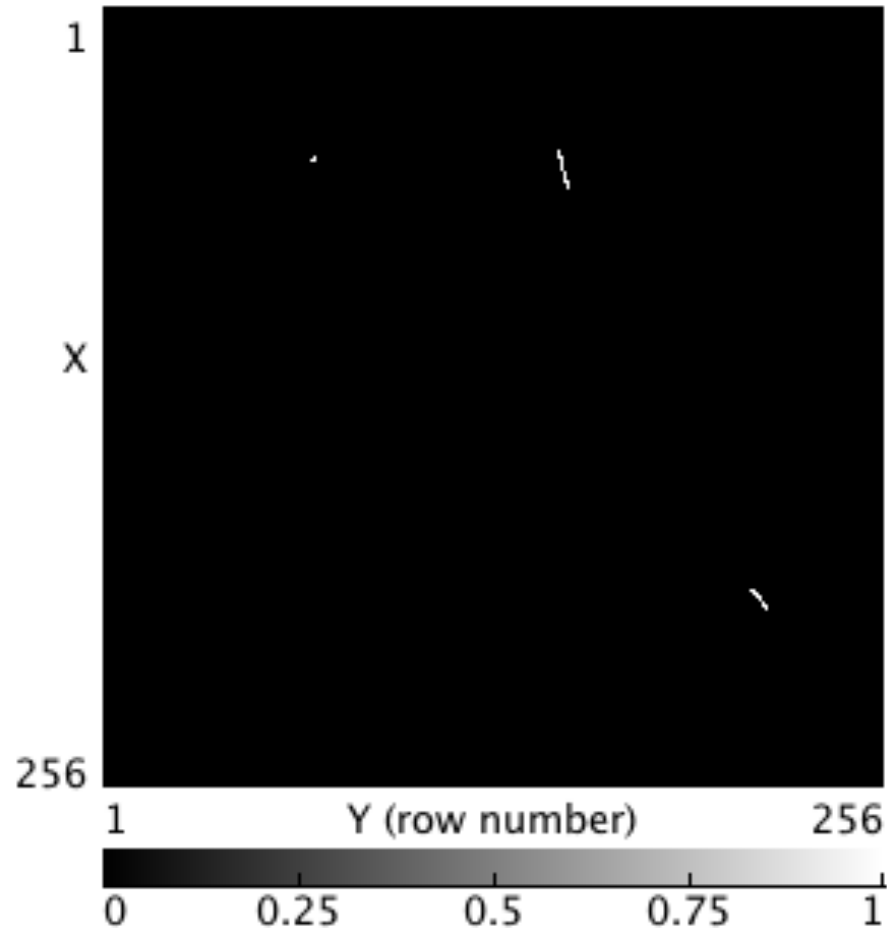


MEDIPIX measurements in-flight

Compare radiation at 10km and sea level



frame 20 at 10km 99 clusters (35 muons)

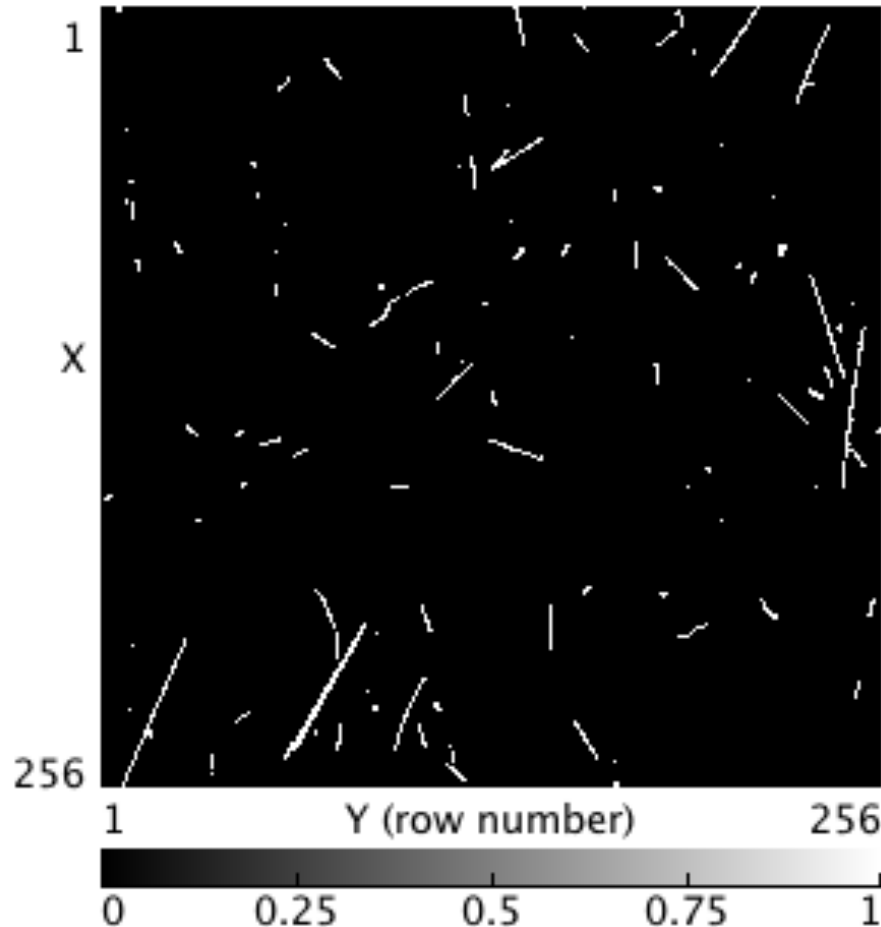


frame 35 at SLAC 3 clusters

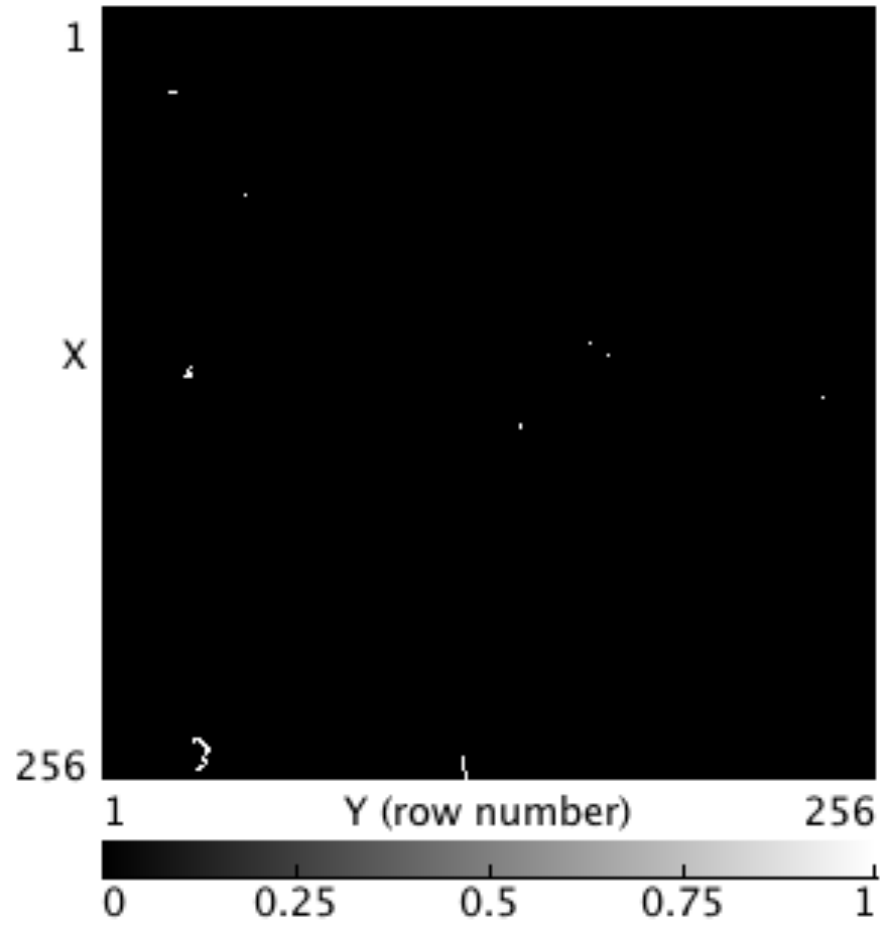
both longitudinal exposure of 60s $(0.8+0.7)\mu\text{Sv/h}$ vs $0.03\mu\text{Sv/h}$ 50x

MEDIPIX measurements in-flight

Compare radiation at 10km and sea level



frame 21 at 10km 105 clusters (36 muons)

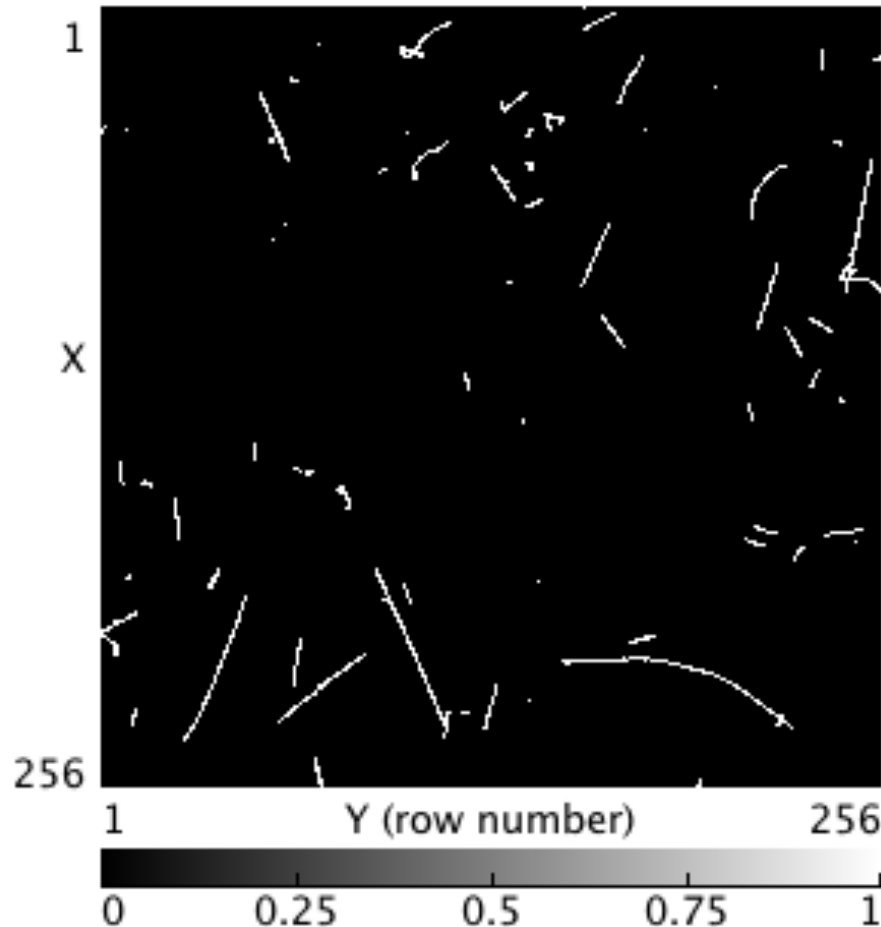


frame 36 at SLAC 9 clusters

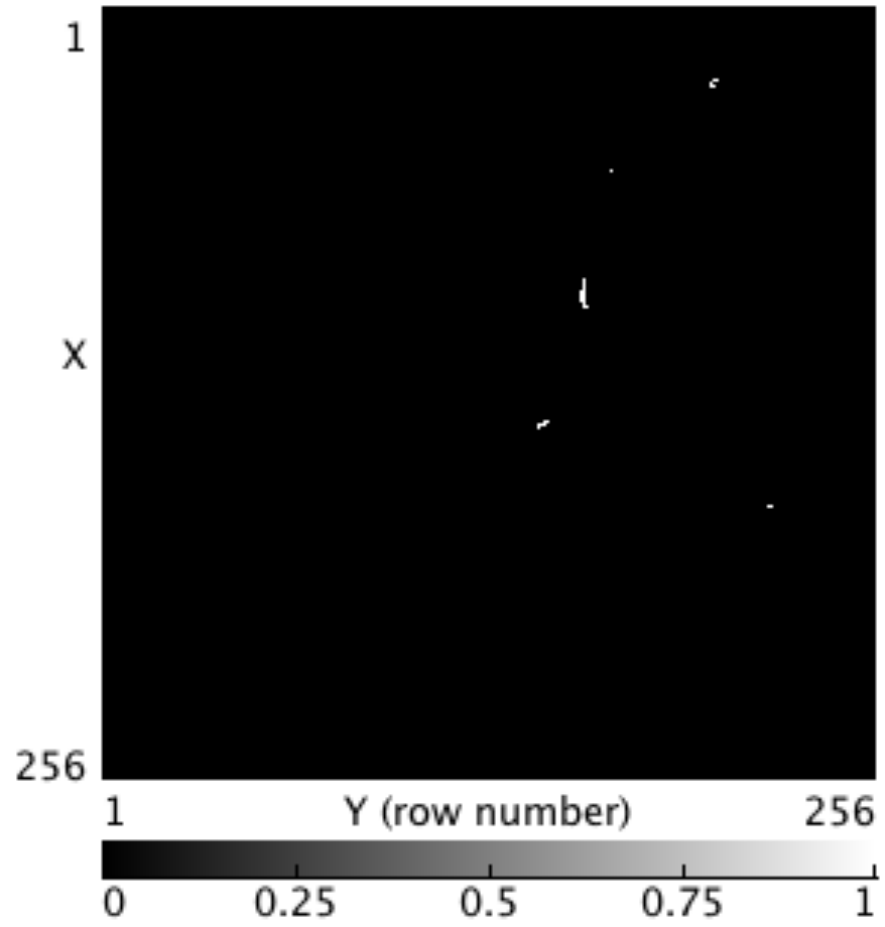
both longitudinal exposure of 60s $(0.9+0.8)\mu\text{Sv/h}$ vs $0.1\mu\text{Sv/h}$ 17x

MEDIPIX measurements in-flight

Compare radiation at 10km and sea level



frame 24 at 10km 72 clusters (28 muons)

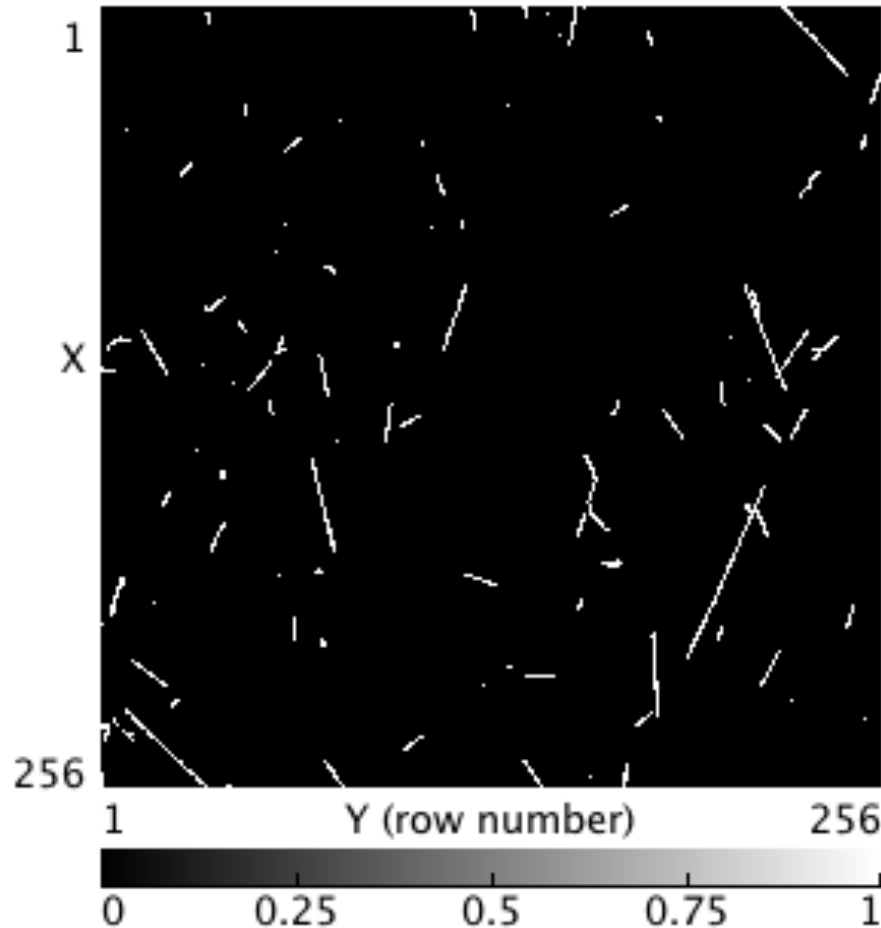


frame 38 at SLAC 5 clusters

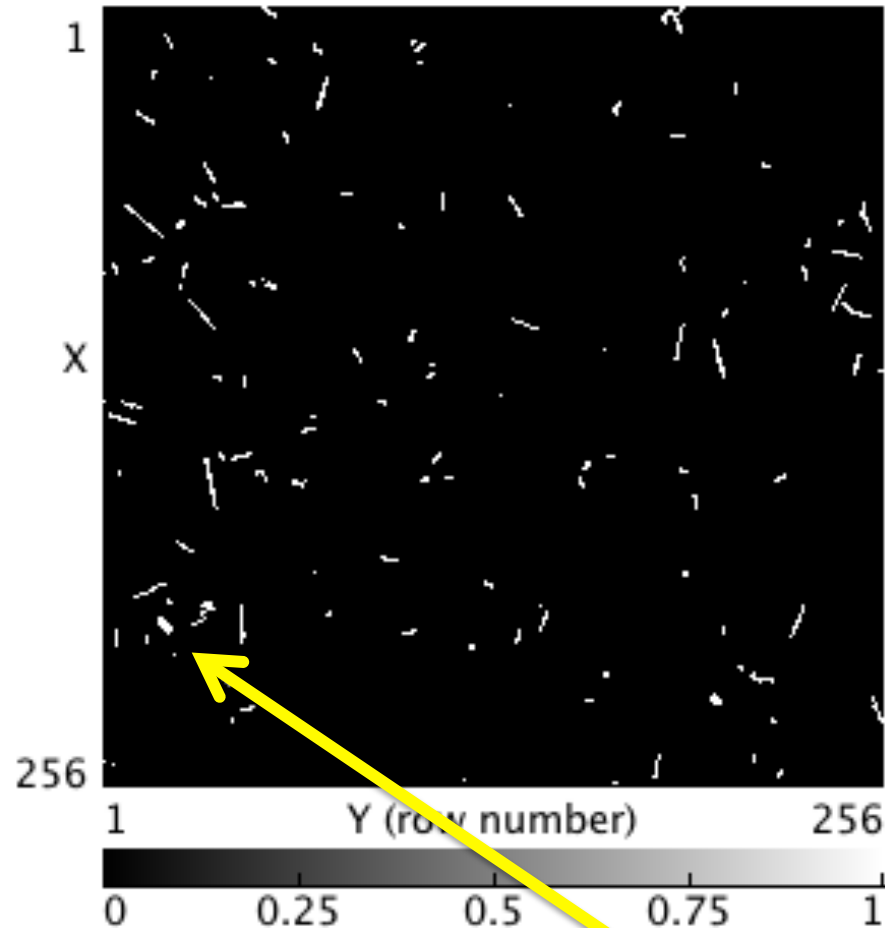
both longitudinal exposure of 60s $(0.6+0.5)\mu\text{Sv/h}$ vs $0.06\mu\text{Sv/h}$ 20x

MEDIPIX measurements in-flight

radiation parallel and perpendicular to sensor



frame 20 at 10km 99 clusters, 35 muons
both 60s exposures **1.5uSv/h**



frame 13 at 10km 119 clusters (31 muons)
1.8uSv/h much shorter muons, 1 heavy trail

ATLAS – MPX

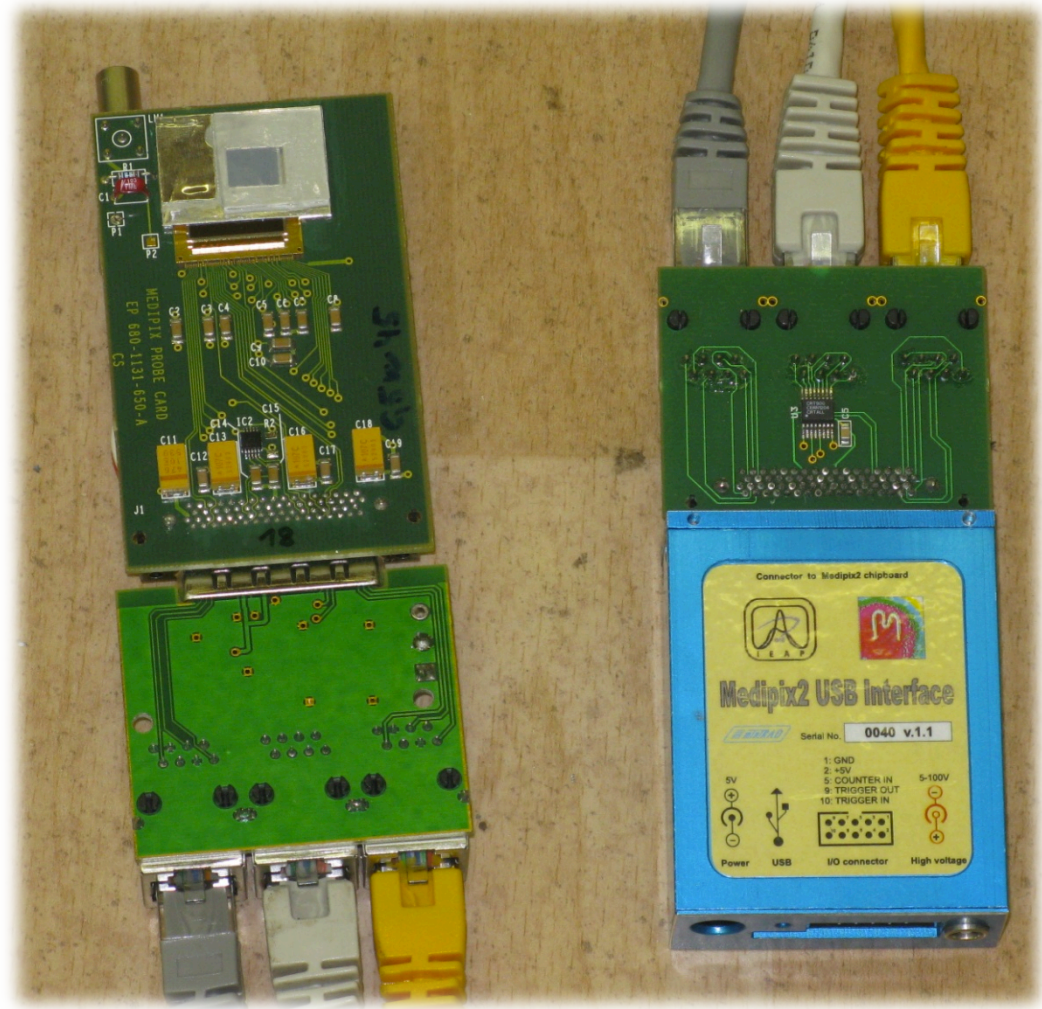
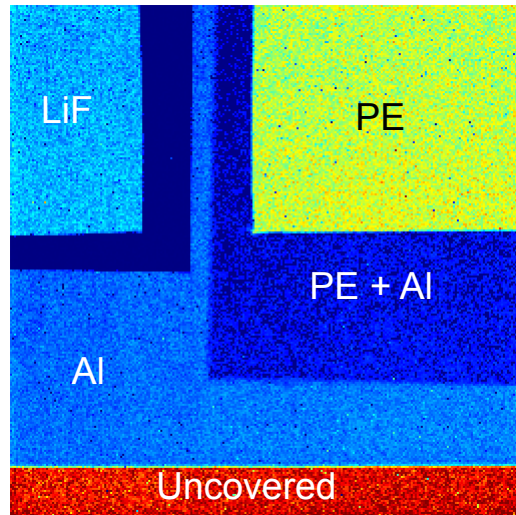
16 devices installed emphasis on neutron environment

Medipix2 ASIC + 300 μ m Si sensor
connected to radhard drivers
3 ethernet cables
receiver and USB interface readout
Pixelman software in PC

Neutron conversion structures:

- 1) LiF+50 μ m Al foil area
- 2) 100 μ m Al foil area
- 3) PolyEthylene PE area
- 4) PE+50 μ m Al foil area
- 5) Uncovered area

geometry of conversion layers



Neutron efficiency calibration

Calibrated efficiency:

Thermal: $1.41\text{E-}2 \pm 7.11\text{E-}4 \text{ cm}^{-2}\text{s}^{-1}$

^{252}Cf : $1.19\text{E-}3 \pm 1.89\text{E-}5 \text{ cm}^{-2}\text{s}^{-1}$

$^{241}\text{AmBe}$: $2.86\text{E-}3 \pm 5.46\text{E-}5 \text{ cm}^{-2}\text{s}^{-1}$

VanDGraaff : $7.23\text{E-}3 \pm 5.81\text{E-}4 \text{ cm}^{-2}\text{s}^{-1}$

PE / PE+Al cluster count ratio:

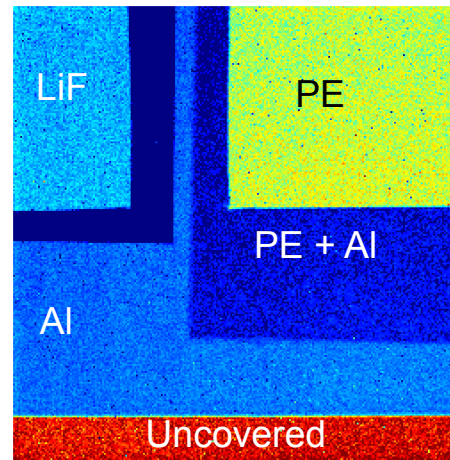
^{252}Cf : 10.70 ± 0.04

$^{241}\text{AmBe}$: 5.18 ± 0.03

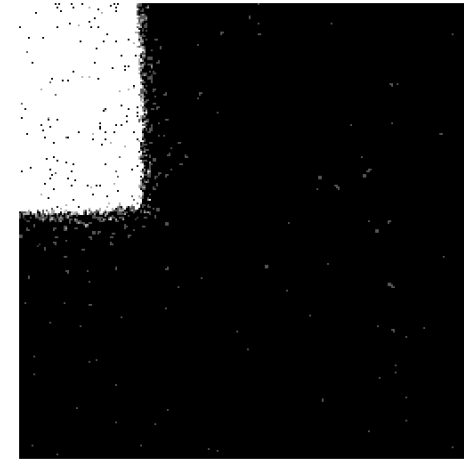
VDG: 2.51 ± 0.03

work in IEAP-CTU Prague

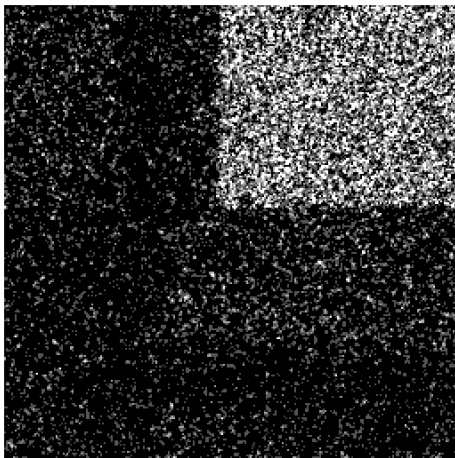
X-ray image of conversion layers



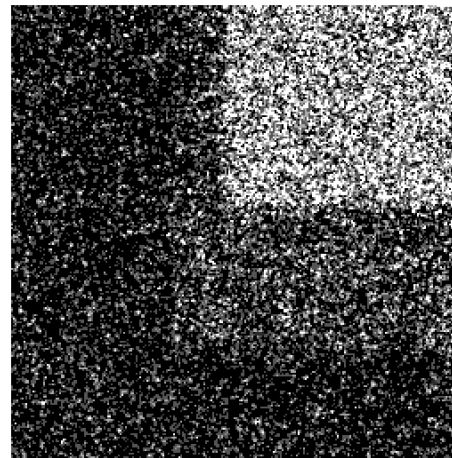
Thermal – 500s (2.5E6 neutrons)



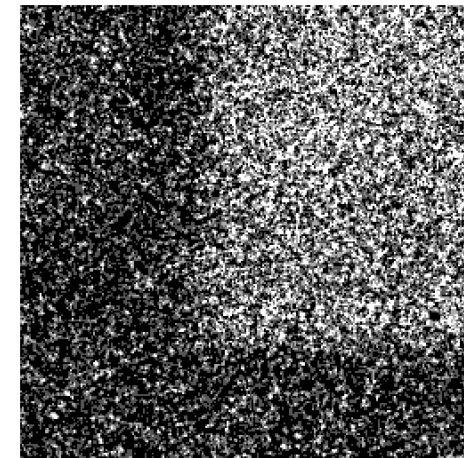
^{252}Cf – 2000s (1E8 neutrons)



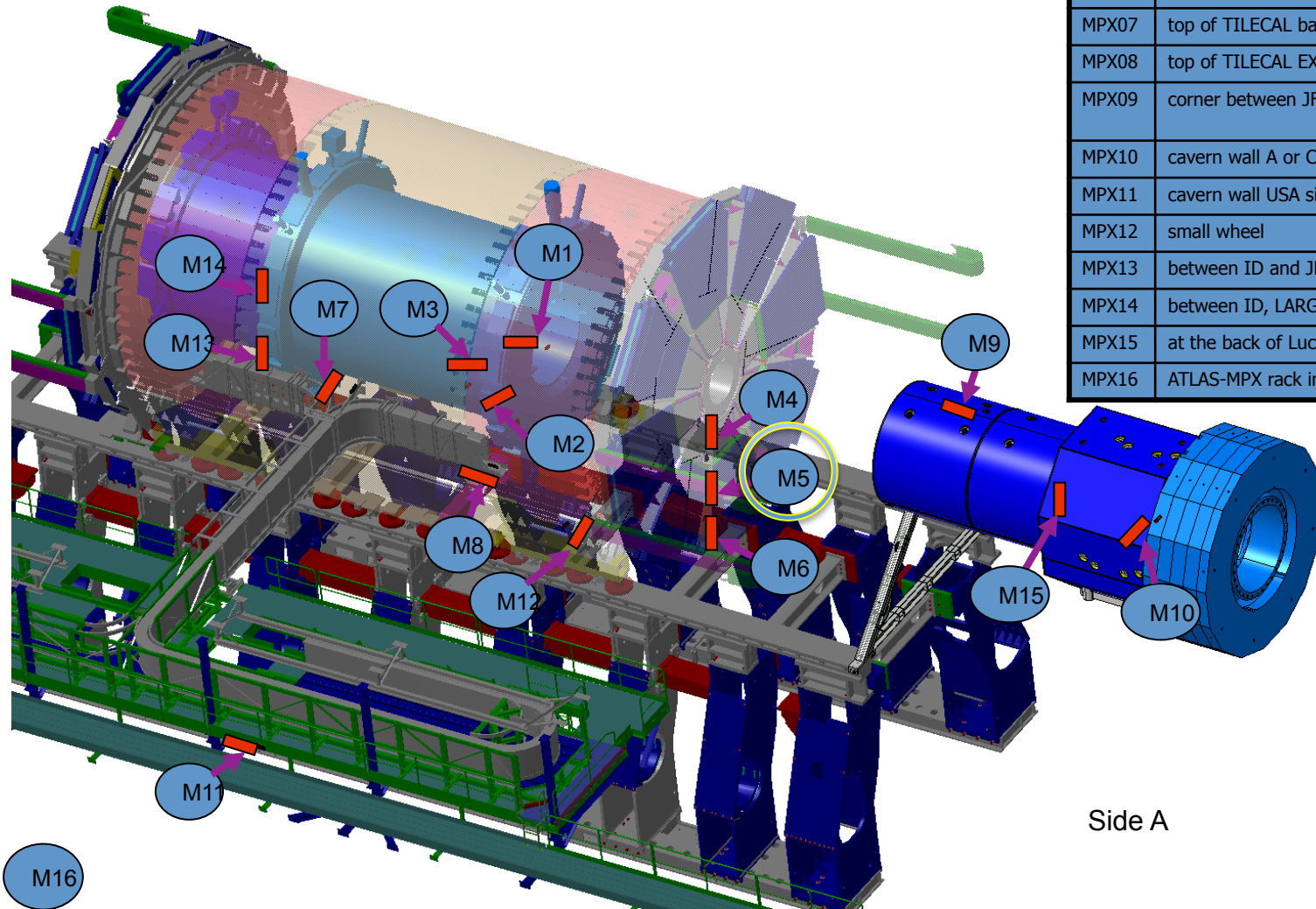
AmBe – 2000s (4E7 neutrons)



VDG – 1000s (1E7 neutrons)



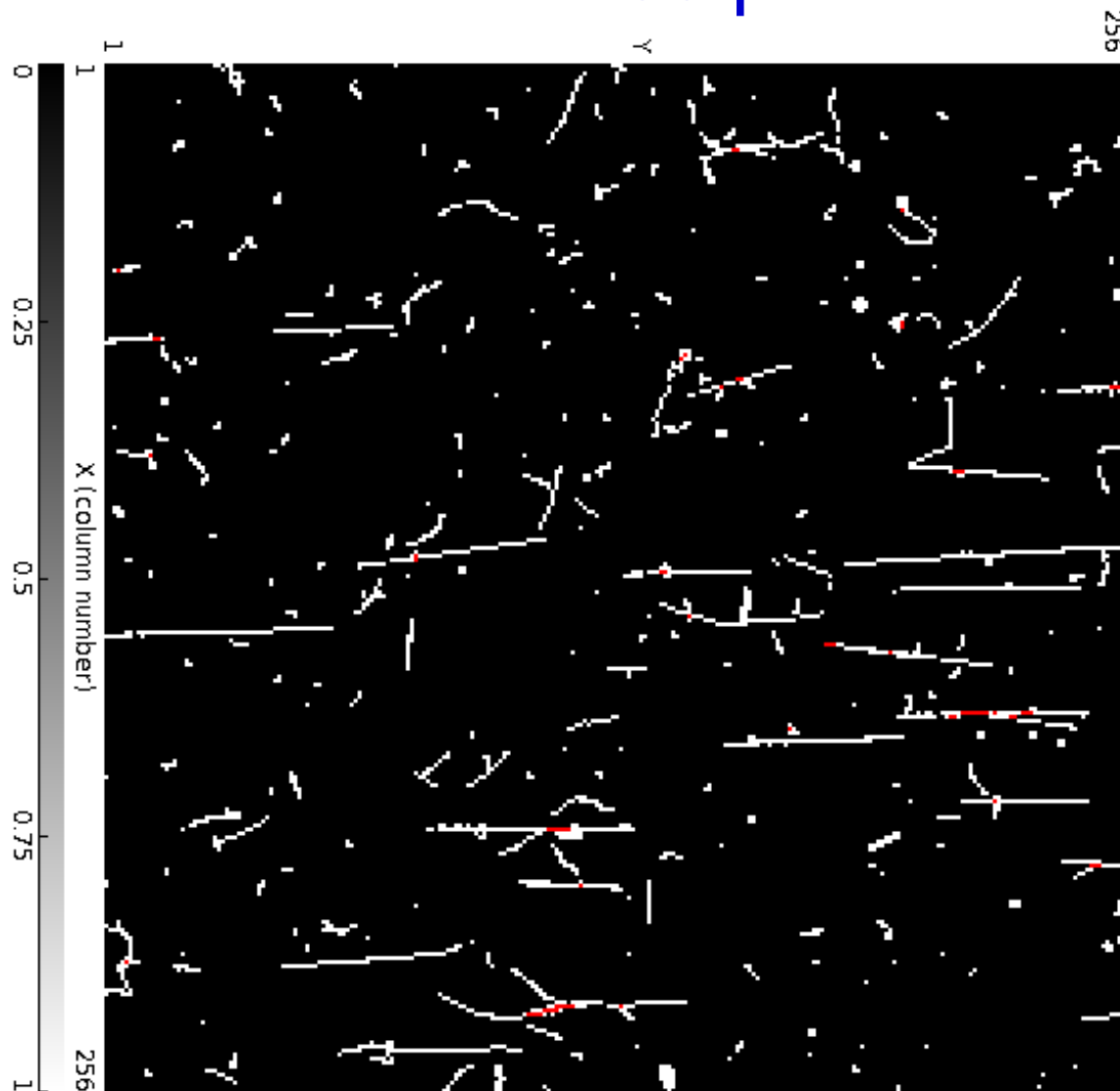
ATLAS-MPX LOCATIONS



MPX01	between ID and JM plug
MPX02	between ID, LARG and JM
MPX03	between LARG and LARG EC
MPX04	between FCAL and JT
MPX05	between LARG and JT wheel
MPX06	between LARG and JT wheel
MPX07	top of TILECAL barrel
MPX08	top of TILECAL EXT. barrel
MPX09	corner between JF cyl. and hexagon
MPX10	cavern wall A or C side
MPX11	cavern wall USA side
MPX12	small wheel
MPX13	between ID and JM plug
MPX14	between ID, LARG and JM
MPX15	at the back of Lucid detector
MPX16	ATLAS-MPX rack in USA15

Side A

Medipix in ATLAS

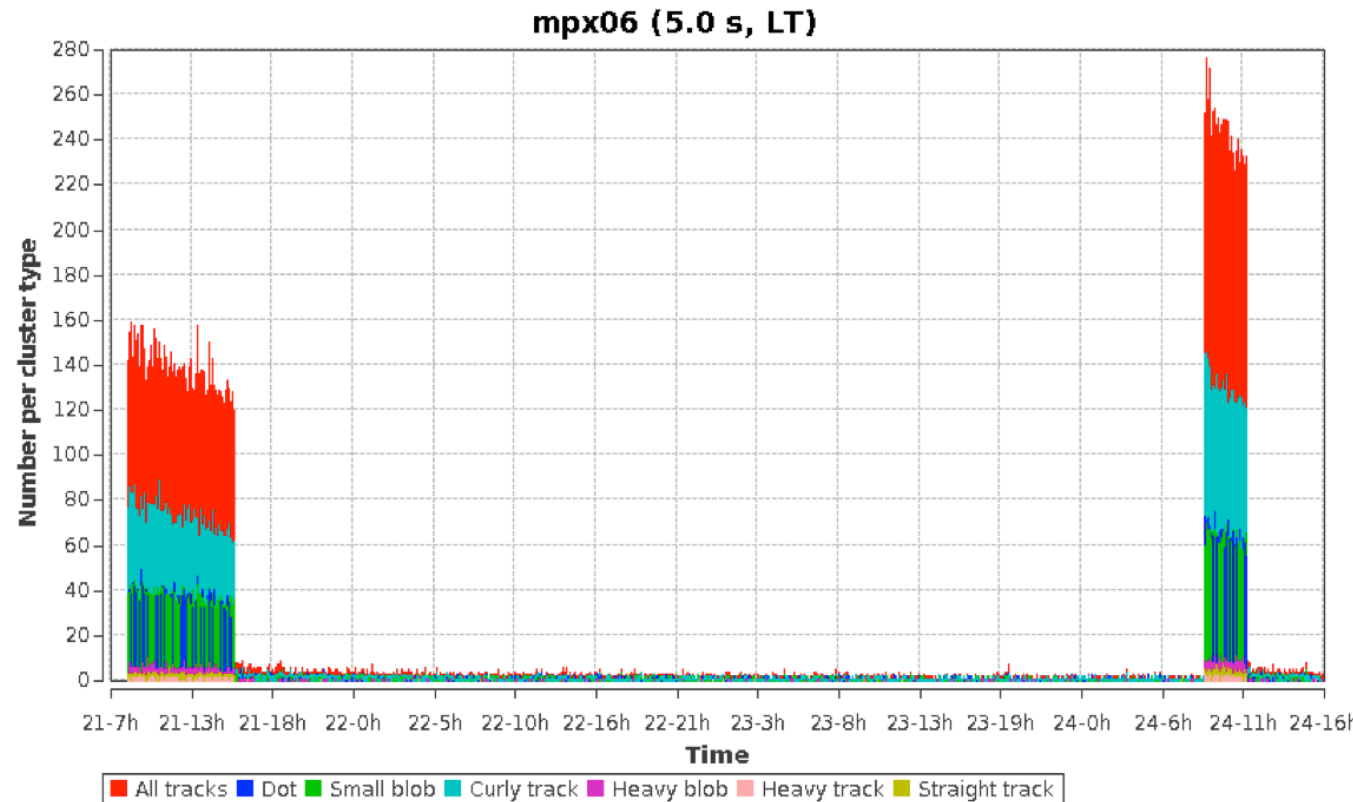


29 Sept 2011

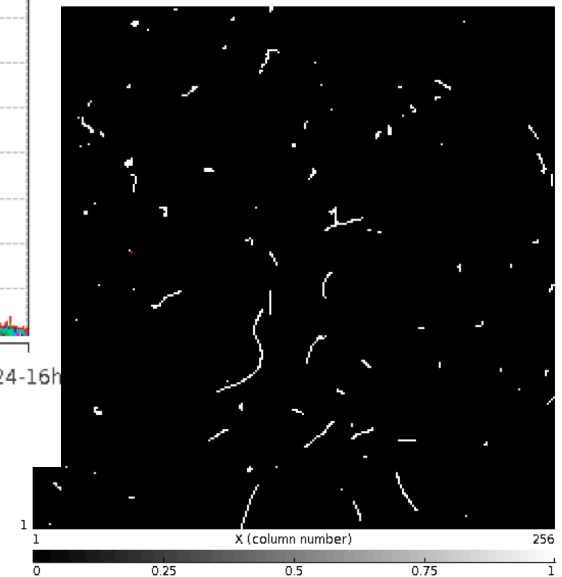
10s exposure

behind forward
muon wheel

Radiation in Atlas (preliminary)



example of recording
one station
21-24 June 2011



note decay of background after collision period

heavy tracks only during collisions

5s 91 clusters
13 $\mu\text{Sv/h}$

'TIMEPIX' CHIP

MODIFICATION of MEDIPIX2 (2007)

CLOCK adjustable up to 100 MHz in EACH PIXEL

newly added operational modes:

ENCODING of ARRIVAL TIME of PULSE

ENCODING TOTAL 'TIME OVER THRESHOLD'

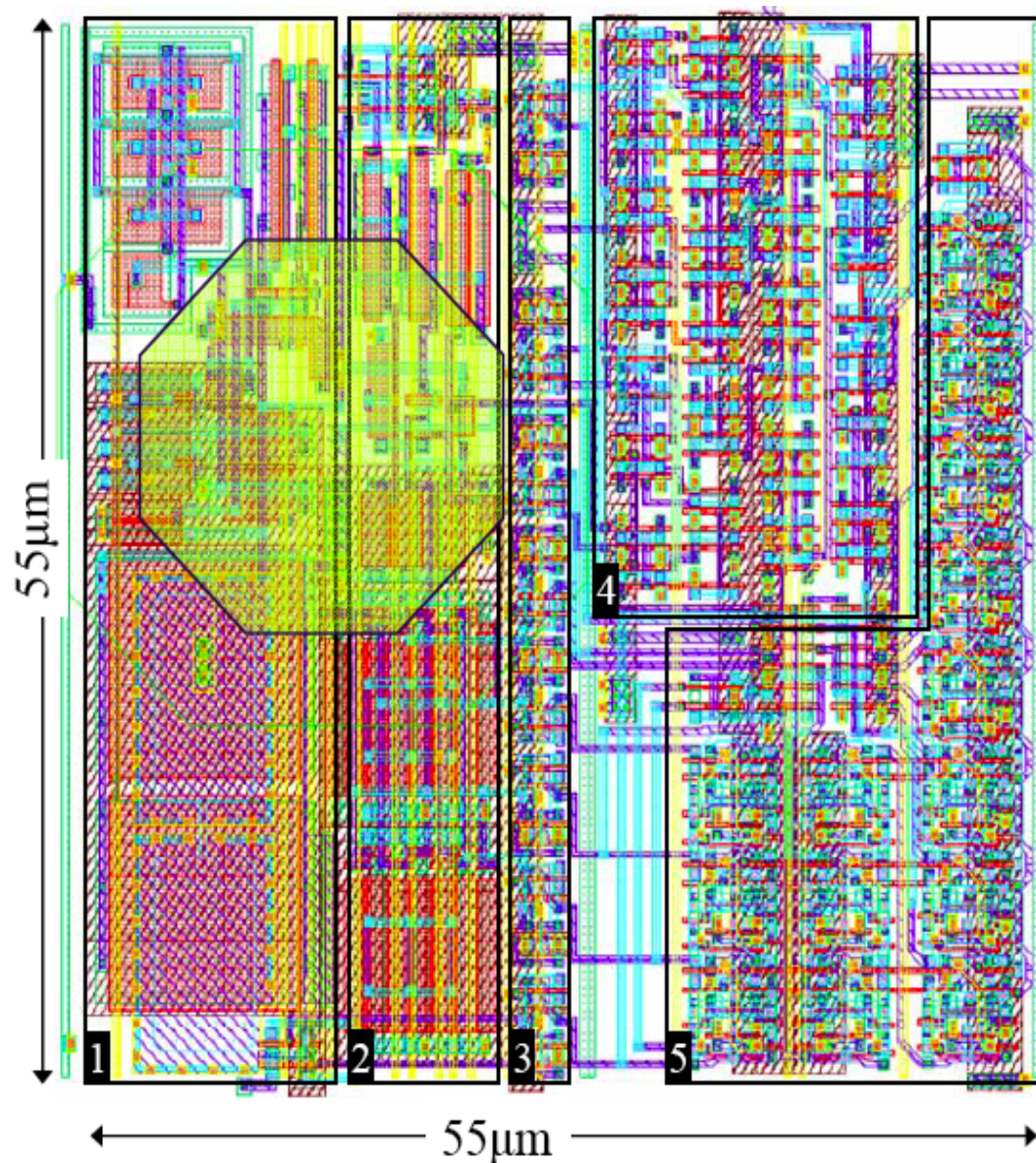
well adapted to dosimetry via

measurement of energy deposit in Si sensor

this readout chip was designed for **GASEOUS TPC** READOUT
as part of R&D for ILC by EUDET COLLABORATION
original ideas by Jan Visschers/NIKHEF and Xavier Llopart/CERN



TIMEPIX CELL LAYOUT

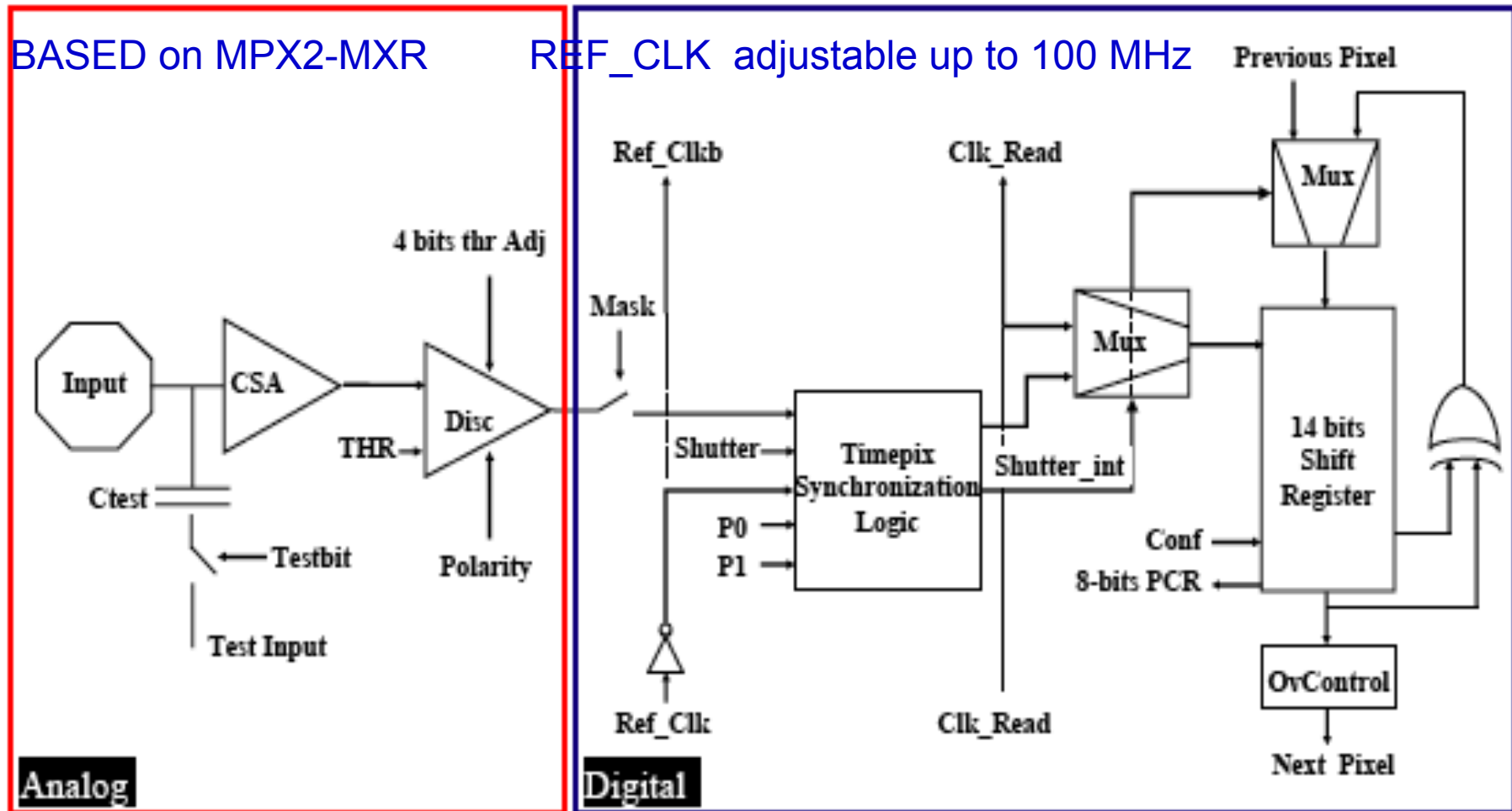


DESIGNER
Xavier LLOPART
CERN 2007
PhD Thesis p. 107

1. PREAMPLIFIER CSA
2. THRESHOLD, 4-BIT TUNING
3. 8-BIT CONFIG REGISTER
4. REF_CLK & SYNCHR LOGIC
5. 14-BIT COUNTER

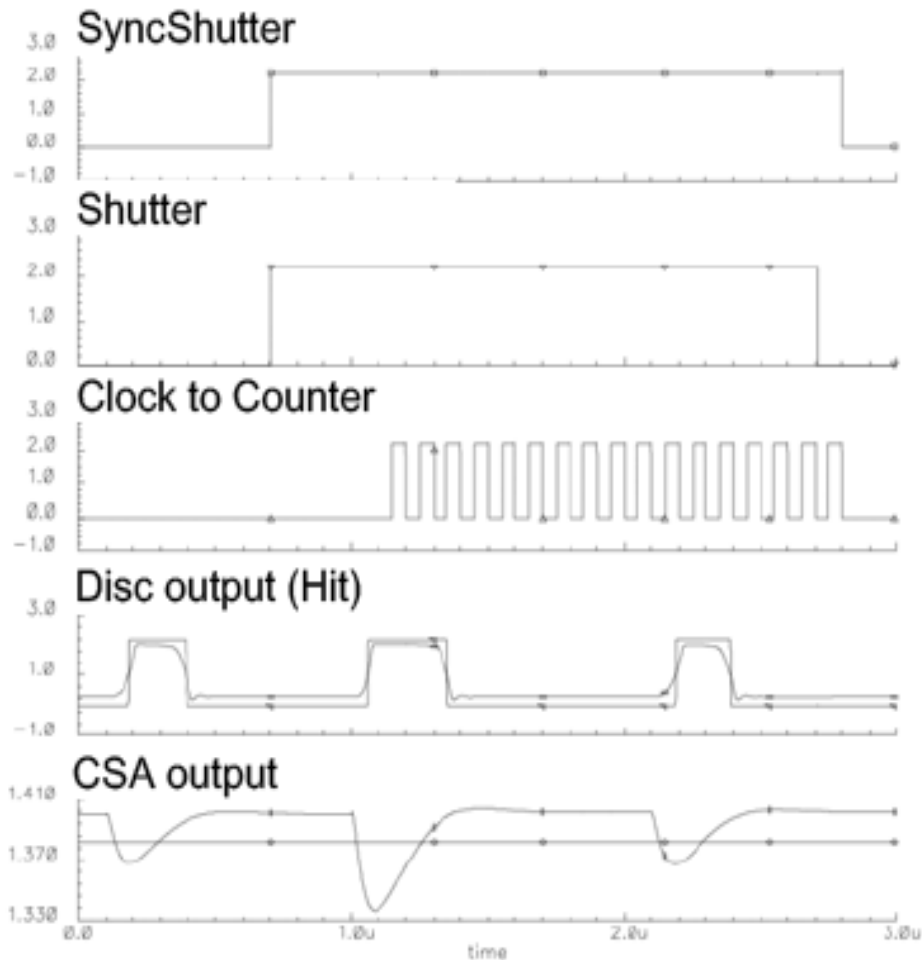
includes Time-Over-Threshold
amplitude digitizer in each pixel

TIMEPIX schematic diagram

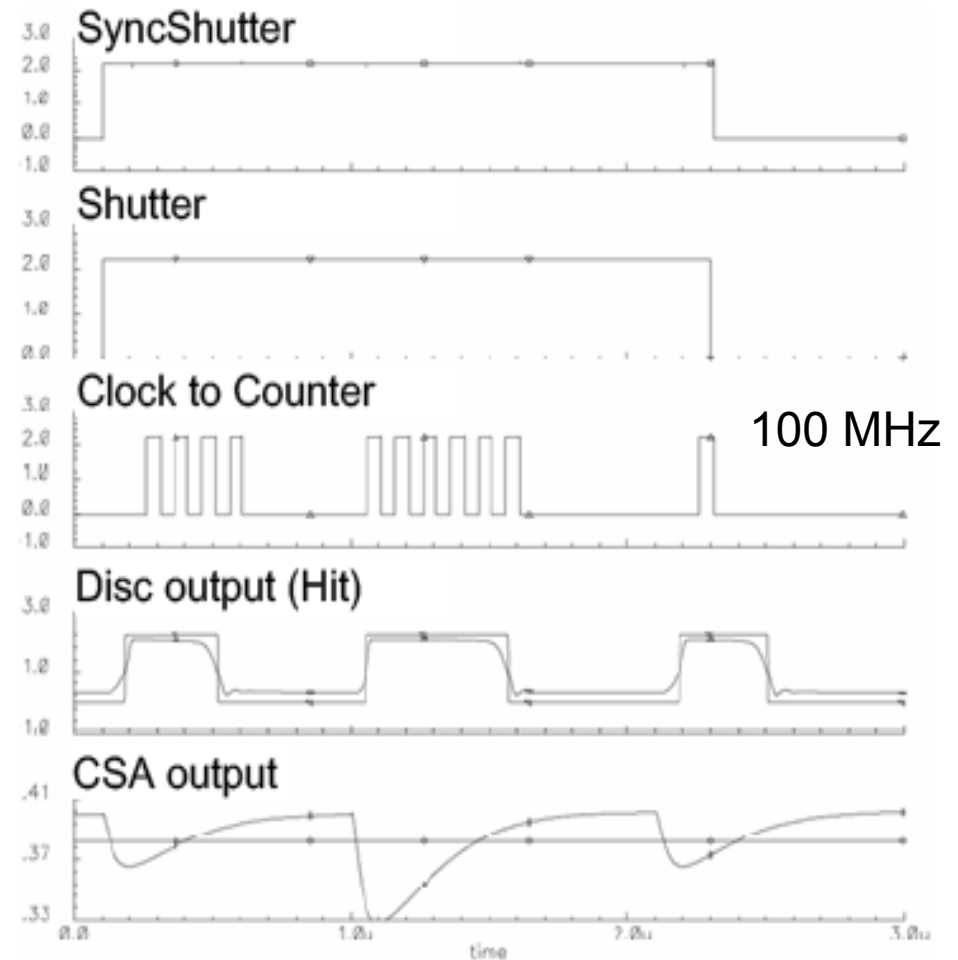


TIME-OVER-THRESHOLD, analog signal encoding in each pixel
NEEDS CLOCK DISTRIBUTION ALL-OVER MATRIX

TIMEPIX OPERATION

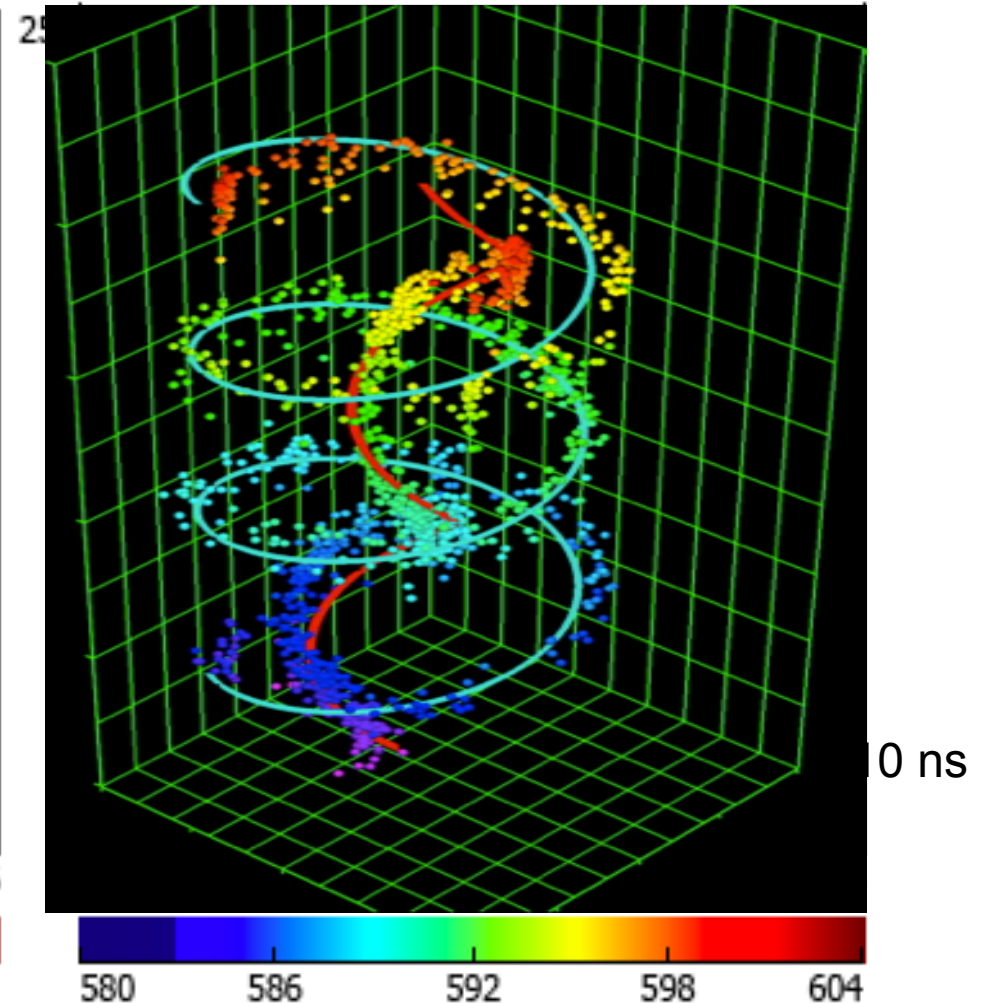
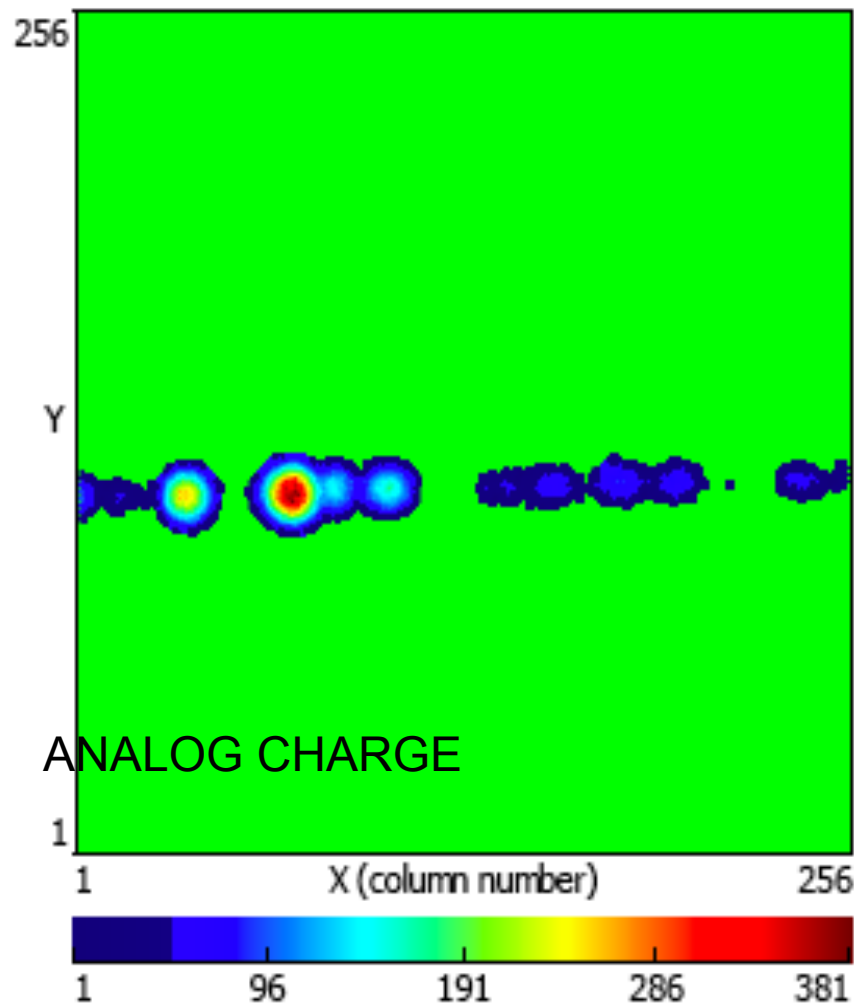


MODE : ARRIVAL
TIME



MODE : TOT 'TIME over THRESHOLD'

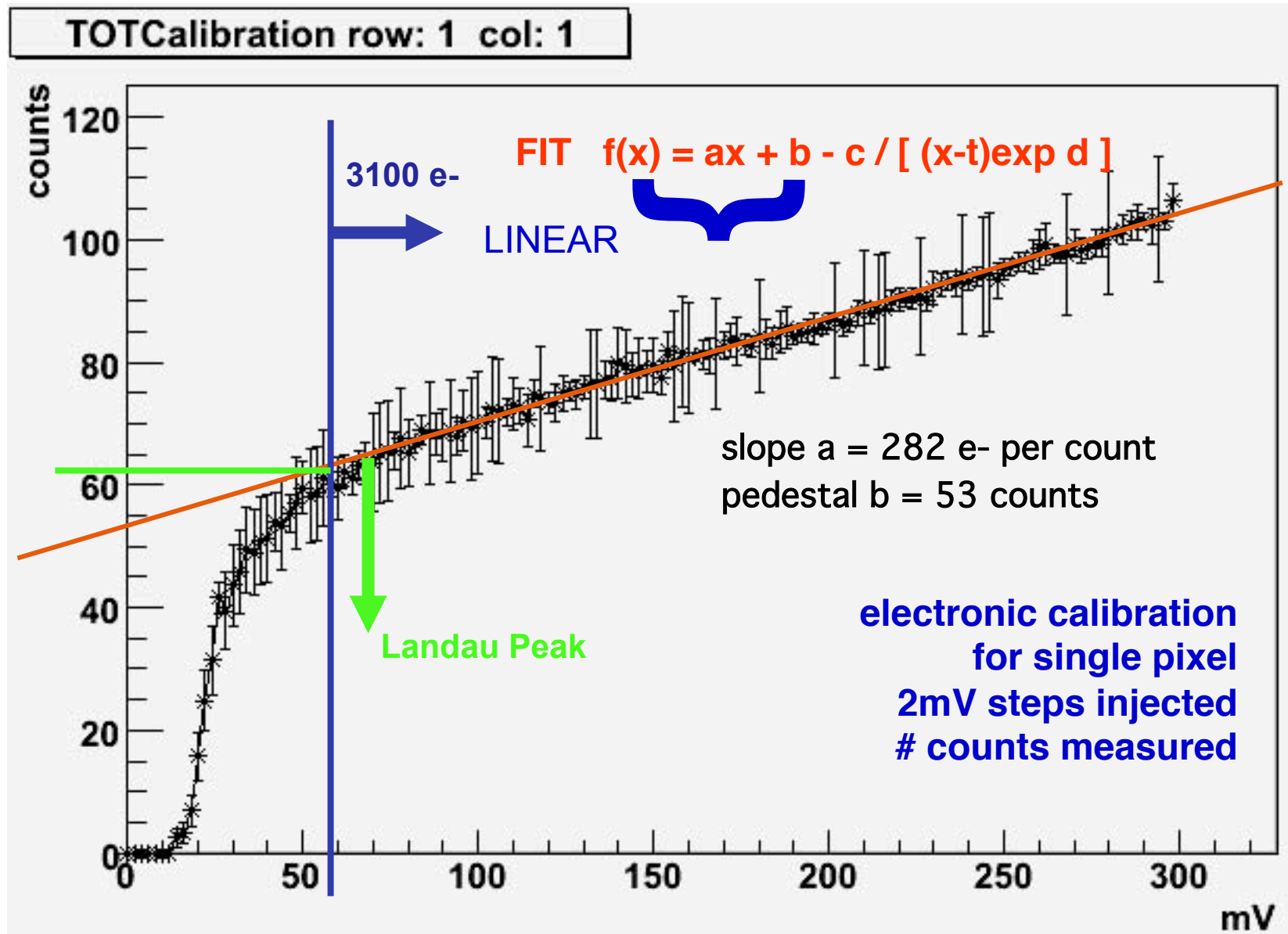
TIMEPIX + GEM in DESY e⁻ BEAM



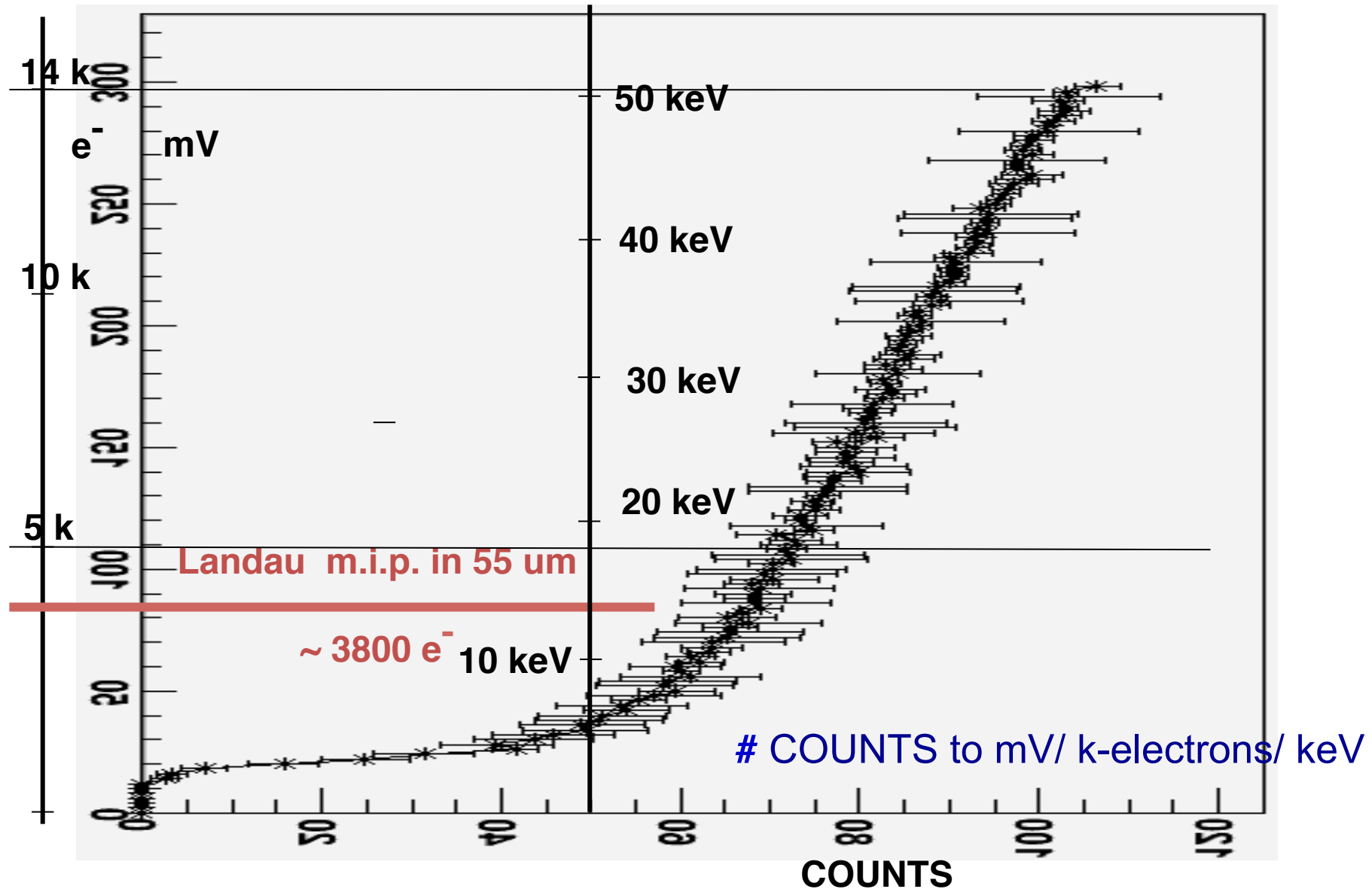
SIMULTANEOUS MIXED : TOT-MODE & ARRIVAL-TIME MODE

vdGraaf et al. NIM A628(2011)27-30

Typical pixel calibration TOT

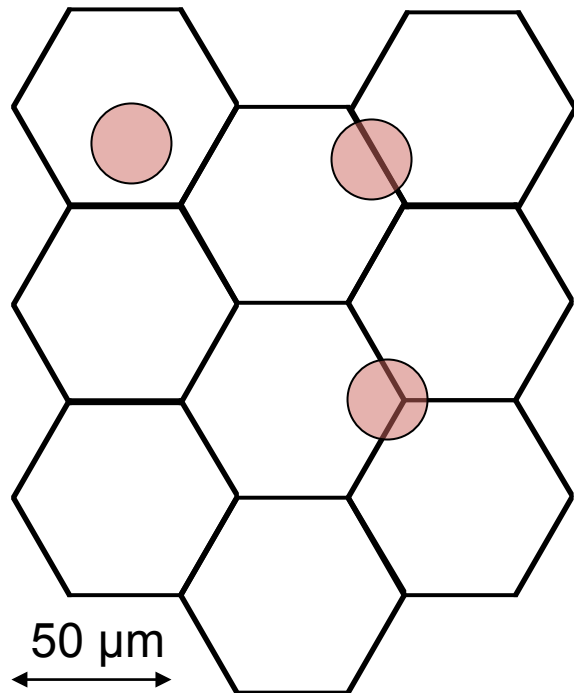


TIMEPIX TOT to mV CONVERSION



HEXAGONAL PIXEL GEOMETRY

ENERGY DEPOSIT is most often DISTRIBUTED
SUMMING of ENERGY needed for Spectrometry
in this case 6 equivalent neighbours, instead of 4
but 'never' quadruple hits



SINGLE/DOUBLE/TRIPLE HITS
MANY FACTORS ENLARGE 'HIT'

readout chip layout
and bump-bonding
more complicated
ADDITIONAL STUDY NEEDED

MEDIPIX3

ATTACKS CHARGE
SHARING

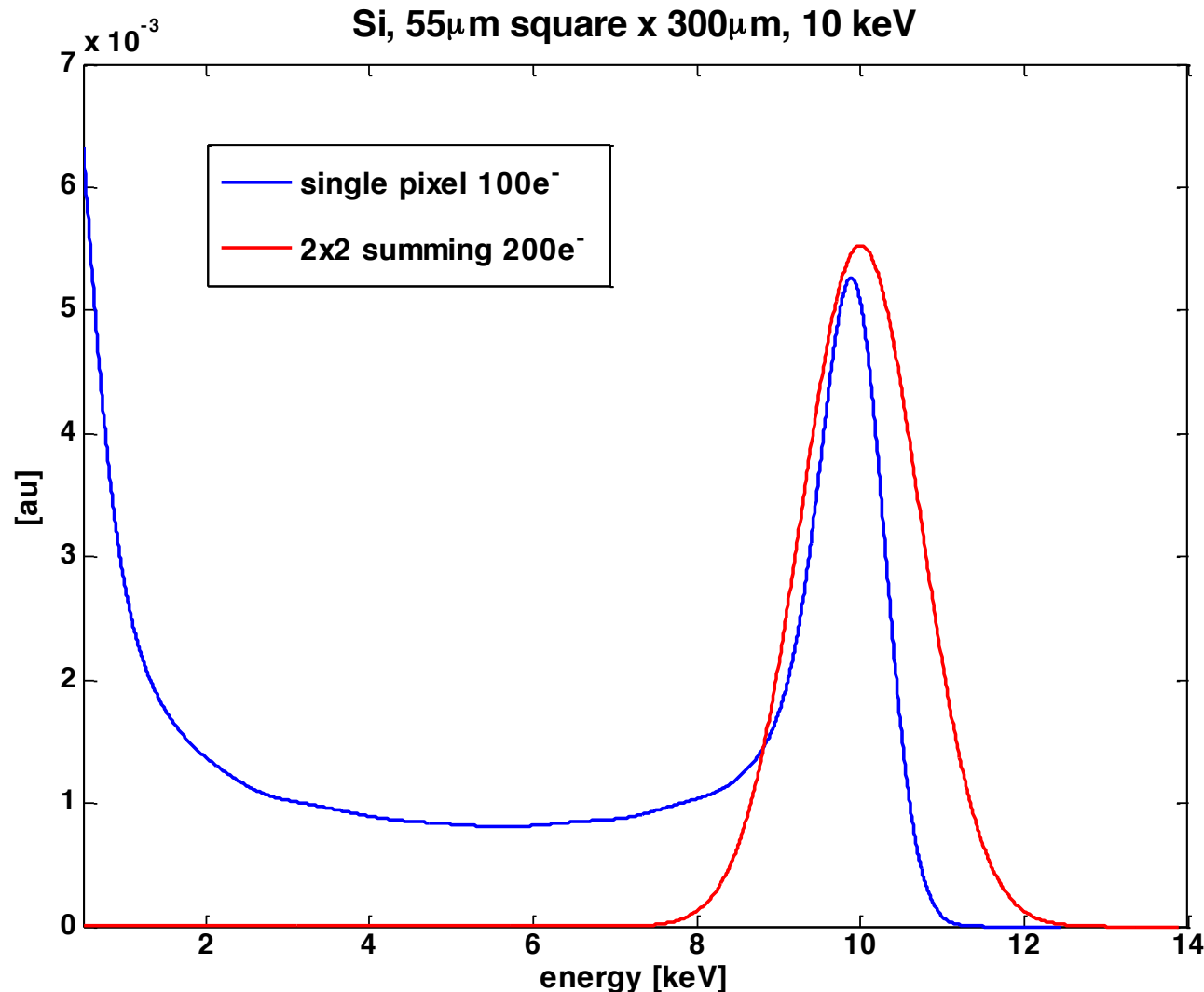
NEED for MORE TRANSISTORS



List of designed 'Medipix' chips

Medipix1 (1998)	1 μ m SACMOS, 64x64 pixels, 170x170 μ m ² PC / Frame based readout
Medipix2 (2001)	0.25 μ m CMOS, 256x256 pixels, 55x55 μ m ² PC / Frame based readout
Timepix (2006)	0.25 μ m CMOS, 256x256 pixels, 55x55 μ m ² PC, ToT, ToA / Frame based readout
Medipix3 (2009)	0.13 μ m CMOS, 256x256 pixels, 55x55 μ m ² PC / Frame based readout Event by event charge reconstruction and allocation
Dosepix (2011)	0.13 μ m CMOS, 16x16 pixels, 220x220 μ m ² ToT, PC / Rolling shutter (programmable column readout) Event by event binning of energy spectra (16 digital thrs)
Timepix3 (2013)	0.13 μ m CMOS, 256x256 pixels, 55x55 μ m ² PC; ToT, ToA (simultaneous)/ Data driven readout
Smallpix	0.13 μ m CMOS, 512x512 pixels, 40x40 μ m ² (TBD) PC, iToT; ToA, ToT1 (simultaneous)/ Frame based (ZC) TSV compatible design
Clickpix prototype	65nm CMOS, 64x64 pixels, 25x25 μ m ² ToA, ToT1 (simultaneous)/ Frame based (ZC)

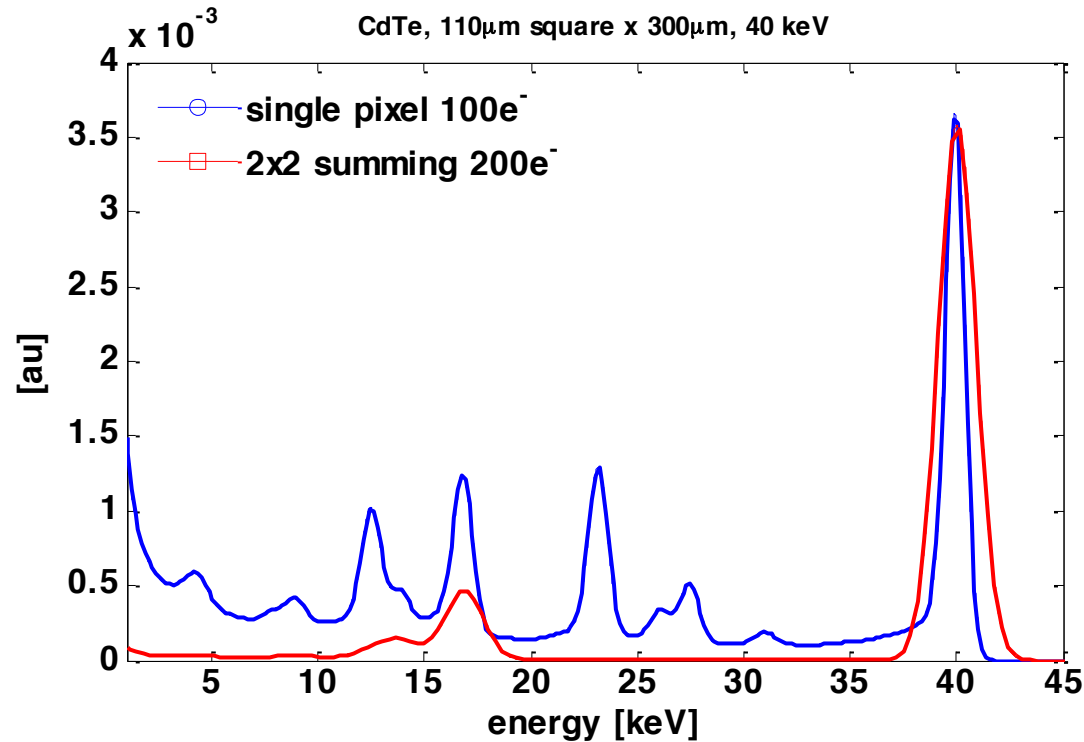
Motivation for the Medipix3 chip



- ***Simulated Data***
- ***Si 300 μm , 55 μm pixel***
- ***10keV monochromatic photon beam***
- ***In the new architecture charge sharing tail is eliminated***

Simulation: L. Tlustos

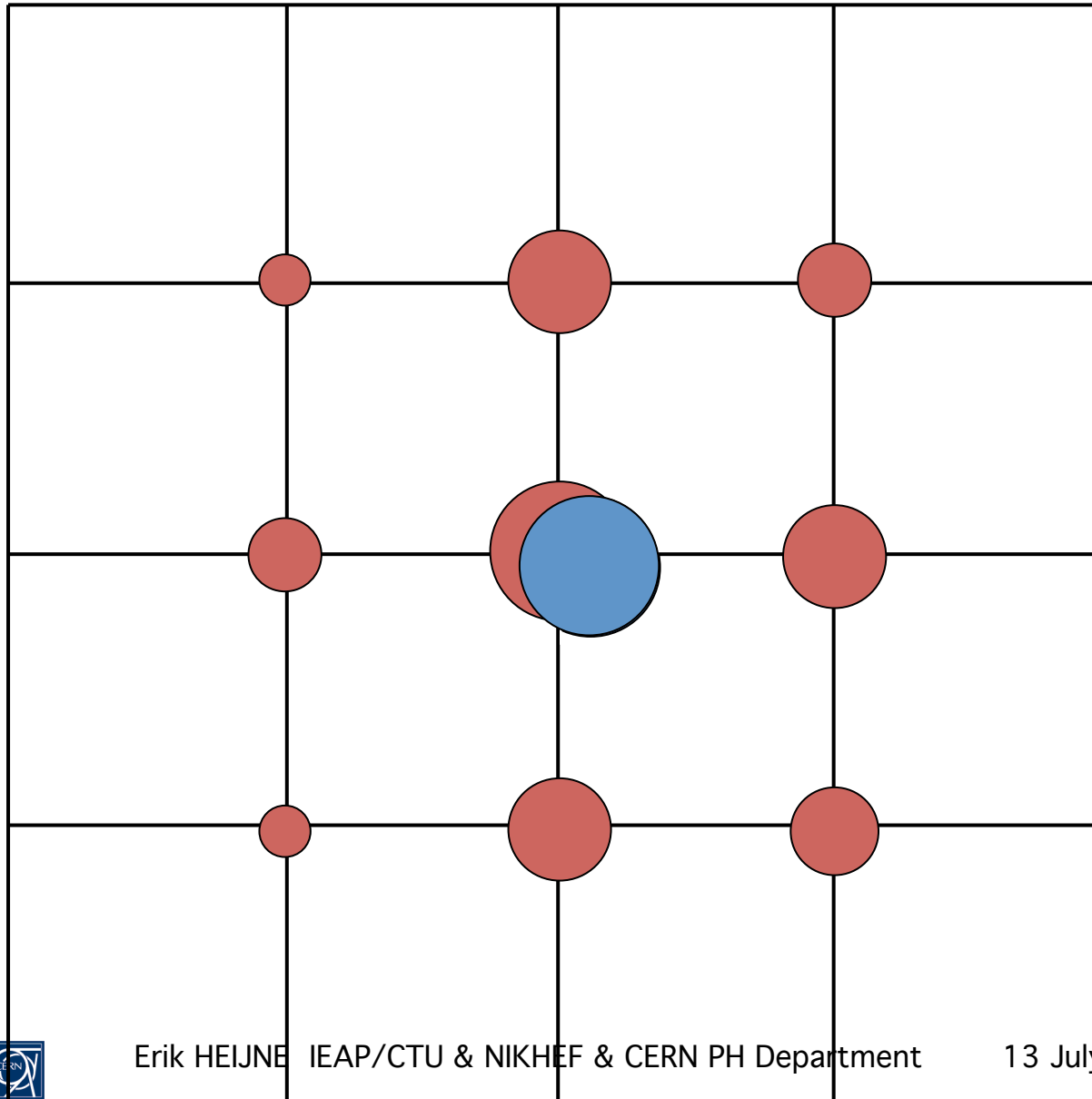
Motivation for the Medipix3 chip



- ***Simulated data***
- ***CdTe 300 μ m***
- ***110 μ m pixel pitch***
- ***40keV monochromatic beam***
- ***Fluorescence photons are included in charge sum if their deposition takes place within the volume of the pixels neighbouring the initial deposition***

Simulation: L. Tlustos

The algorithm for charge reconstruction and hit allocation: Charge Summing Mode



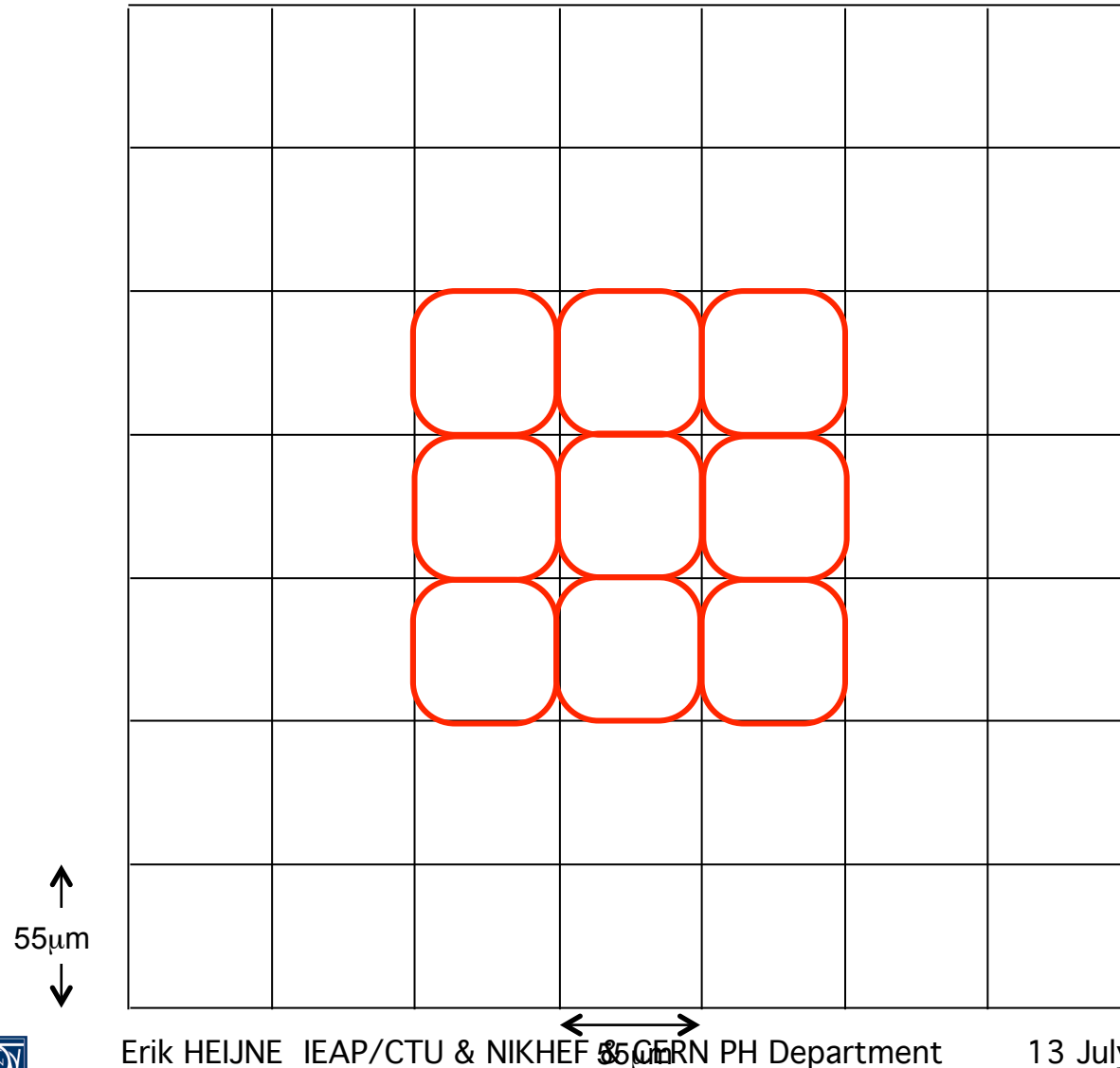
1. TH_0 is applied to the local signal

2. Arbitration circuitry identifies the pixel with largest charge and suppresses the pixels with lower signal

3. In parallel, the charge has been reconstructed in the analog summing circuits

4. The pixel with highest charge checks the adjacent summing circuits to see if at least one of them exceeds TH_1

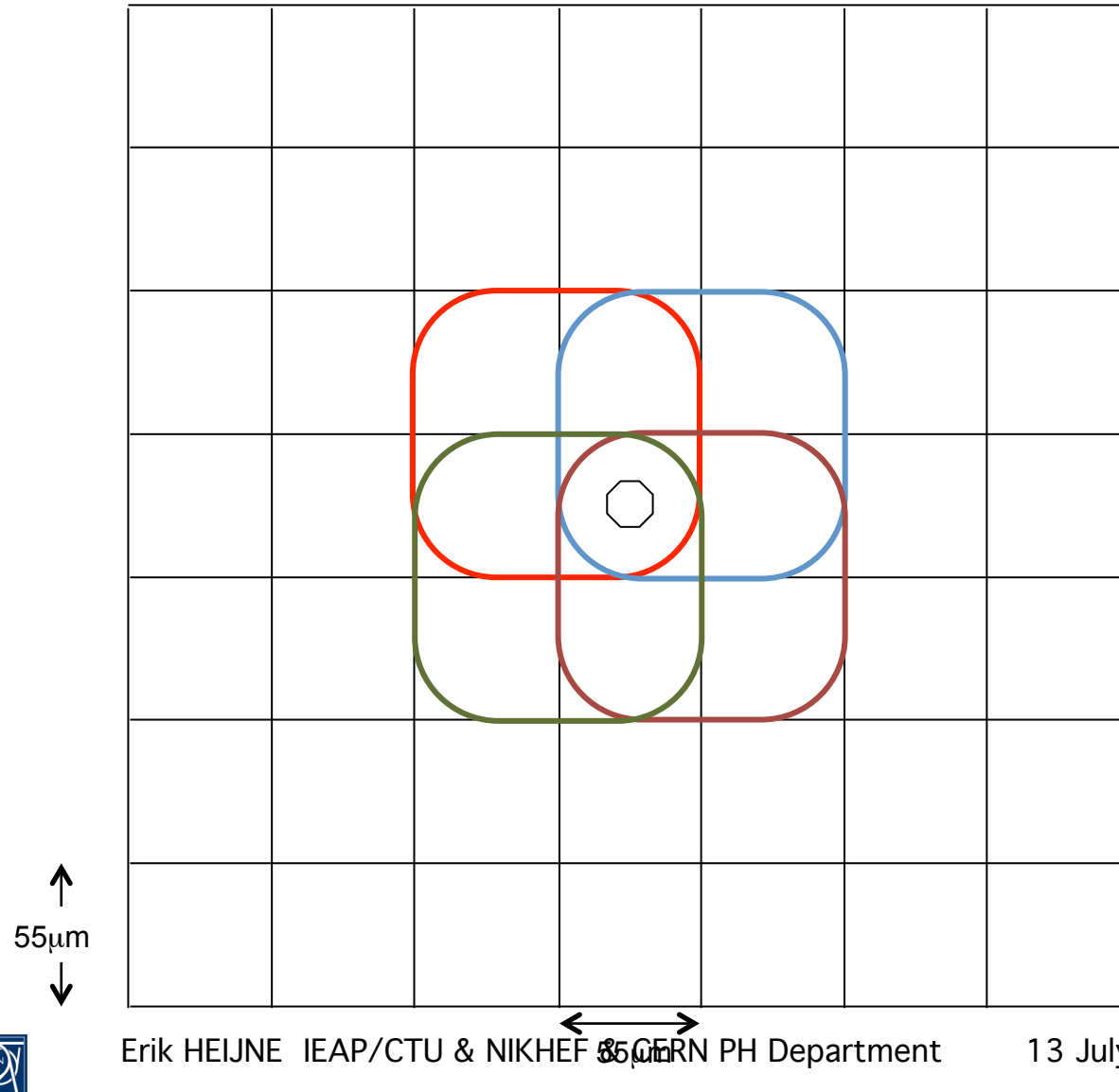
Fine pitch mode, Single Pixel Mode



- ***$55\mu\text{m}$ pixel pitch***
- ***2 thresholds/pixel***
- ***2 counters***

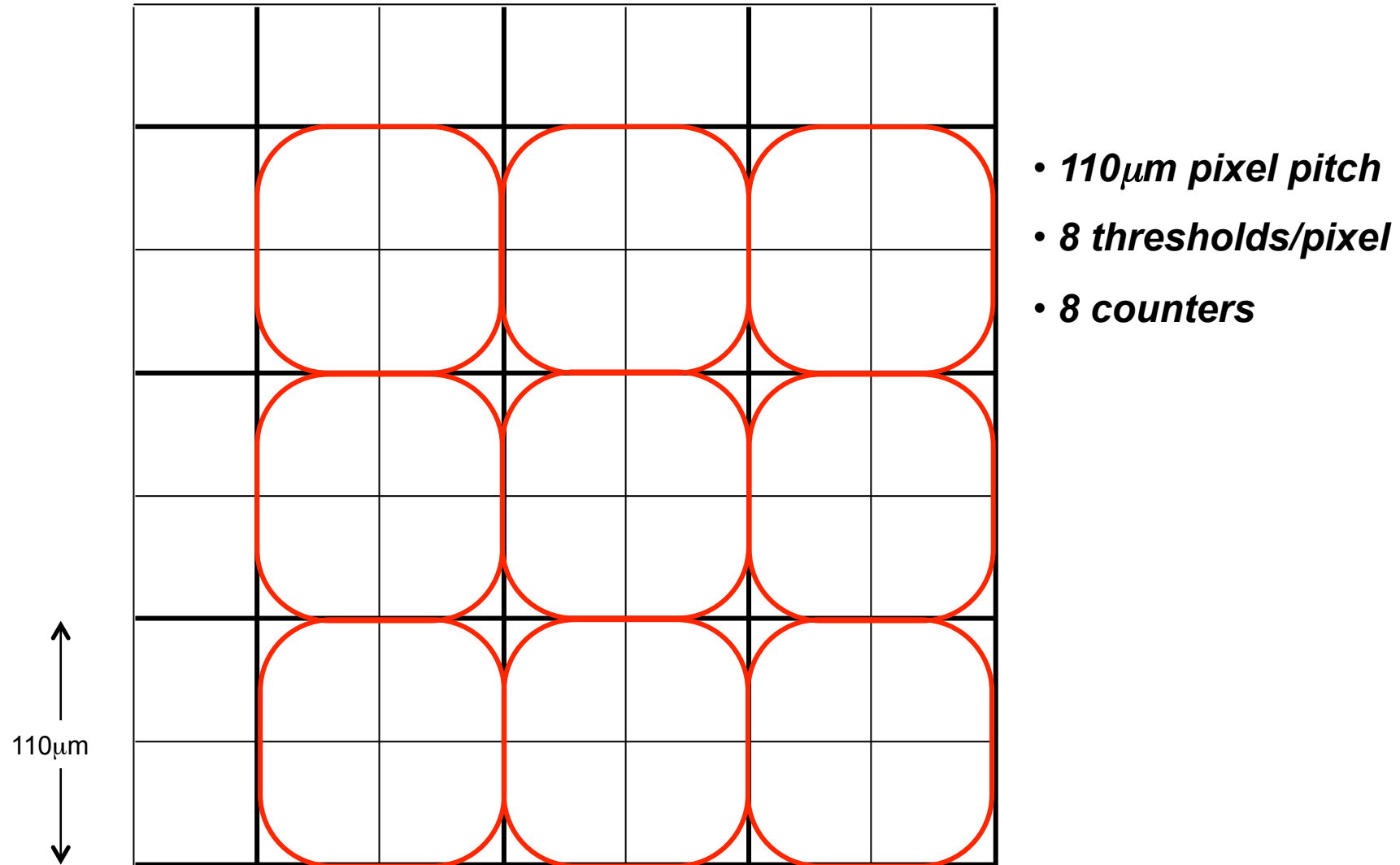
- ***Pixels work independently from one another***

Fine pitch mode, Charge Summing Mode

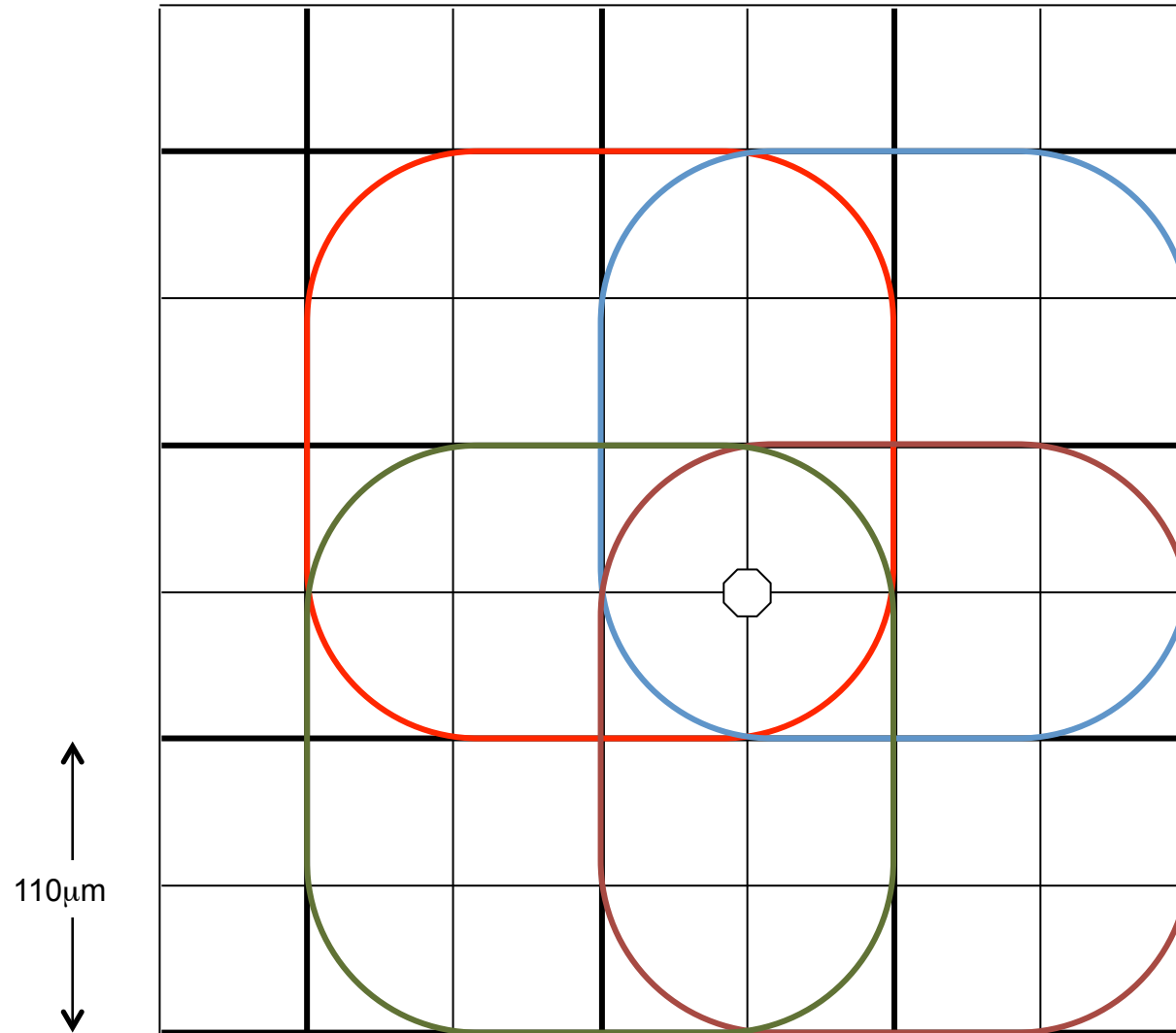


- *55μm pixel pitch*
- *Reconstruction over overlapping 110μm x 110μm areas*
- *2 thresholds/pixel (1 for local charge/1 reconstructed charge)*
- *2 counters*
- *Advantage of small pixels without disadvantage of charge sharing*

Spectroscopic mode, Single Pixel Mode



Spectroscopic mode, Charge Summing Mode



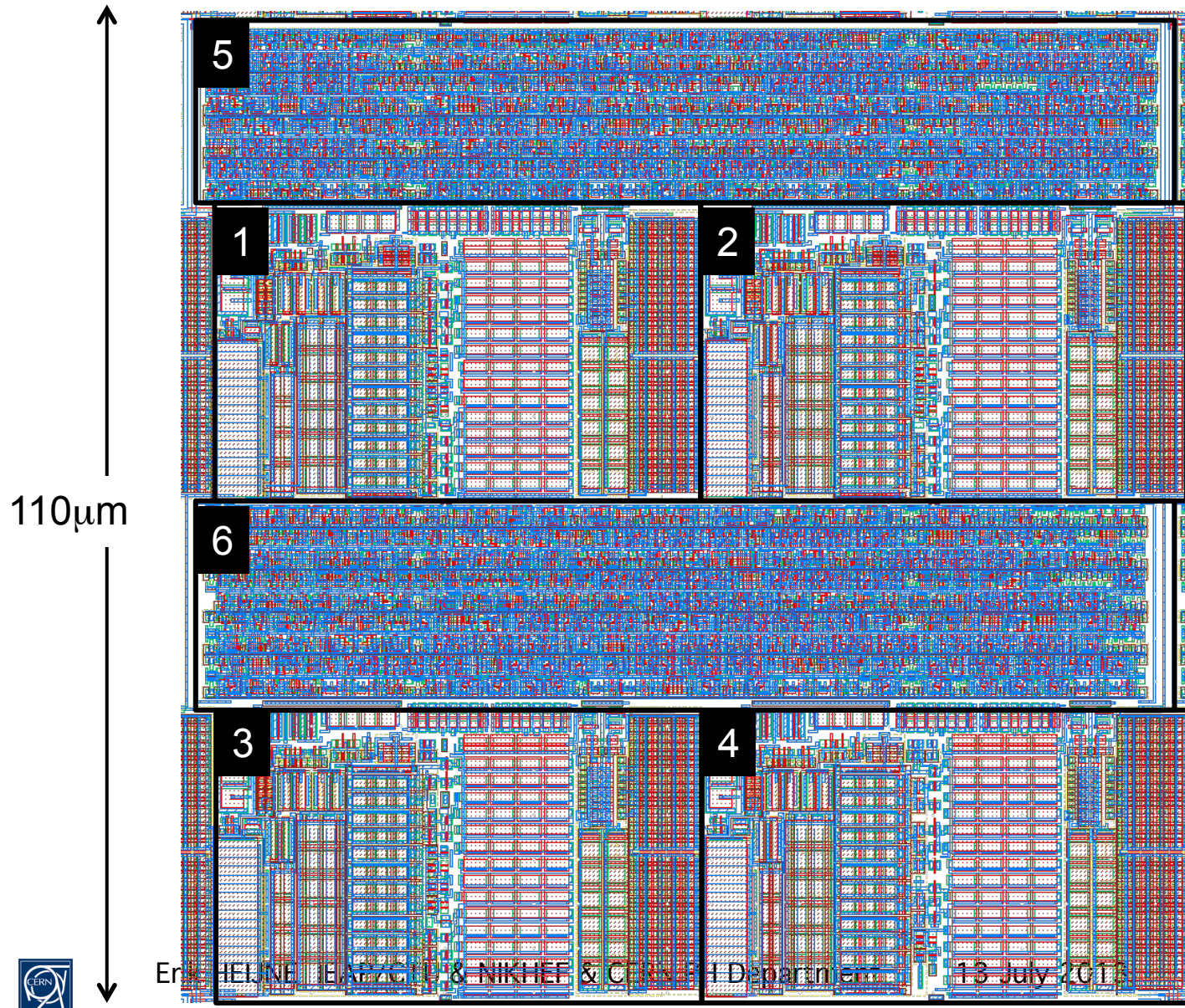
- **110μm pixel pitch**
- **Reconstruction over 220μm x 220μm area**
- **8 thresholds/pixel (4 for local charge/4 reconstructed charge)**

- **8 counters**

Common to all configurations:

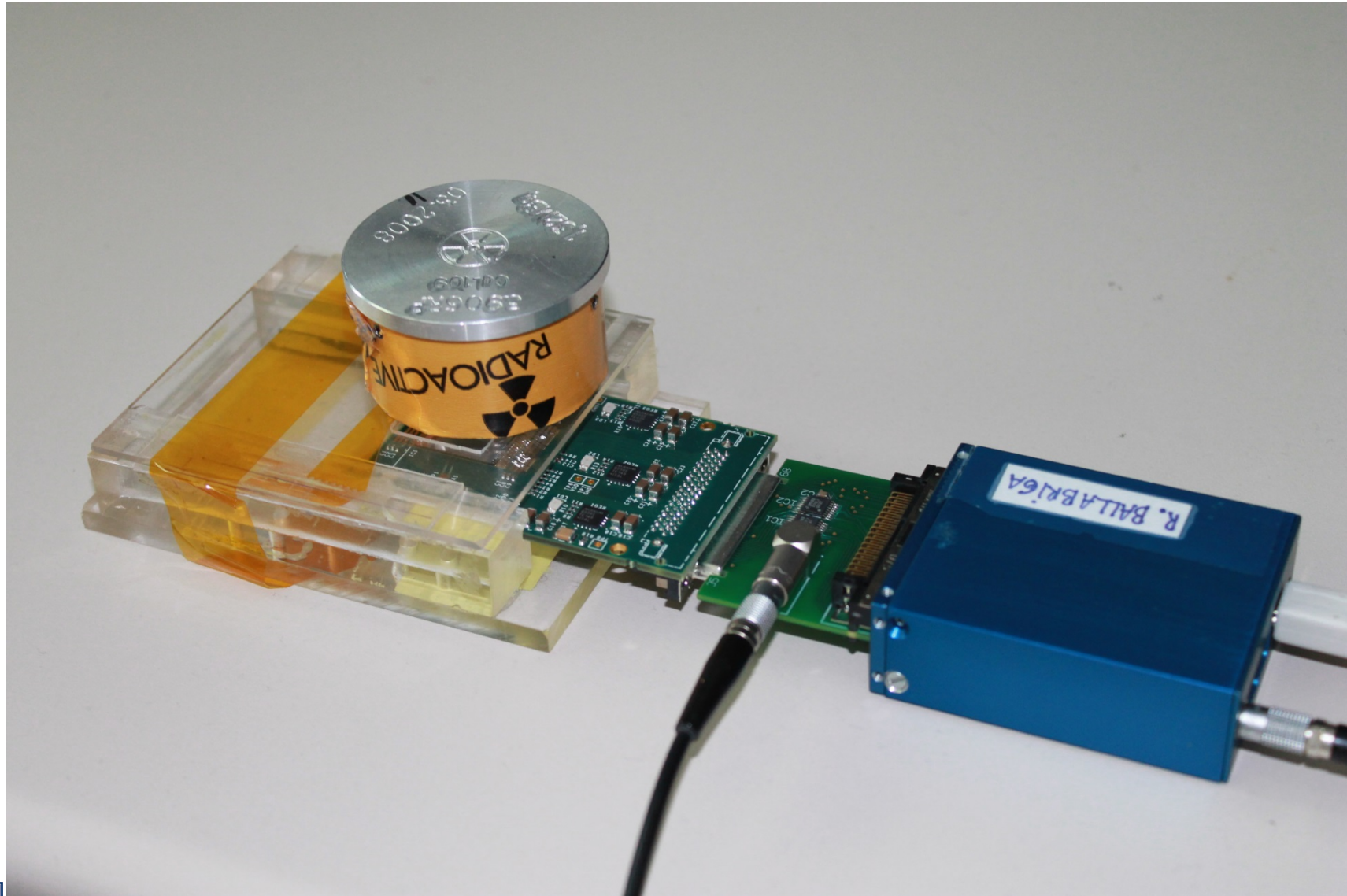
- **4 selectable gain mode**
- **Possibility of Continuous Acquisition/Readout**

Medipix3RX Pixel layout

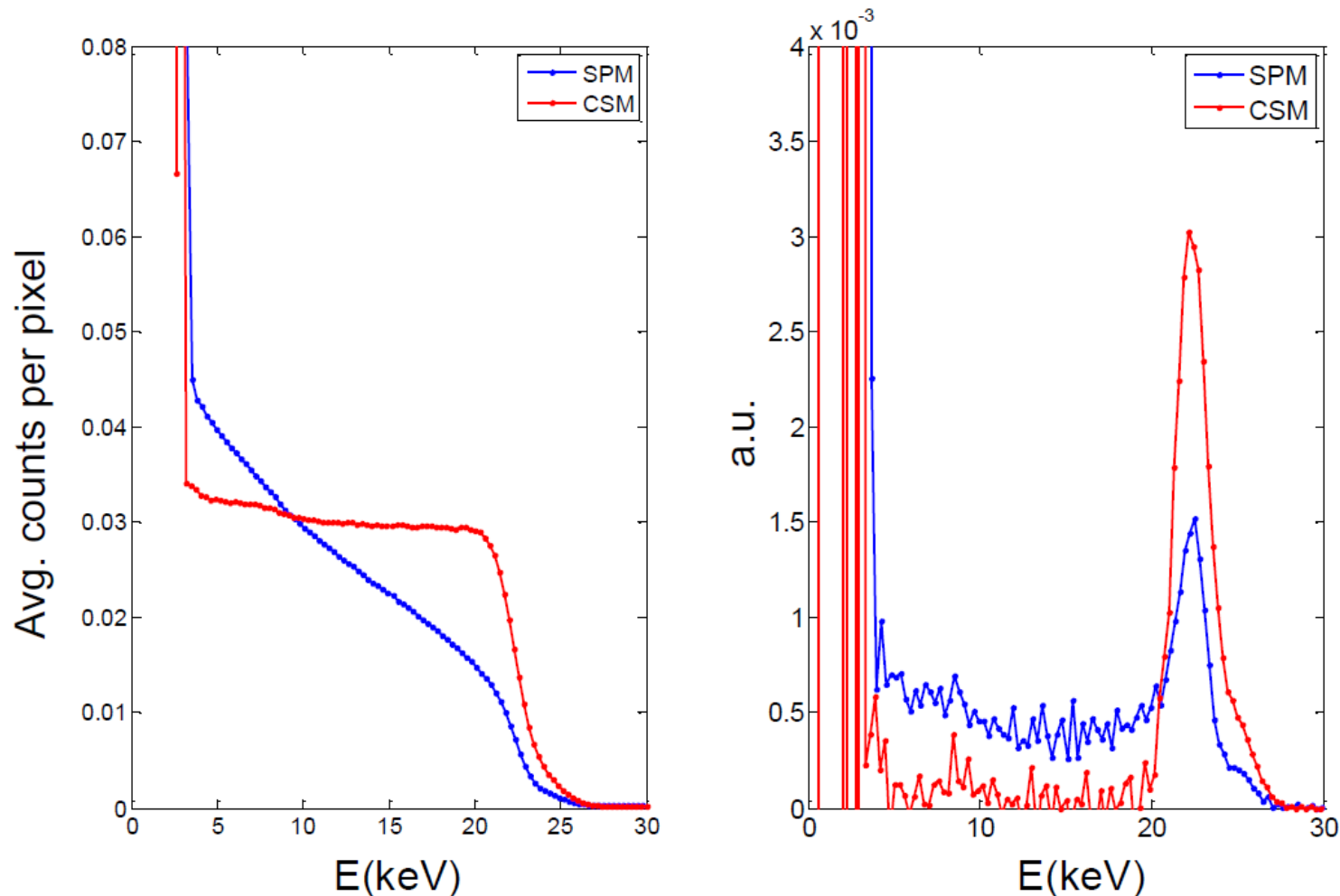


0.13µm
CMOS
8 metal layers

Measurements using Radioactive Sources



Measurement of ^{109}Cd energy spectrum



Measurement in HGM @ very low flux conditions

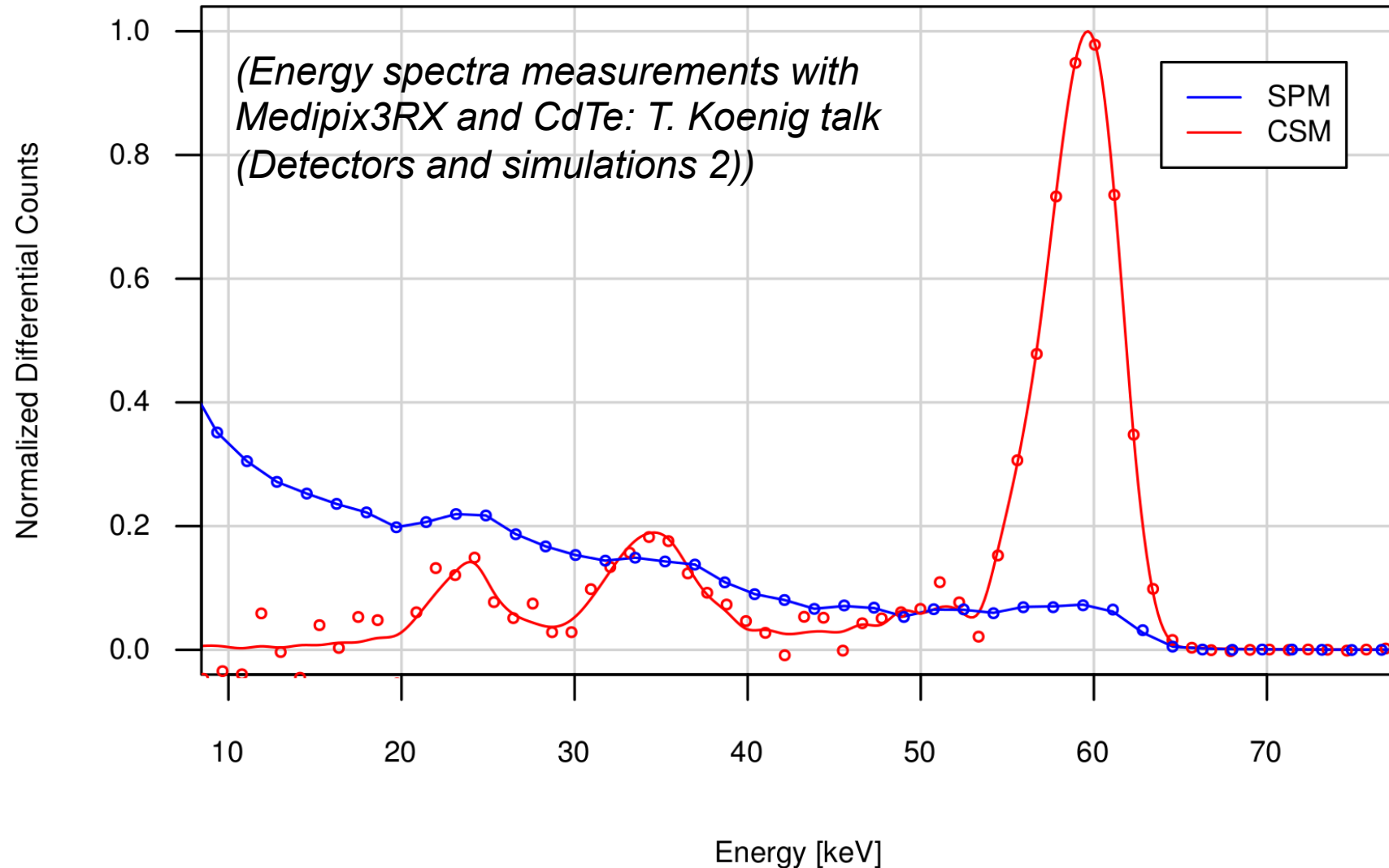
Only 4 pixels masked in the matrix

Raw data. No realignment in data

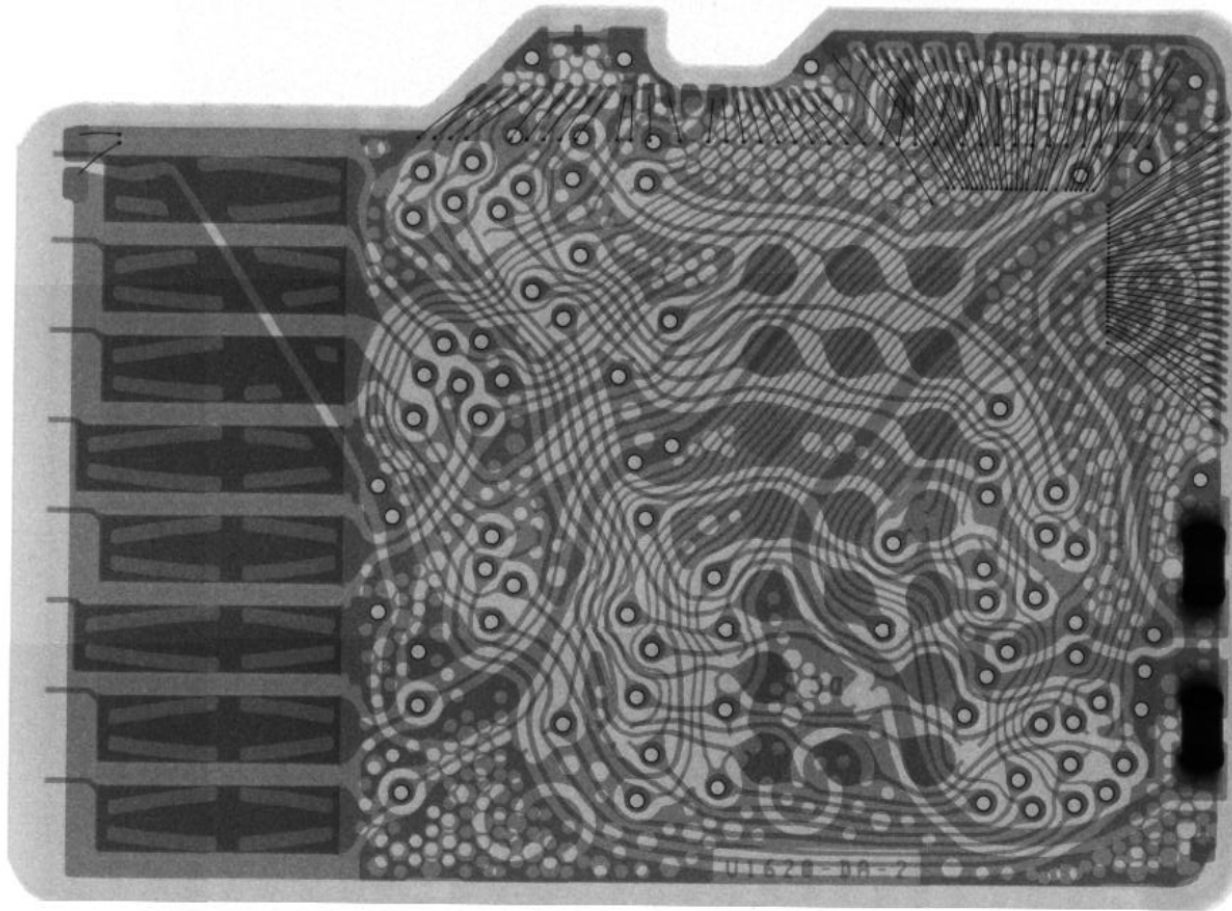
In Charge Summing Mode each photon is counted once



Measurements (60keV, 110 μ m pitch, 2mm CdTe)



Imaging a μ SD card in CSM



μ Sd card

4x3 tiles, magnification 3.2x

X-ray tube voltage: 30 kVp, Tube current: 100 μ A, 1mm Al filtering, 5s acquisition



Medipix3RX electrical characterization: measurements obtained (chip with sensor)

	SPM	CSM	Units
Gain (SHGM)	25	55	e^- /DAC step
ENC (SHGM)	75	150	e^- r.m.s.
Threshold dispersion (SHGM)	37.5	85.5	e^- r.m.s.
Peaking time	120	120	ns
Power consumption	0.78	1	W/chip
Dead time/channel*	0.22/4.5	2.94/0.34	μ s/MHz
Count rate*	375	28	Mc/mm ² s

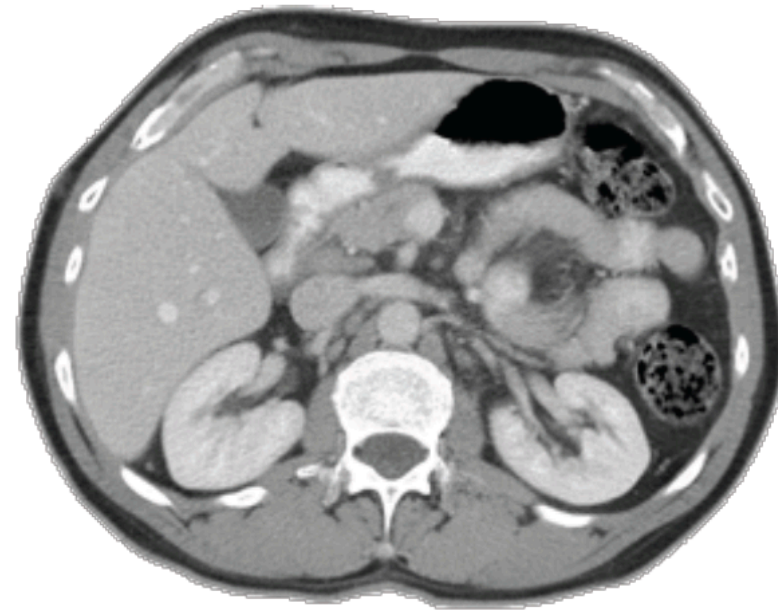
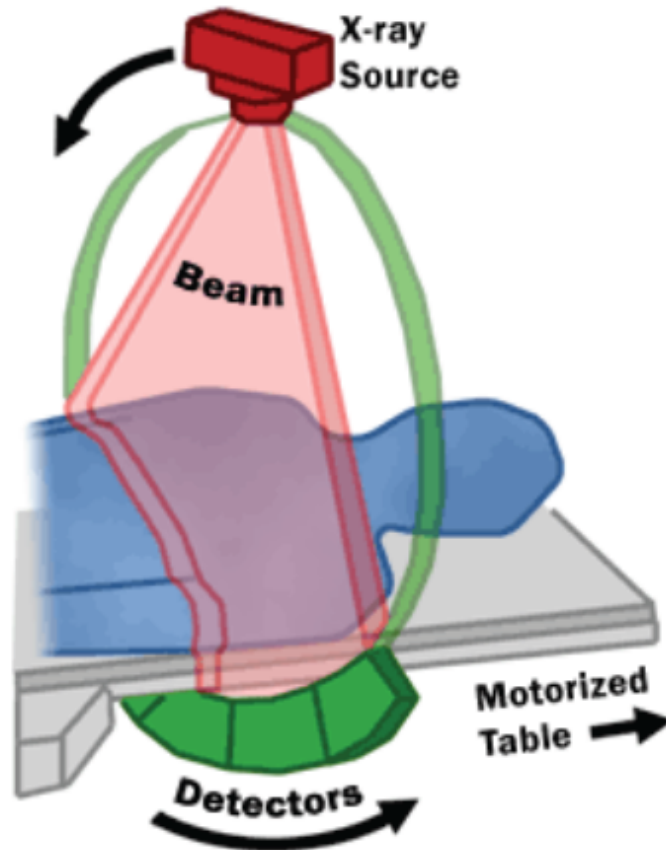
*Measurements with CdTe, 2mm thick at 110 μ m pitch (paralizable model fit)

MEDIPIX / TIMEPIX APPLICATIONS



CT Imaging

CT is now one of the most used imaging techniques



Cross-sectional image of abdomen
many slices combined into 3D image

Images from : <http://www.fda.gov/radiation-emittingproducts>

CT Imaging

example:

CT allows 3D reconstruction of part of a mouse



Medipix3 for small-animal CT scanning



Anthony Butler



Medipix3 for small-animal CT scanning

Test Objects: internal presentation

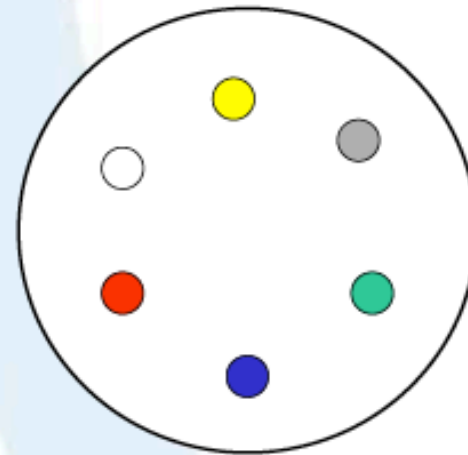
Mouse set in Perspex

- Gold in chest cavity



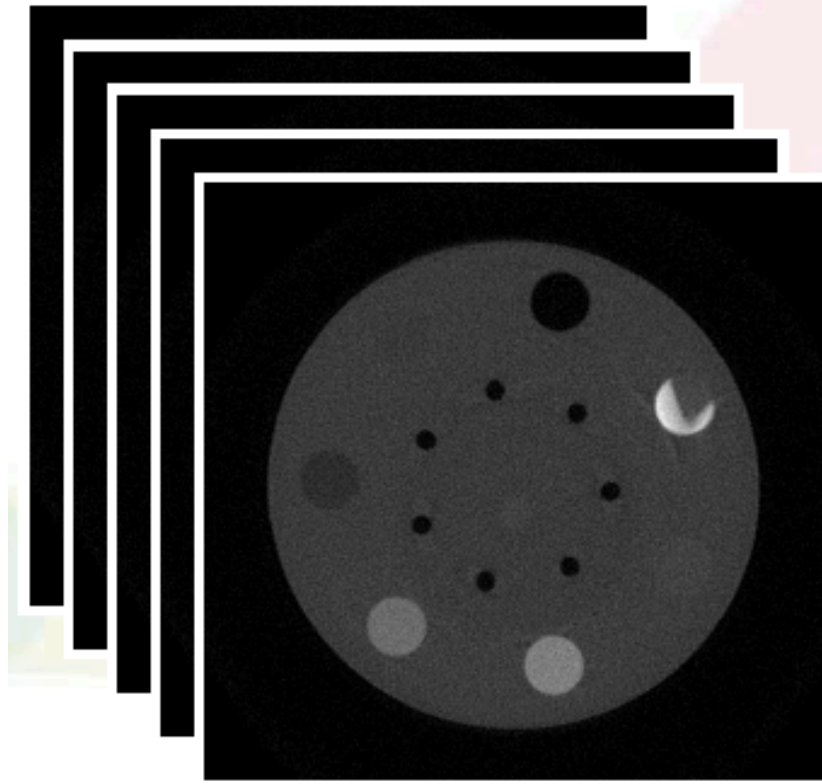
Perspex phantom

- 2cm diameter rod
- Contains air, fat, water, Ca, Au, I

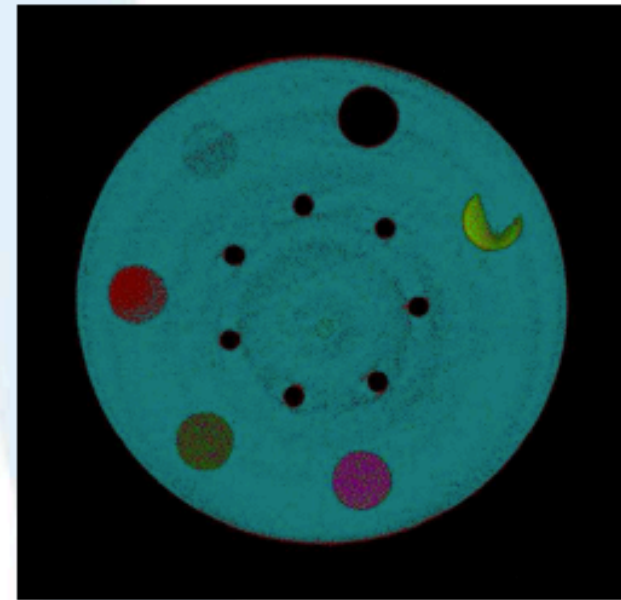


Medipix3.1 for small-animal CT scanning

GaAs sensor: Multi-material Decomposition now possible
for human X-ray energy one needs heavier sensor material



10-100 keV



Red - Fat

Cyan - Water

Purple - Iodine

Green - Calcium

Yellow - Gold

CT Imaging

Following slide is a comparison of Computed Tomography images of a mouse head taken under identical circumstances between a conventional X-ray detector the Medipix3 chip combined with a Si sensor.

The improvement of clarity in the Medipix3 image is obvious even to the untrained observer.

The dose used for both measurements was about 170 mGy/cm.

from PhD Thesis: Jördis Lübke,
"Entwicklung eines iterativen Rekonstruktionsverfahrens
für einen Medipix3-Computertomographen",
Dissertation University of Freiburg 2011

Comparison of usual detector and Medipix3+Si

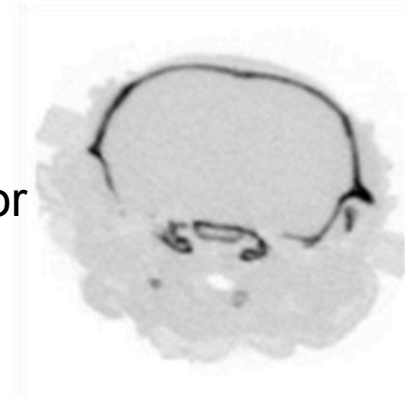
Micro-CT

coronal:

sagittal:

transaxial:

Usual detector



6mm

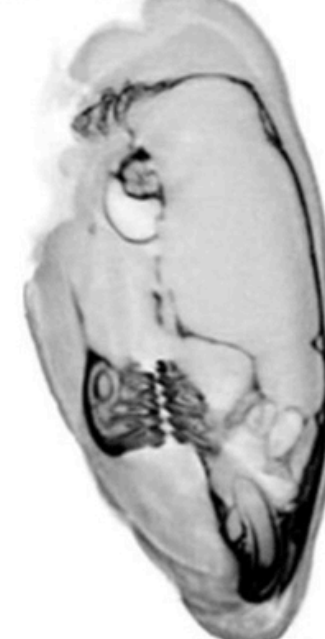
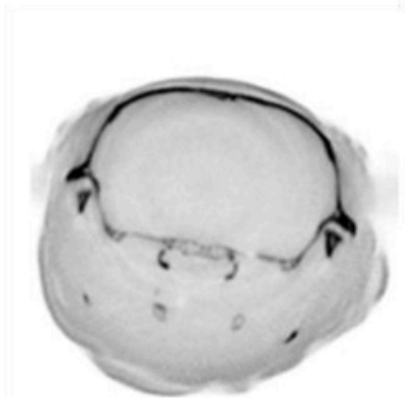
Medipix3-CT

coronal:

sagittal:

transaxial:

Medipix3



6mm



Erik HEIJNE

}



Human Medical Imaging

CT needs detectors

with good stopping power for hard X-rays 50-150 keV

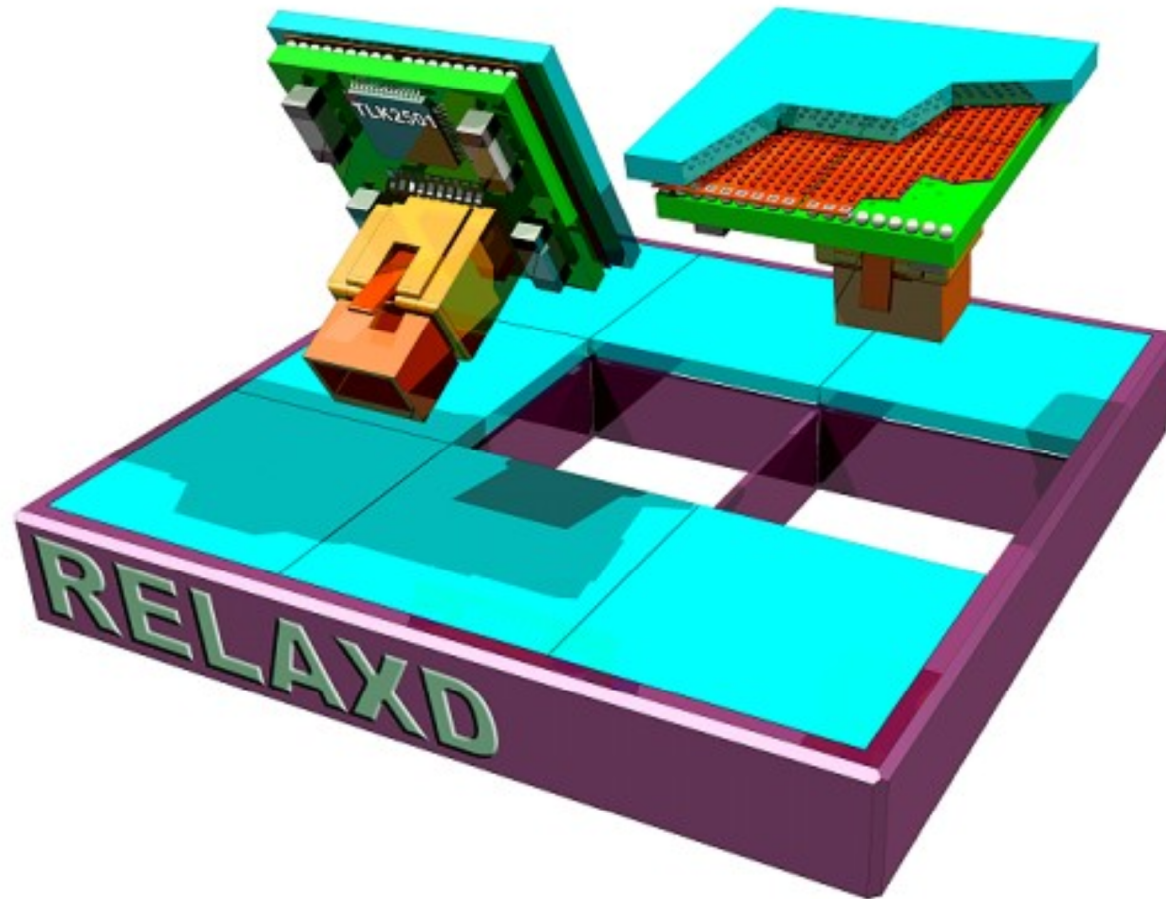
radiation tolerance of sensors and electronics

need for large area coverage, without gaps

cost is a major issue in commercial applications

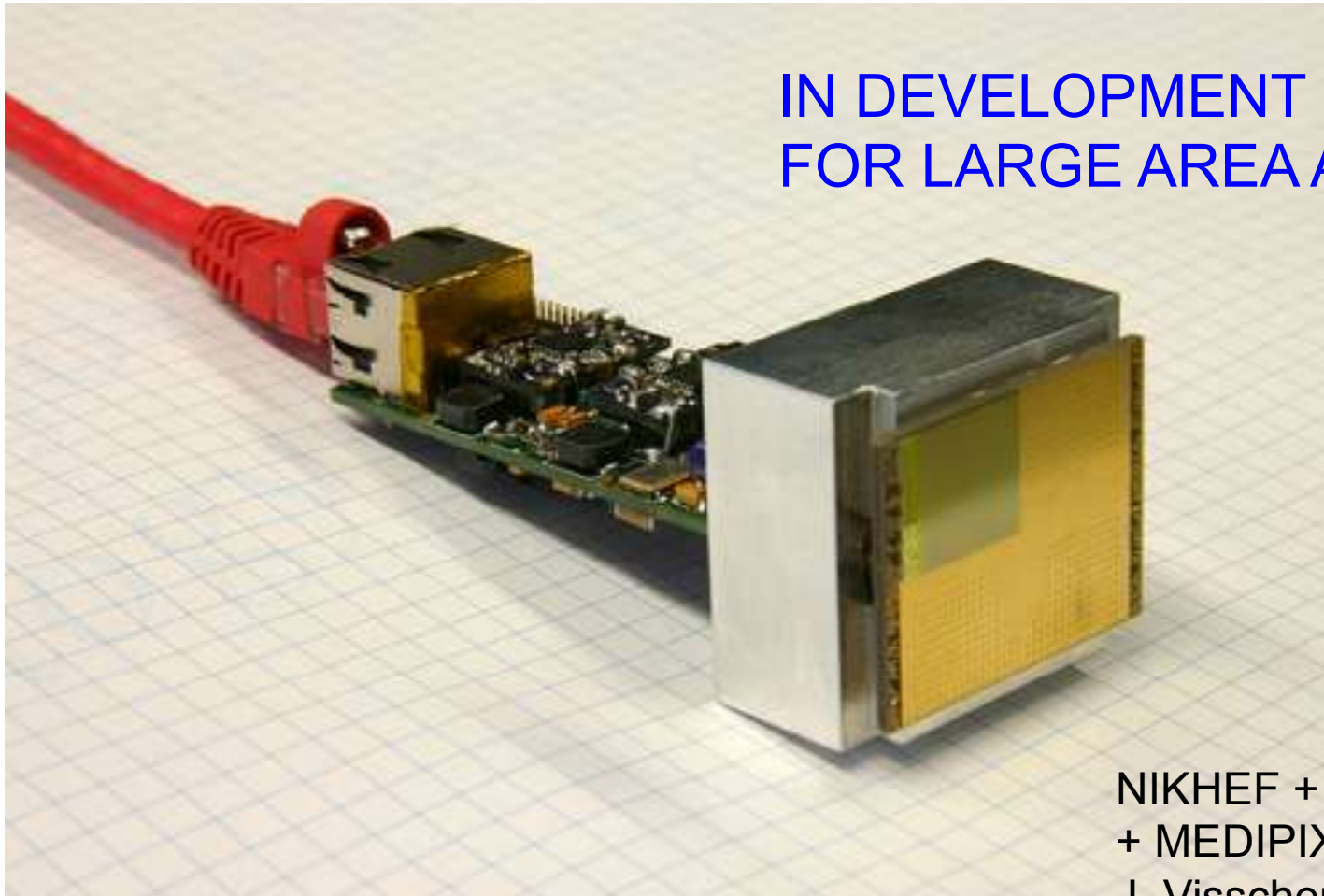


Large Area X-Ray Detector RELAXD NIKHEF



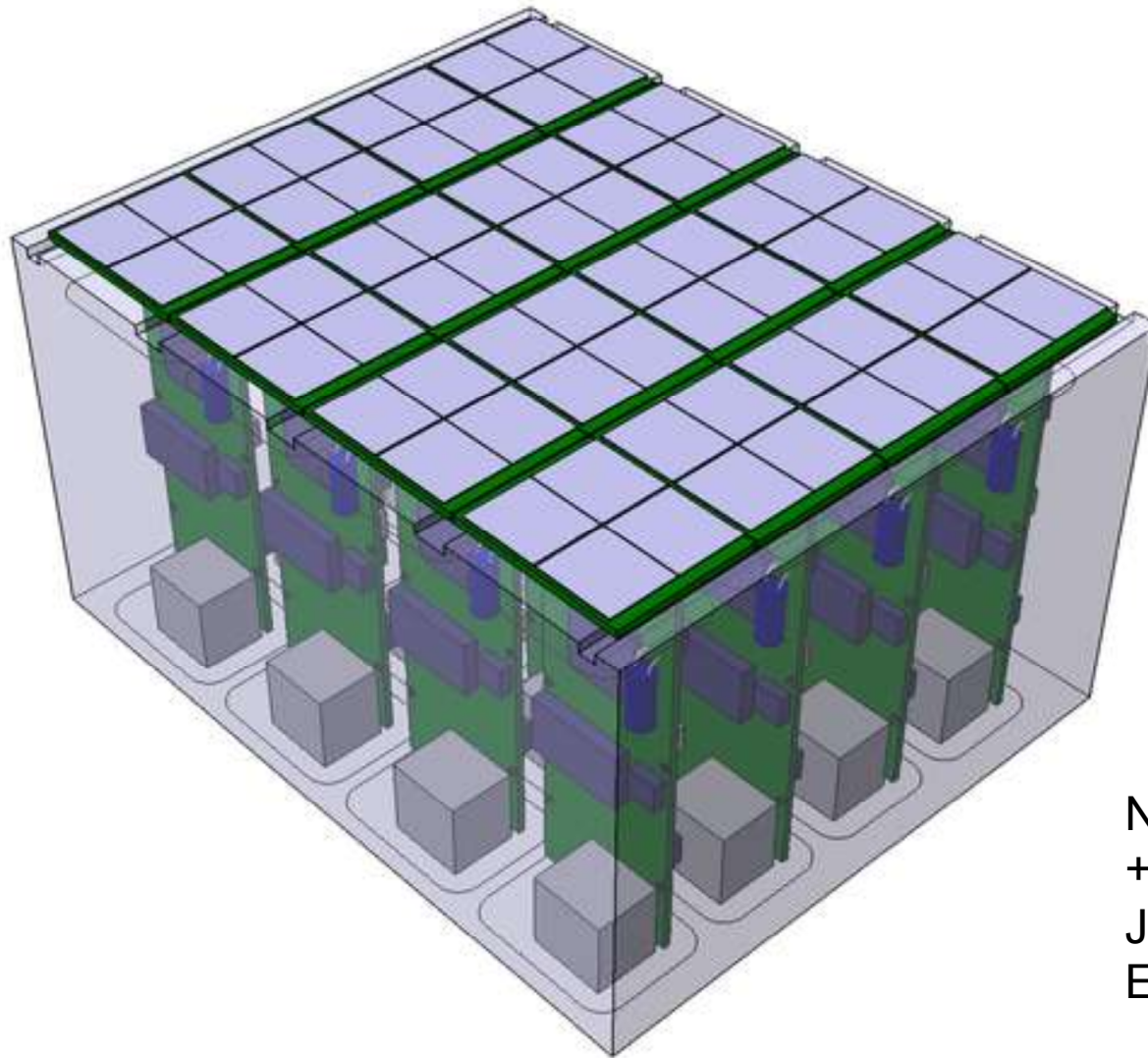
MEDIPIX UNIT "RELAXD"

IN DEVELOPMENT
FOR LARGE AREA ARRAY



NIKHEF + PANALYTICAL
+ MEDIPIX / CERN
J. Visschers, K.Bethke,
E. Heijne cs.

MEDIPIX ARRAY DESIGN

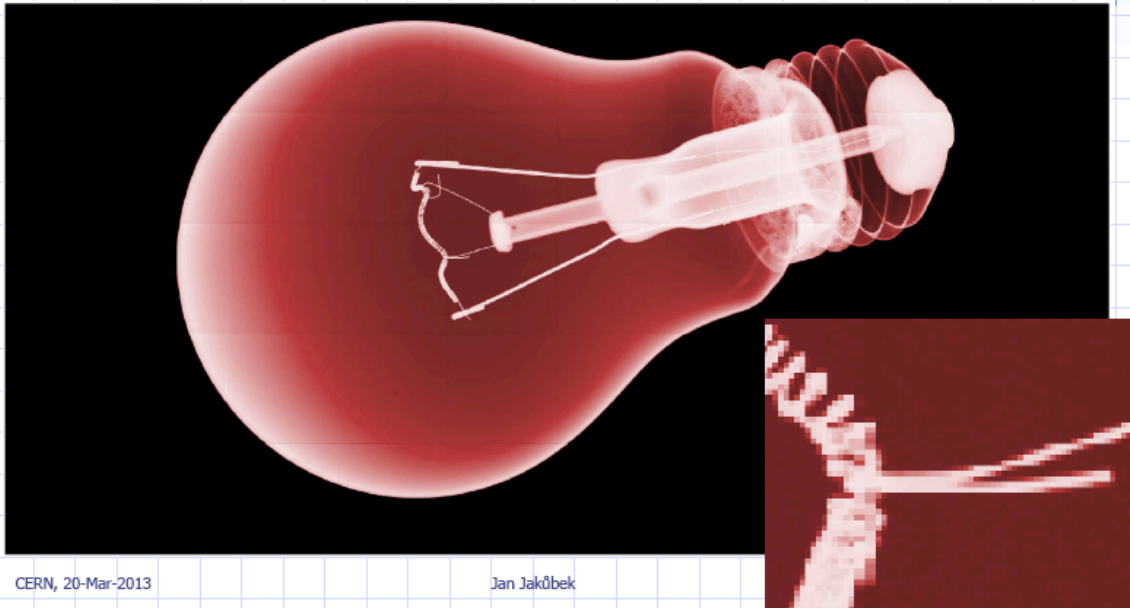


NIKHEF + PANALYTICAL
+ MEDIPIX / CERN
J. Visschers, K.Bethke,
E. Heijne cs.

A Large Area Timepix Detector

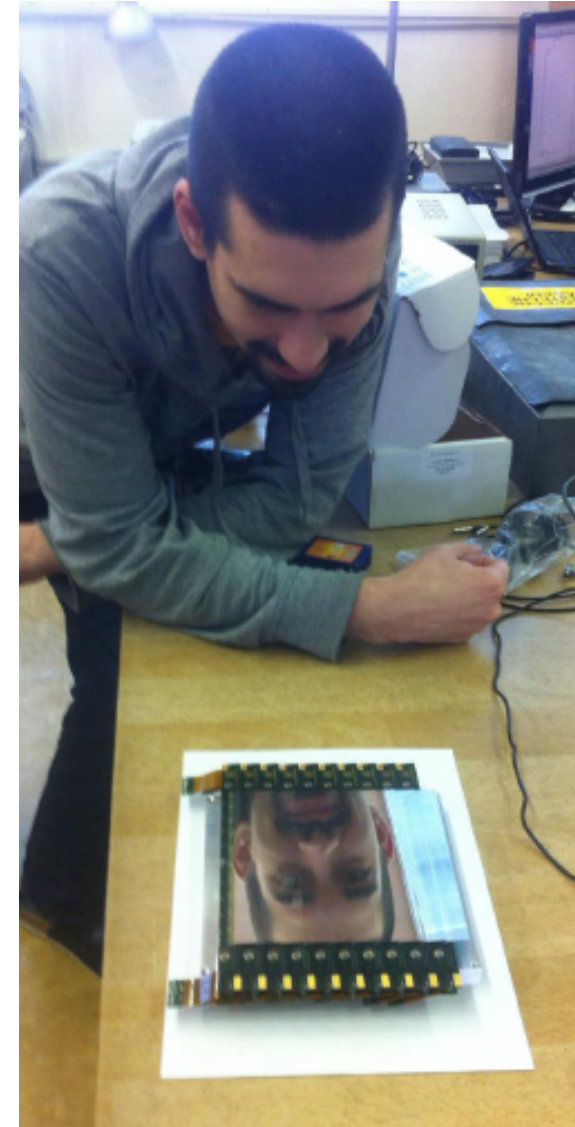
10 x 10 chip ~ 14 cm x 14 cm
using edgeless sensors
wirebonds underneath, small angles
made at Inst Exp Appl Phys IEAP Prague
Jan Jakubek & colleagues

Bulb: BH artifacts are seen (material difference + tube warming)



CERN, 20-Mar-2013

Jan Jakubek



Some Applications of Medipix/Timepix

X-ray imaging other than medical

X-ray diffraction patterns XRD

X-ray fluorescence XRF

phase contrast enhancement

environmental applications

imaging of electrons, neutrons, molecules

electron microscopy (cryogenic, ..)

LEEM

visible light via micro-channel plate (MCP)

neutron imaging (enhanced by converter materials)

dosimetry

mass spectrometry imaging

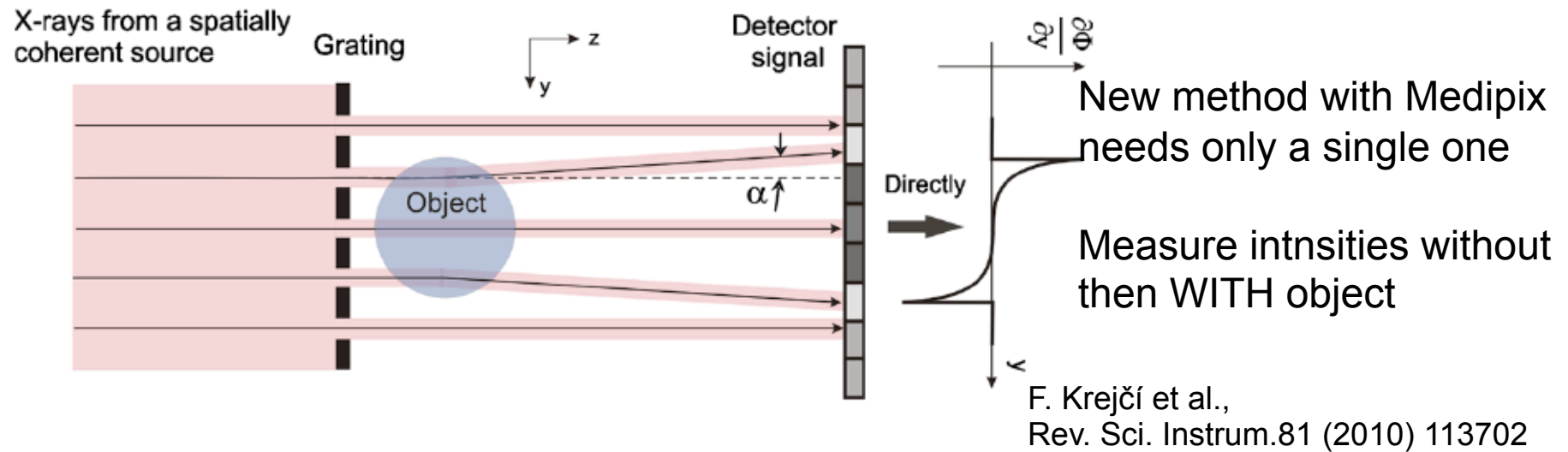
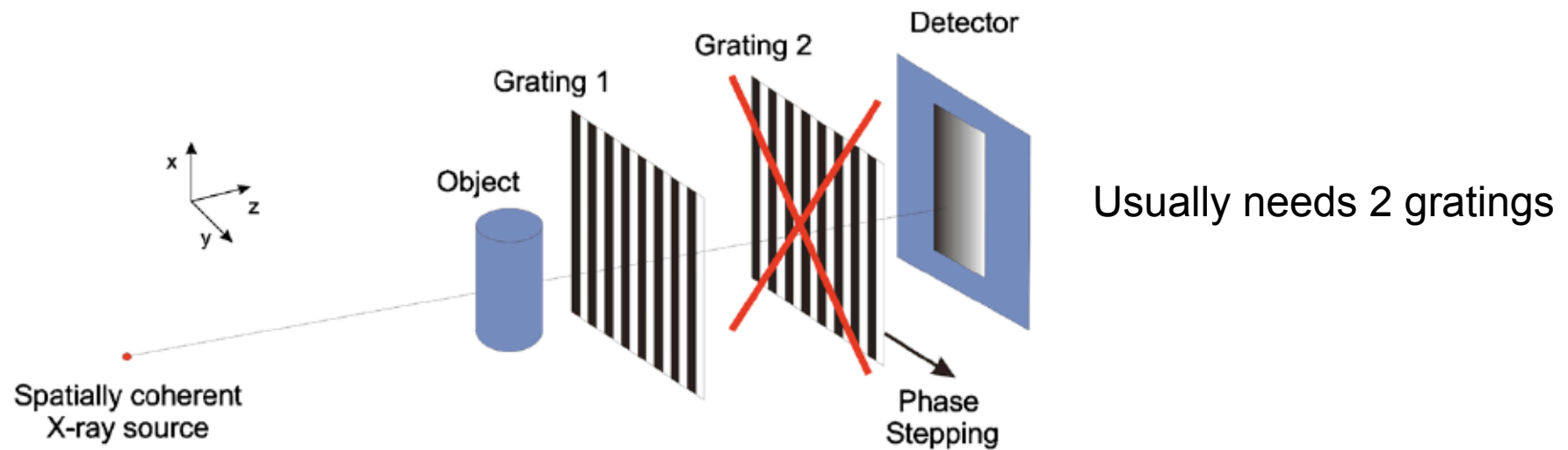
dosimetry

Timepix at International Space Station

Timepix anywhere (in school, also in LHC: ATLAS and CMS)

dedicated dosimeter chip Dosepix

Phase Contrast Imaging



Phase Contrast Imaging

Can use only one single grating, if Medipix is used as detector

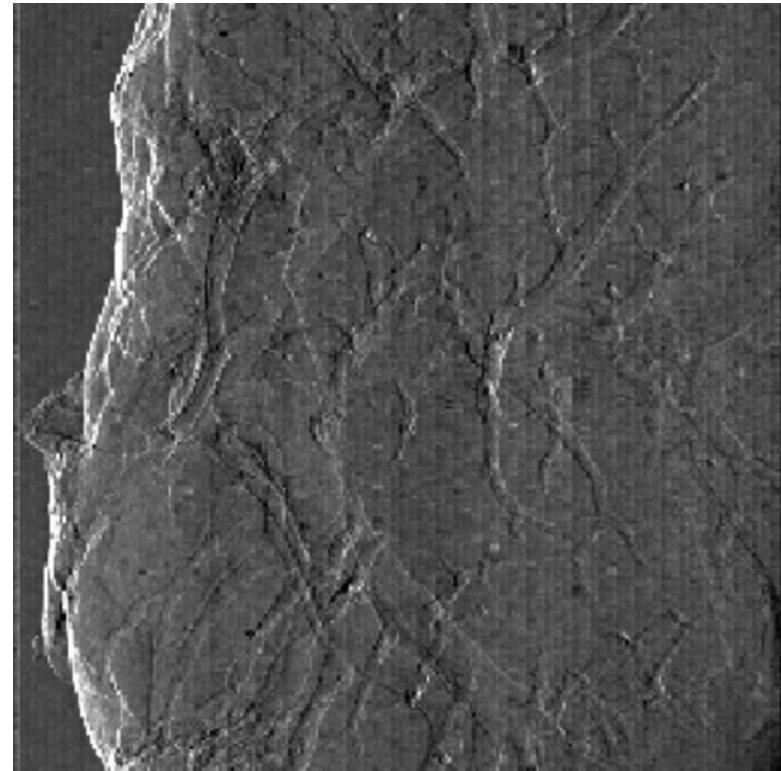
Mouse kidney:

50keV X-ray absorption



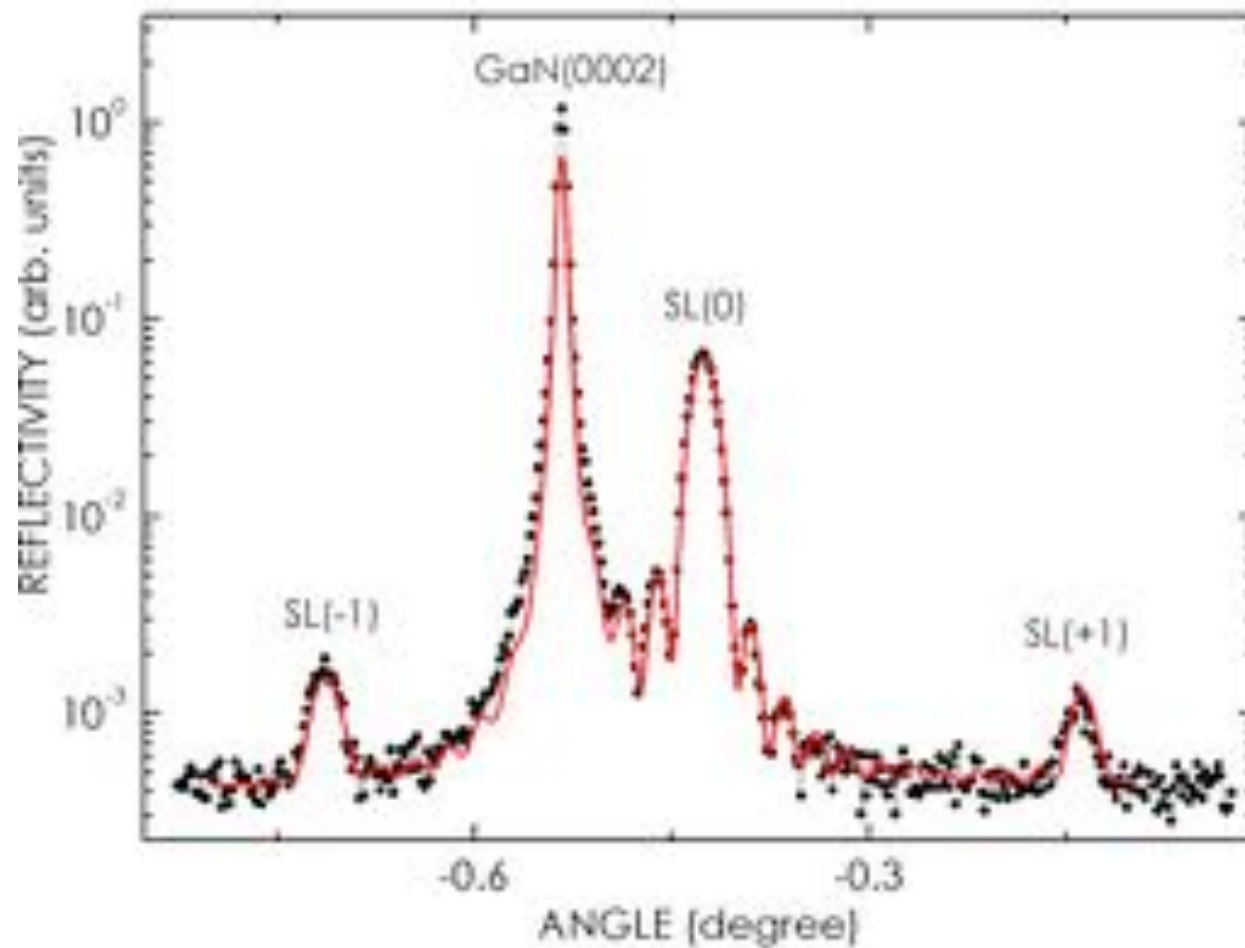
Mouse kidney:

50keV X-ray Phase Contrast



F. Krejčí, J. Jakůbek, M. Kroupa, " Hard x-ray phase contrast imaging using single absorption grating and hybrid semiconductor pixel detector", Rev. Sci. Instrum. 81 (2010) 113702

X-ray Diffraction for Materials Analysis



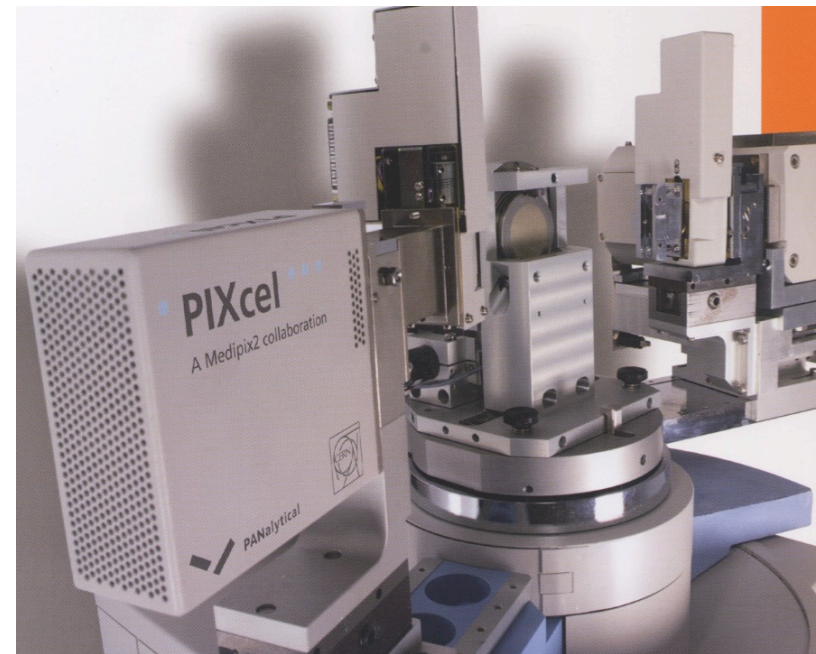
PIXCEL detector for X-RAY DIFFRACTION

Replaces Si microstrip detector in
their analyzer

SPIN-OFF to
PANALYTICAL
Almelo, NL

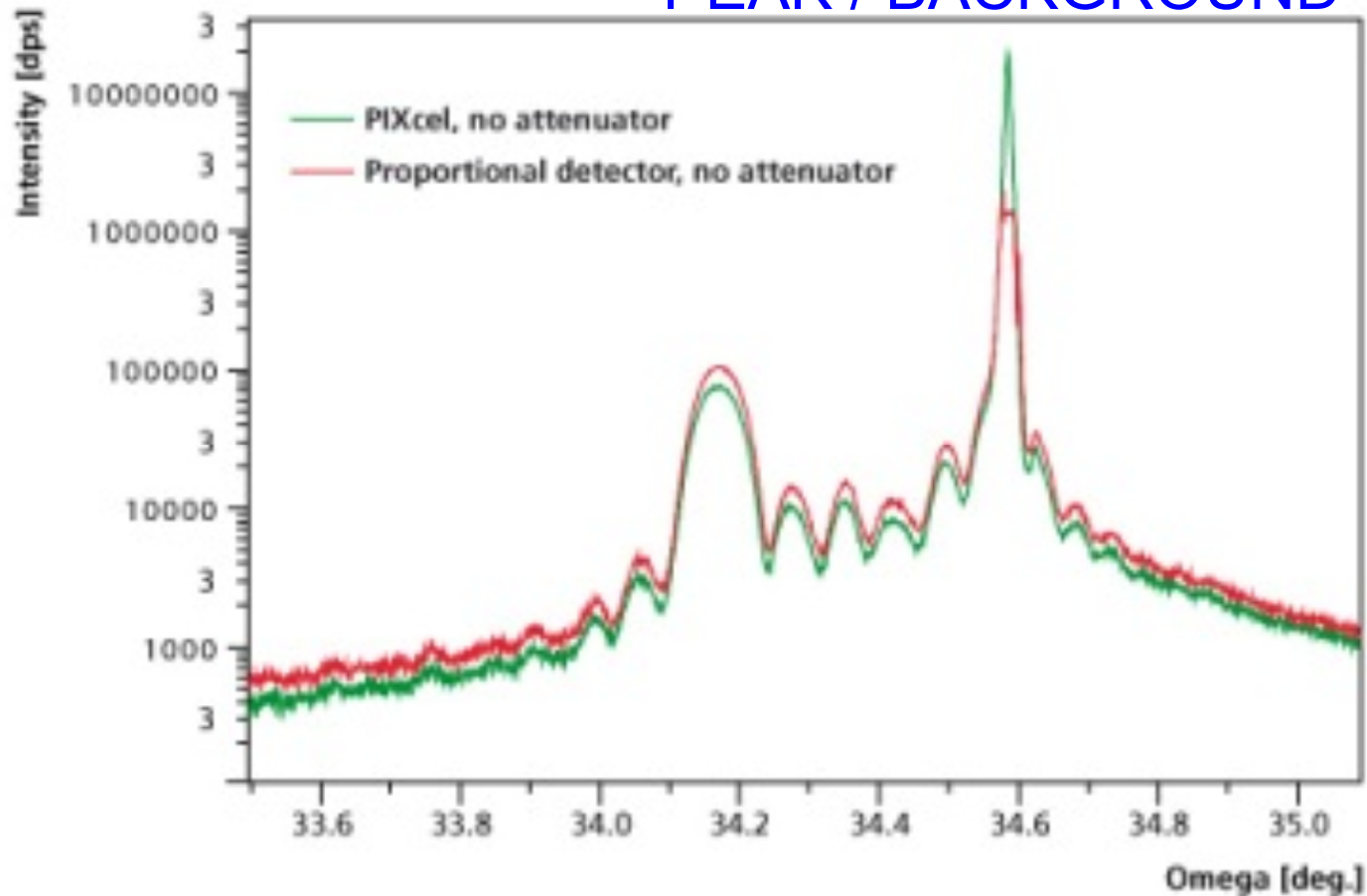


<http://www.panalytical.com/XPert-Powder/>



PANALYTICAL X-RAY DIFFRACTION

Improvement in ratio
PEAK / BACKGROUND



ALMELO, NL



Erik HEIJNE IEAP/CTU & NIKHEF & CERN PH Department

13 July 2013

99



Environmental Imaging

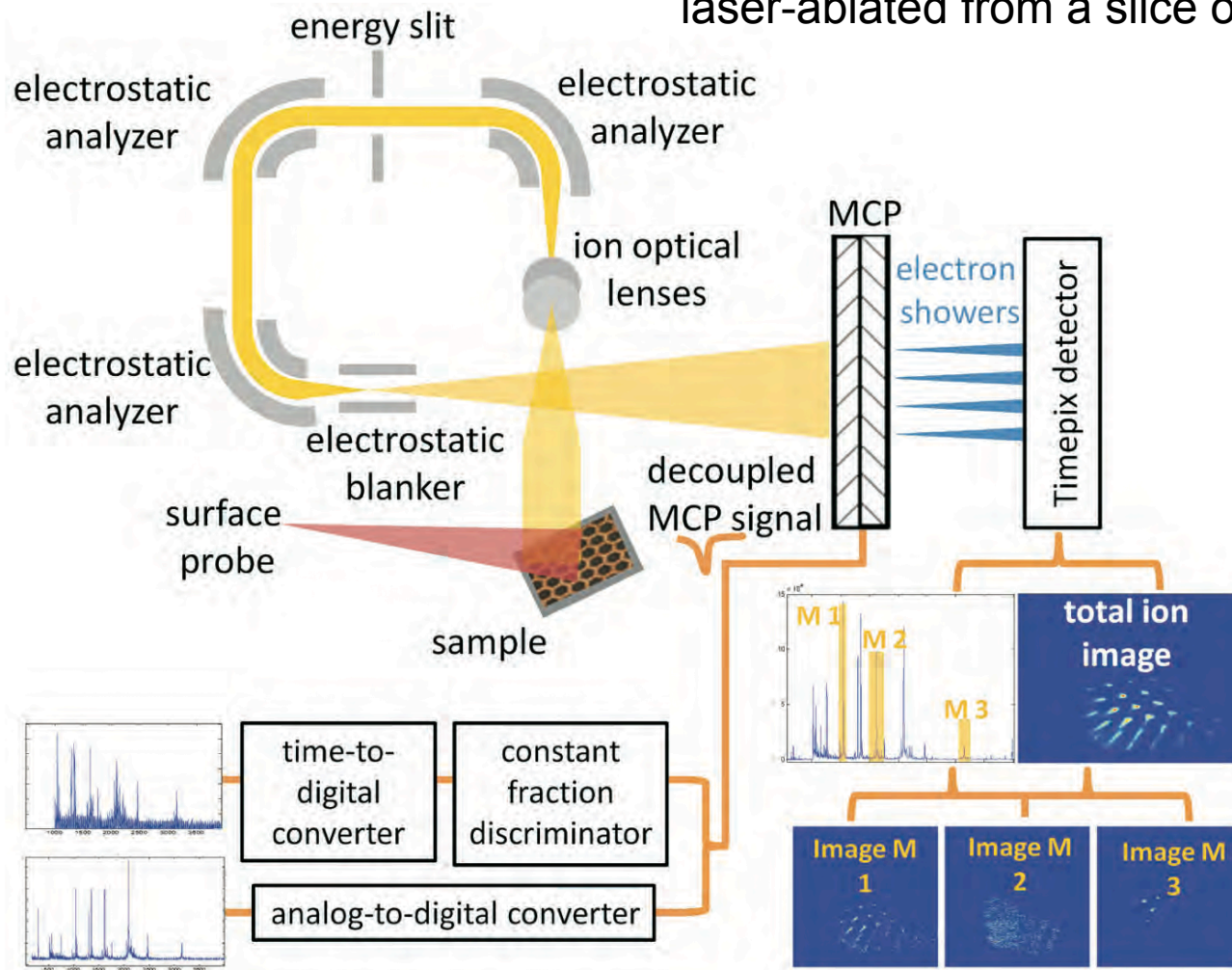


Medipix Image
superposed on
photograph of
container with
radio-waste

CEA-LIST
Paris

Mass Spectrometry Imaging

Analysis of spatial distribution and types of molecules
laser-ablated from a slice of some object



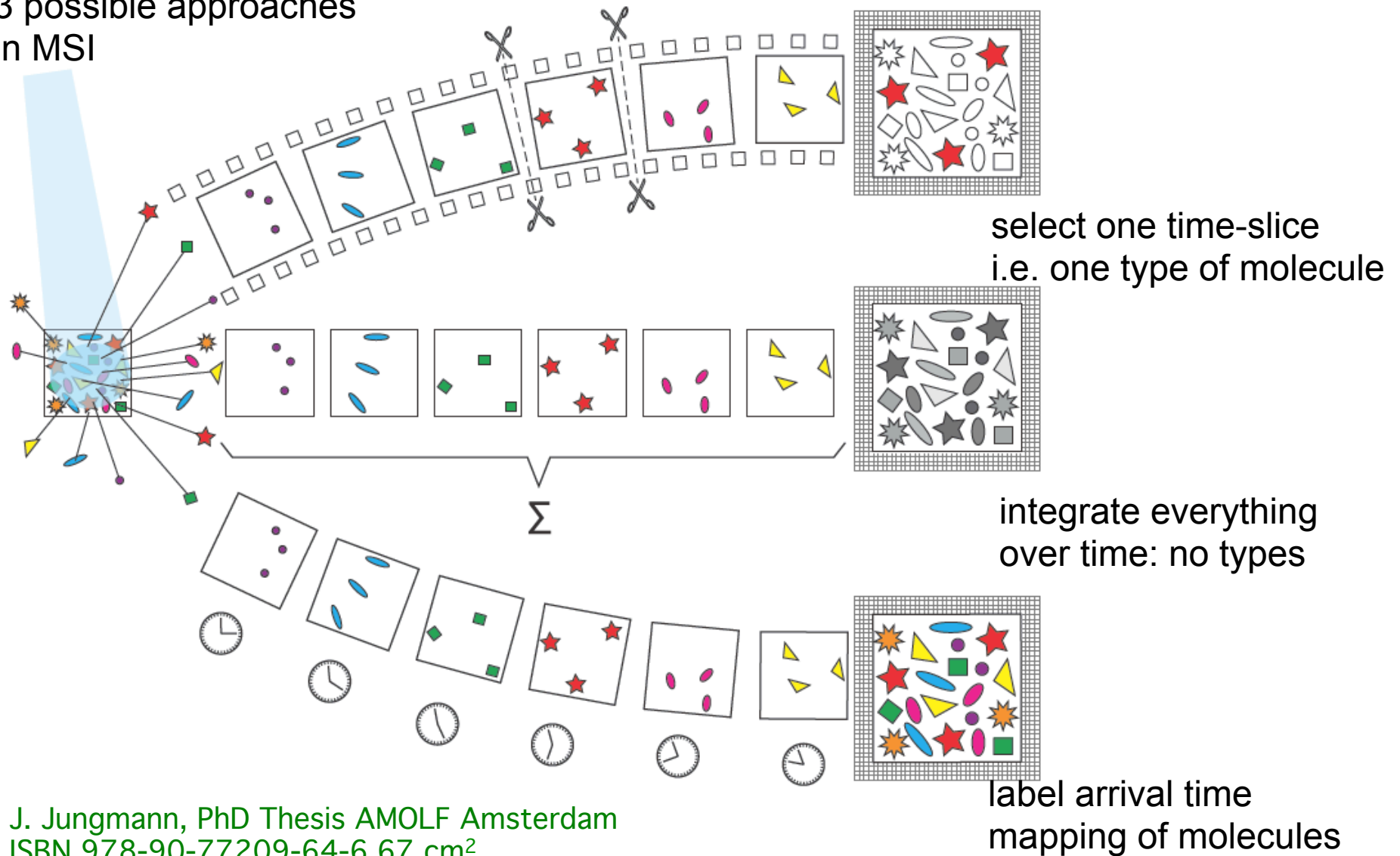
The masses are analyzed
by their speed:
time of arrival
identifies the molecules

With very low speed/energy
there is no penetration
and chevron MCP is used
to generate electron signal

J. Jungmann, PhD Thesis AMOLF Amsterdam
ISBN 978-90-77209-64-6.67 cm²

Mass Spectrometry Imaging

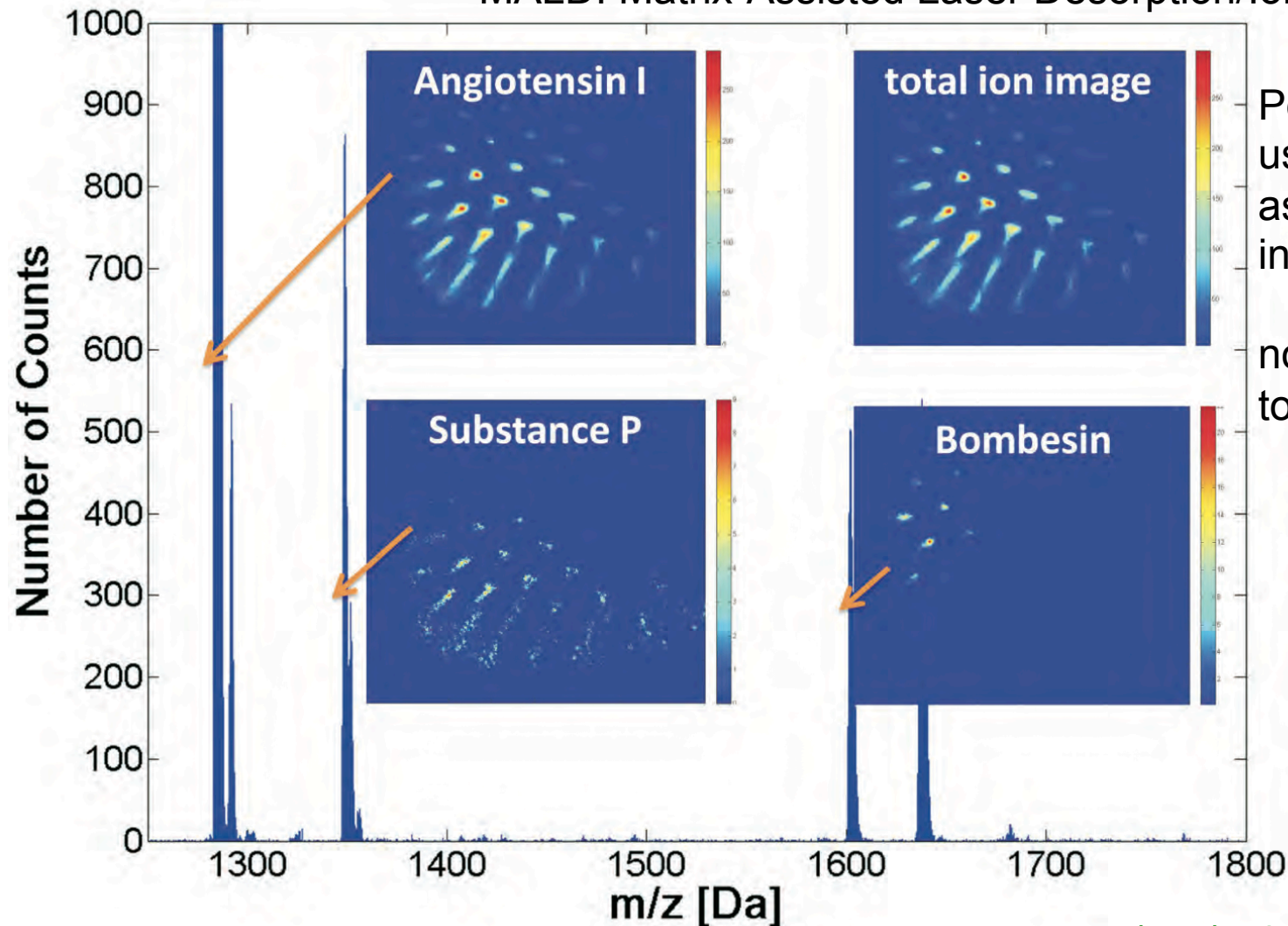
3 possible approaches
in MSI



J. Jungmann, PhD Thesis AMOLF Amsterdam
ISBN 978-90-77209-64-6.67 cm²

Mass Spectrometry Imaging

MALDI Matrix-Assisted Laser Desorption/Ionization

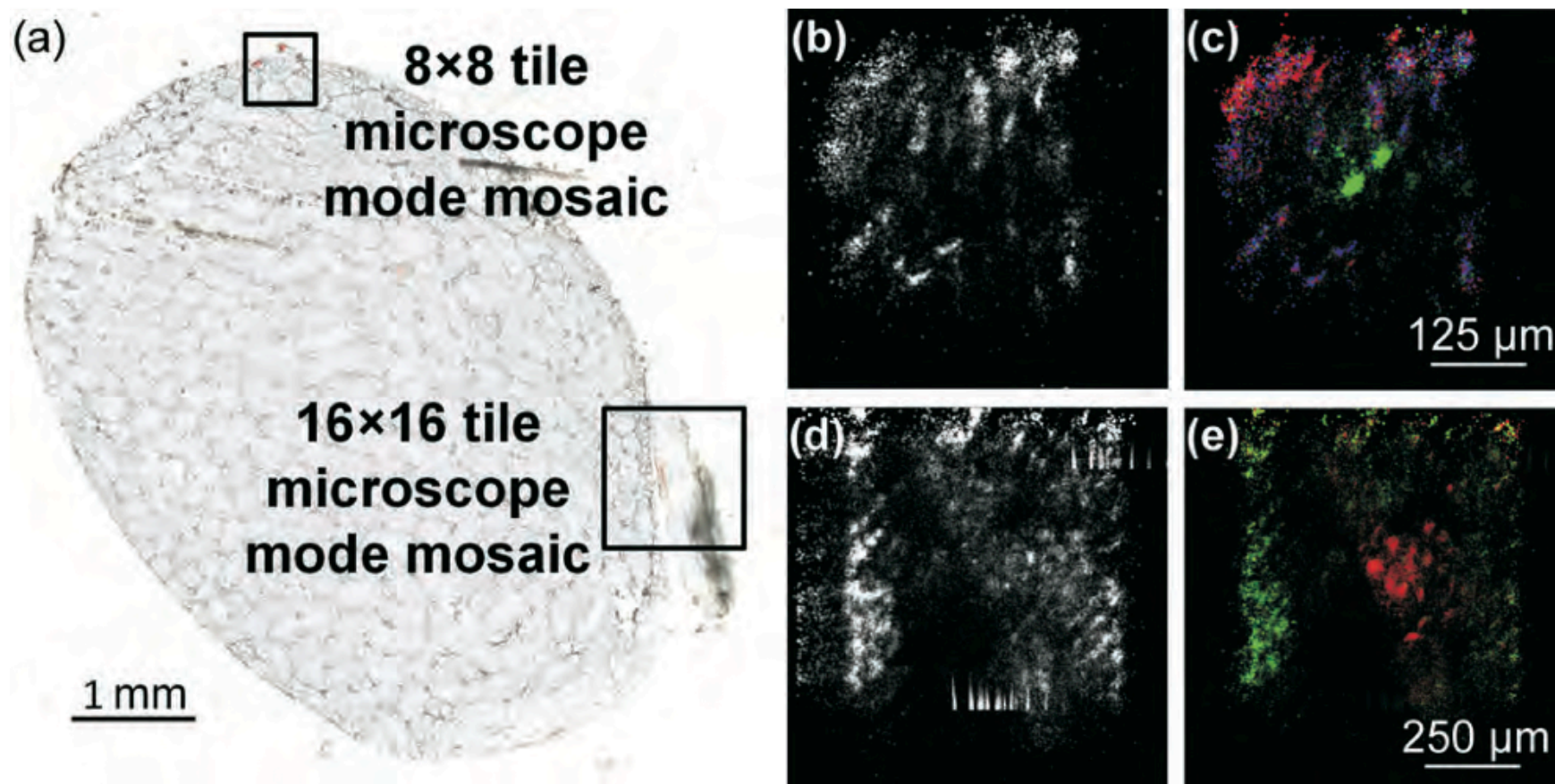


Peptide measured using Timepix as imaging device in a single pass

no blanker needed to select a molecule

J. Jungmann, PhD Thesis AMOLF Amsterdam
ISBN 978-90-77209-64-6.67 cm²

Mass Spectrometry Imaging

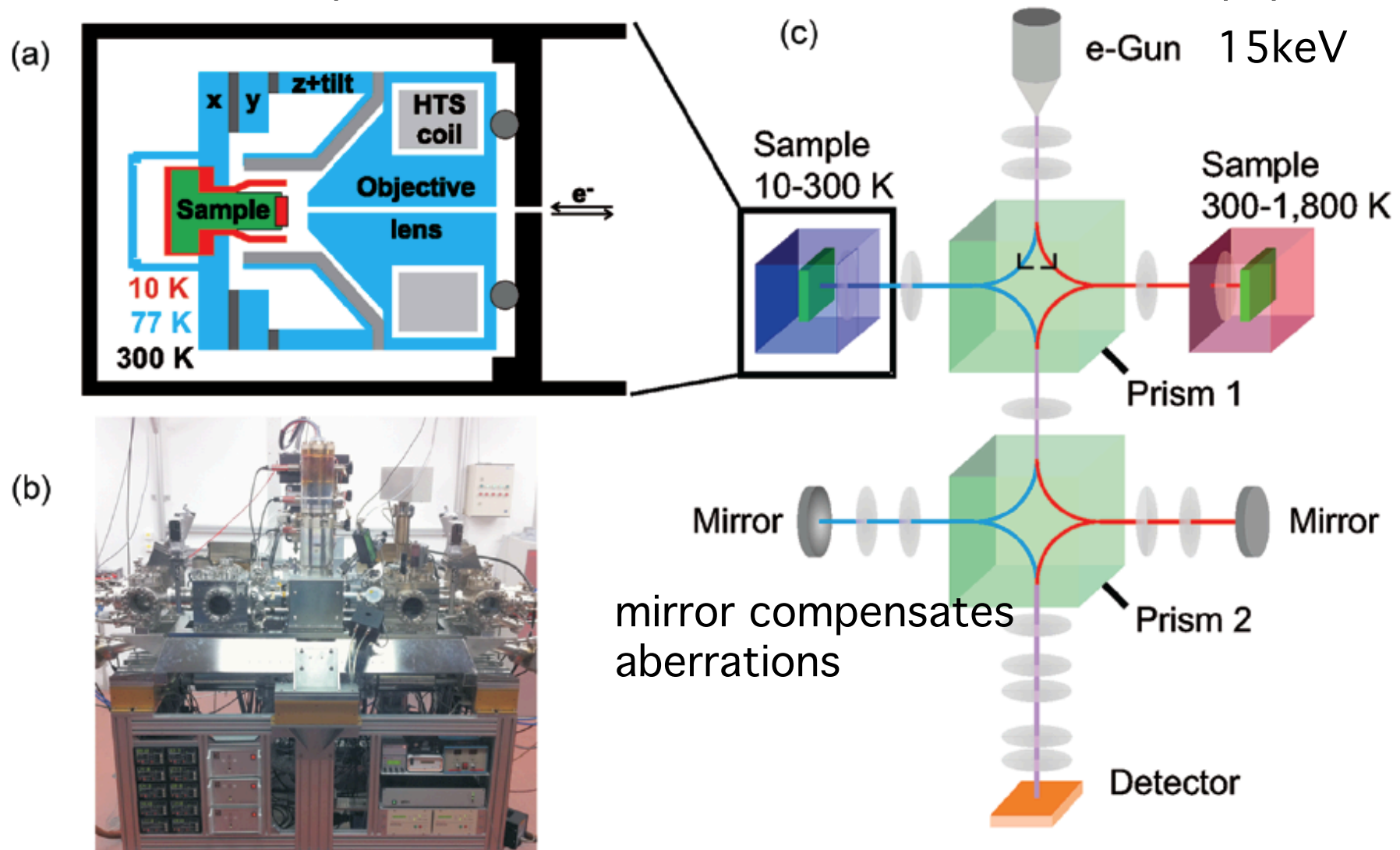


J. Jungmann, PhD Thesis AMOLF Amsterdam
ISBN 978-90-77209-64-6.67 cm²

Low Energy Electron Microscopy LEEM

also Photo Emission Electron Microscopy PEEM

'Escher' set-up Leiden from IBM J Res&DEv 55-5(2011) paper 1



Low Energy Electron Microscopy LEEM

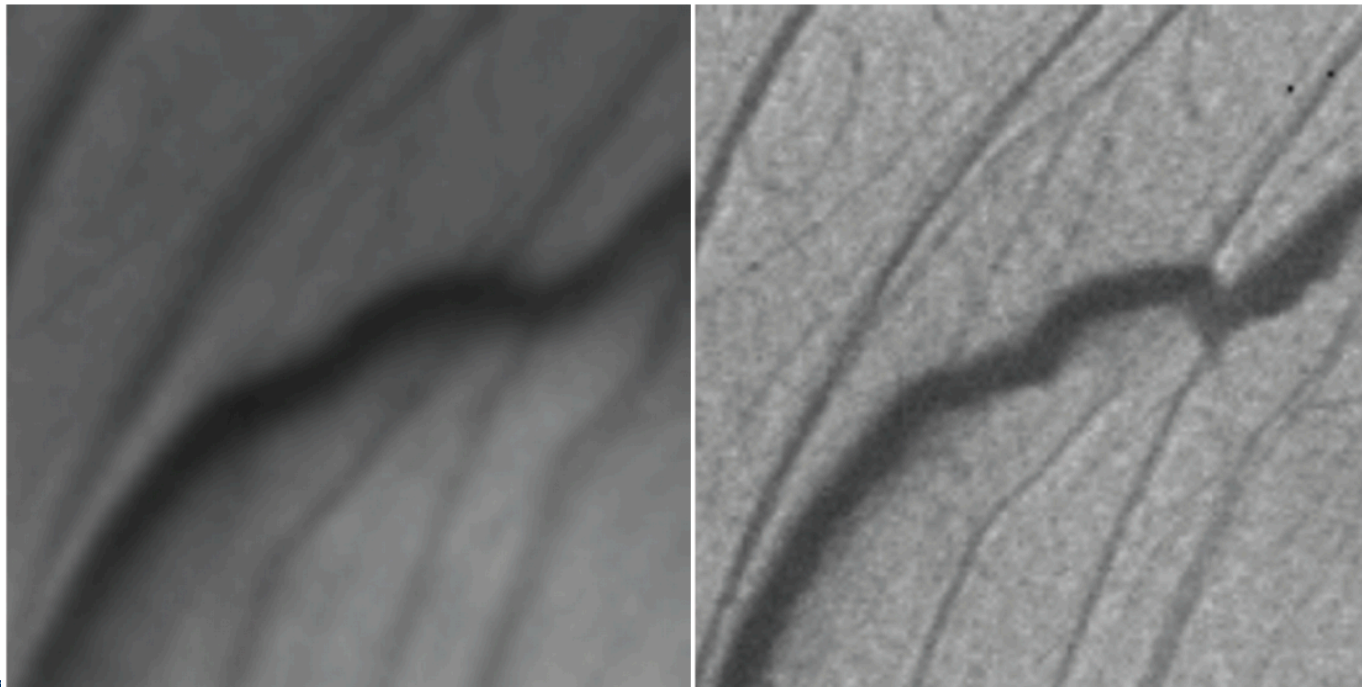
15keV electrons are decelerated to a 0-100 eV

before they reach the sample.

They reflect from the sample, and are re-accelerated to 15keV,
and directed to the imaging detector.

Using magnification and sophisticated compensation

by a segmented mirror, one can achieve a resolution of a few nm
i.e. $1\mu\text{m} = 1000$ pixels



(a)

(b)

graphene flakes
on Ir <111> surface
 $1.5\mu\text{m} \times 1.5\mu\text{m}$

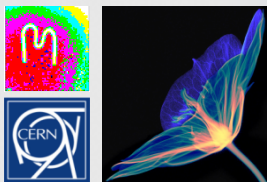
a) standard MCP+
CCD-based imager

b) with Medipix
256x256 imager

2x improvement

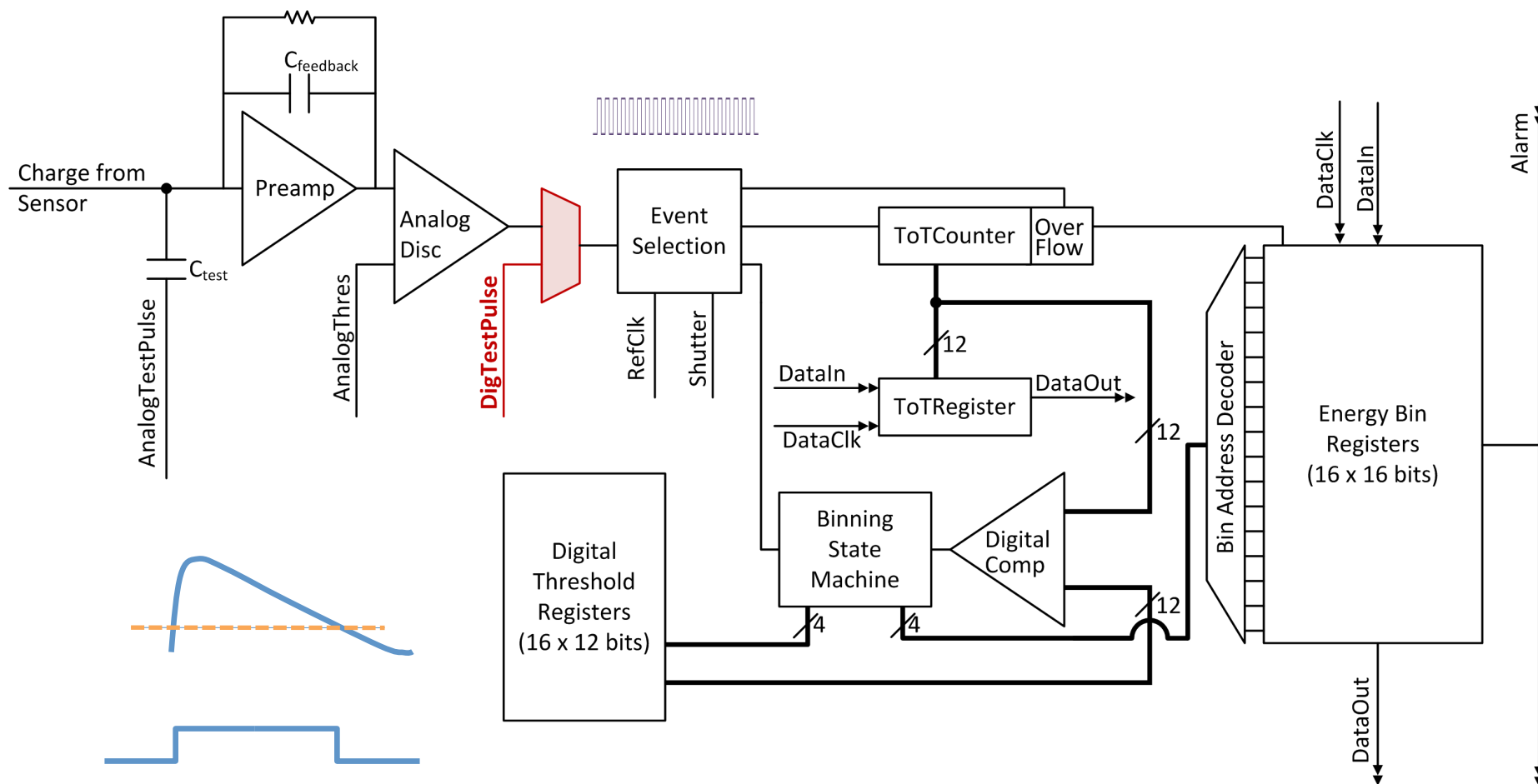
Designed chips

Medipix1 (1998)	1 μ m SACMOS, 64x64 pixels, 170x170 μ m ² PC / Frame based readout
Medipix2 (2001)	0.25 μ m CMOS, 256x256 pixels, 55x55 μ m ² PC / Frame based readout
Timepix (2006)	0.25 μ m CMOS, 256x256 pixels, 55x55 μ m ² PC, ToT, ToA / Frame based readout
Medipix3 (2009)	0.13 μ m CMOS, 256x256 pixels, 55x55 μ m ² PC / Frame based readout Event by event charge reconstruction and allocation
Dosepix (2011)	0.13 μ m CMOS, 16x16 pixels, 220x220 μ m ² ToT, PC / Rolling shutter (programmable column readout) Event by event binning of energy spectra (16 digital thrs)
Timepix3 (2013)	0.13 μ m CMOS, 256x256 pixels, 55x55 μ m ² PC; ToT, ToA (simultaneous)/ Data driven readout
Smallpix	0.13 μ m CMOS, 512x512 pixels, 40x40 μ m ² (TBD) PC, iToT; ToA, ToT1 (simultaneous)/ Frame based (ZC) TSV compatible design
Clickpix prototype	65nm CMOS, 64x64 pixels, 25x25 μ m ² ToA, ToT1 (simultaneous)/ Frame based (ZC)

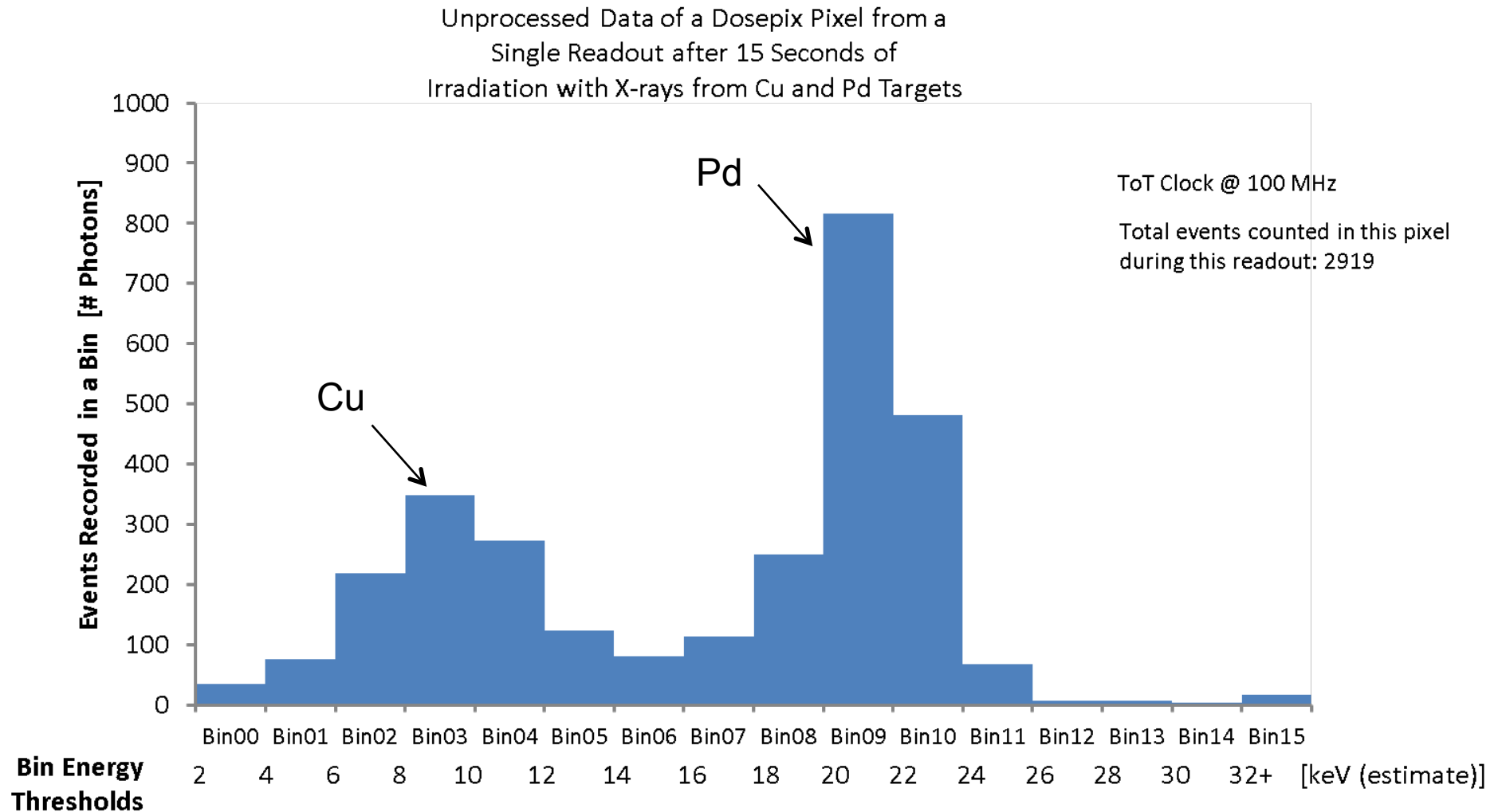


'Dosepix' schematic circuit diagram

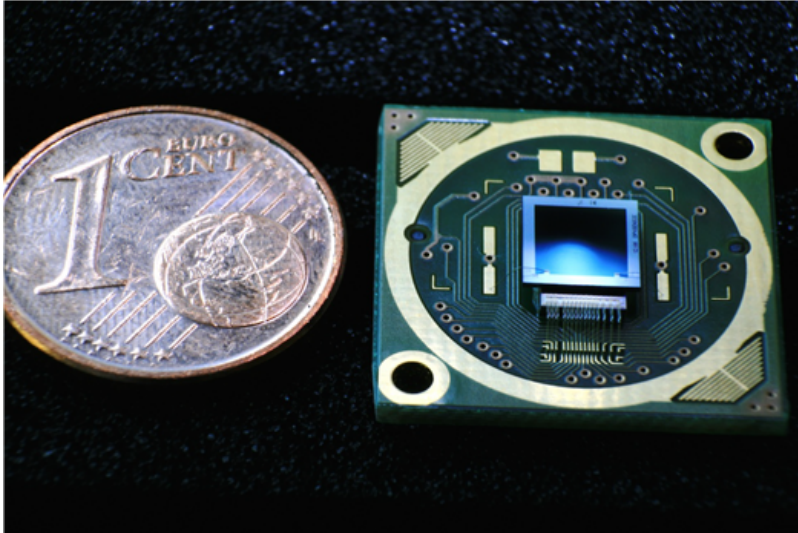
Dosepix
slide from W.
Wong



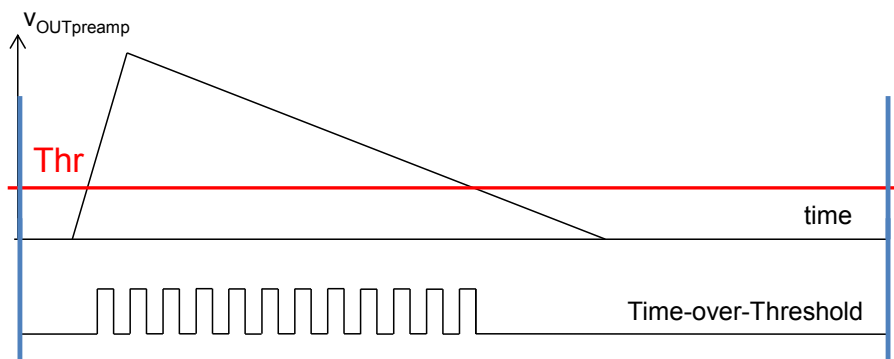
Dosepix single acquisition unprocessed data



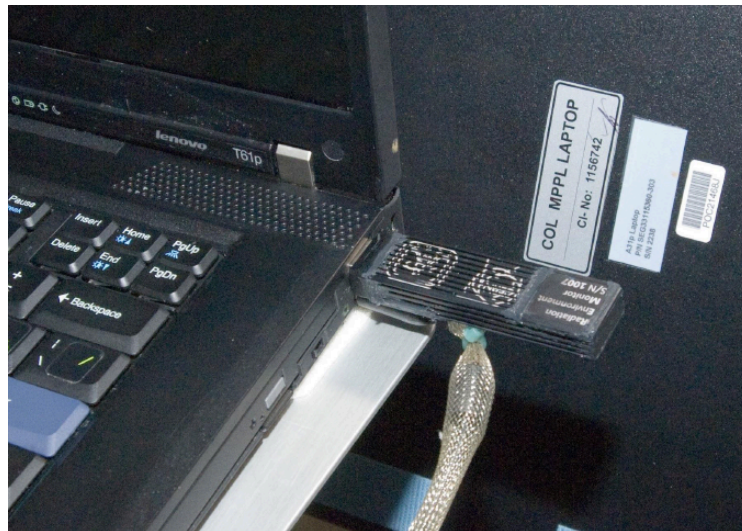
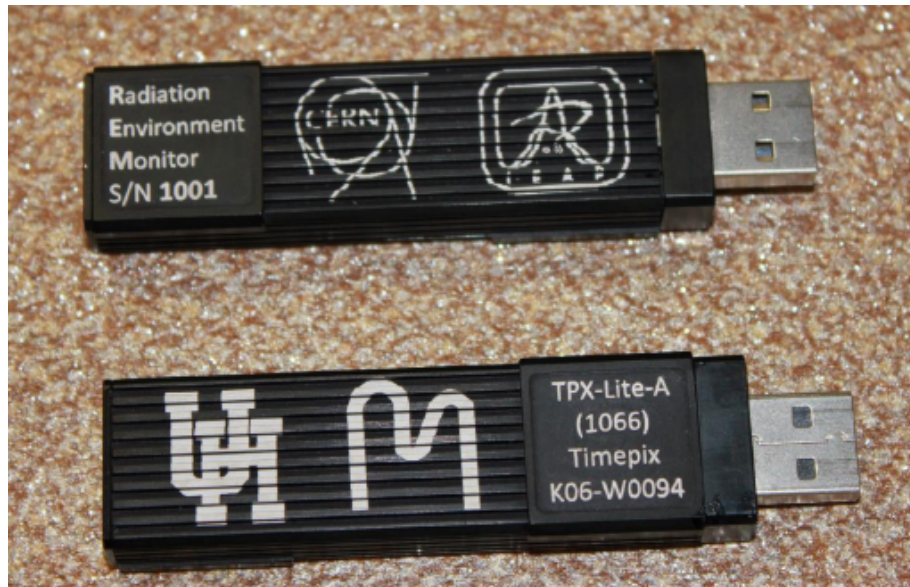
Dosepix



- Developed in the framework of the Medipix2 collaboration
- Main application: dosimetry
- 16x16 pixel matrix, $220 \times 220 \mu\text{m}^2$ pixels
- CMOS $0.13 \mu\text{m}$ technology
- 15mW full chip consumption
- 1 global analog threshold
- Operation Modes:
 - Energy binning mode
 - 12 bit ToT measurement @100MHz
 - 16 digital thresholds for event-by-event energy binning
 - 16x16bit counters
 - Photon counting mode (8 bits)
 - Integral ToT (24 bits)

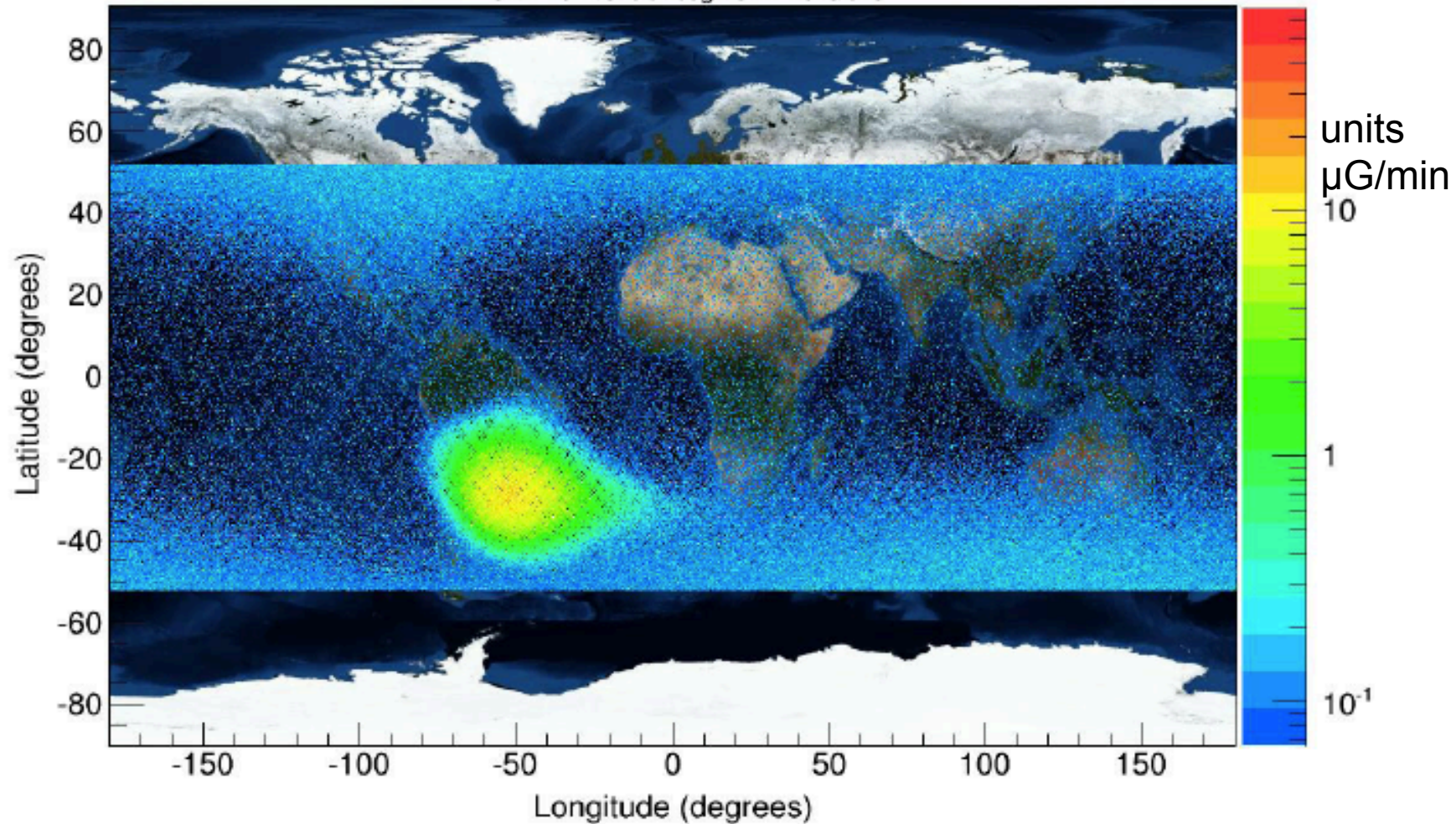


Dosimetry at the Int Space Station ISS

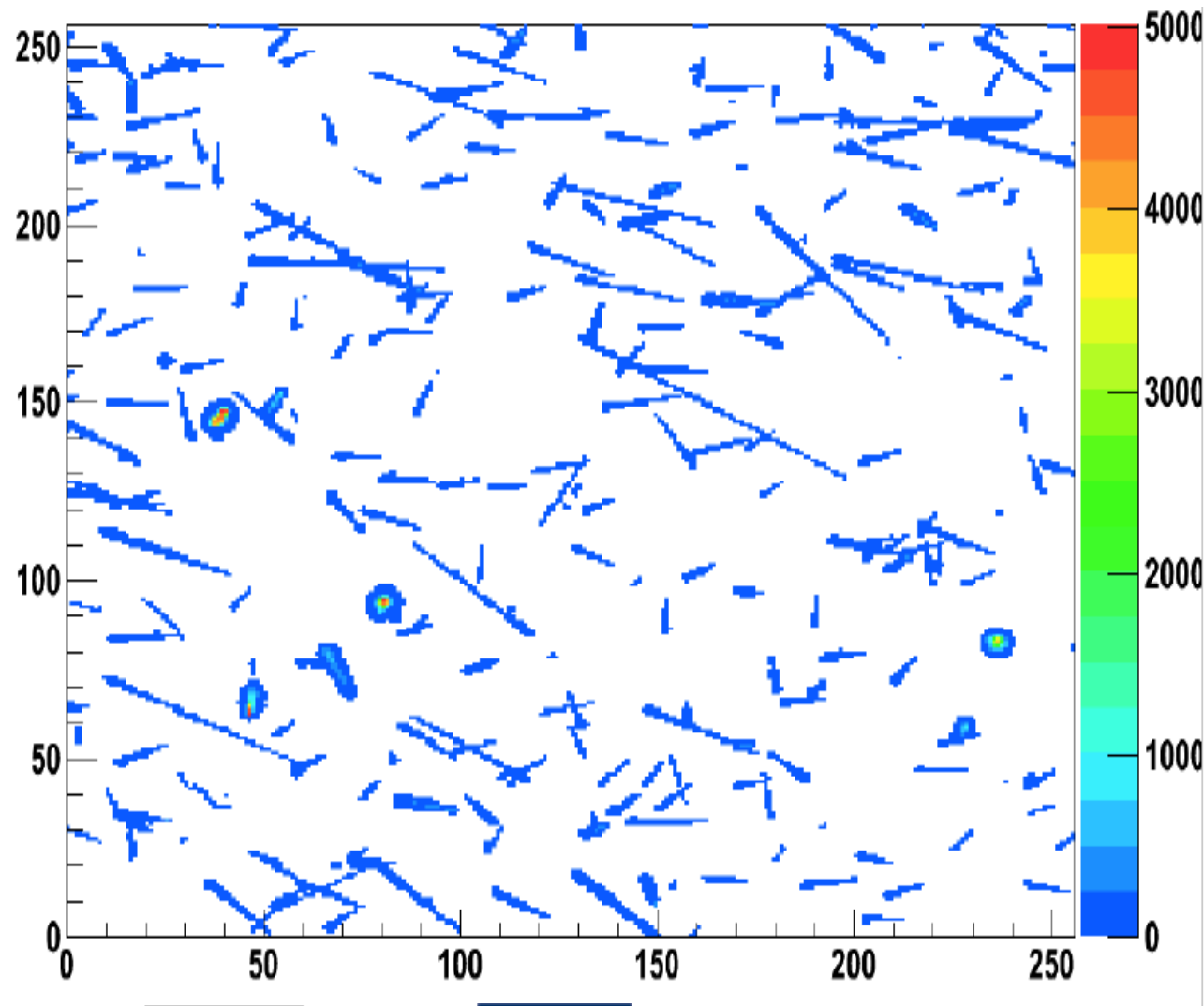


Dosimetry at the Int Space Station ISS

REM Orbital Dose Rate Map ($\mu\text{Gy}/\text{min}$)
D03-W0094 (S/N 1007)
GMT 2012/320 through GMT 2013/045

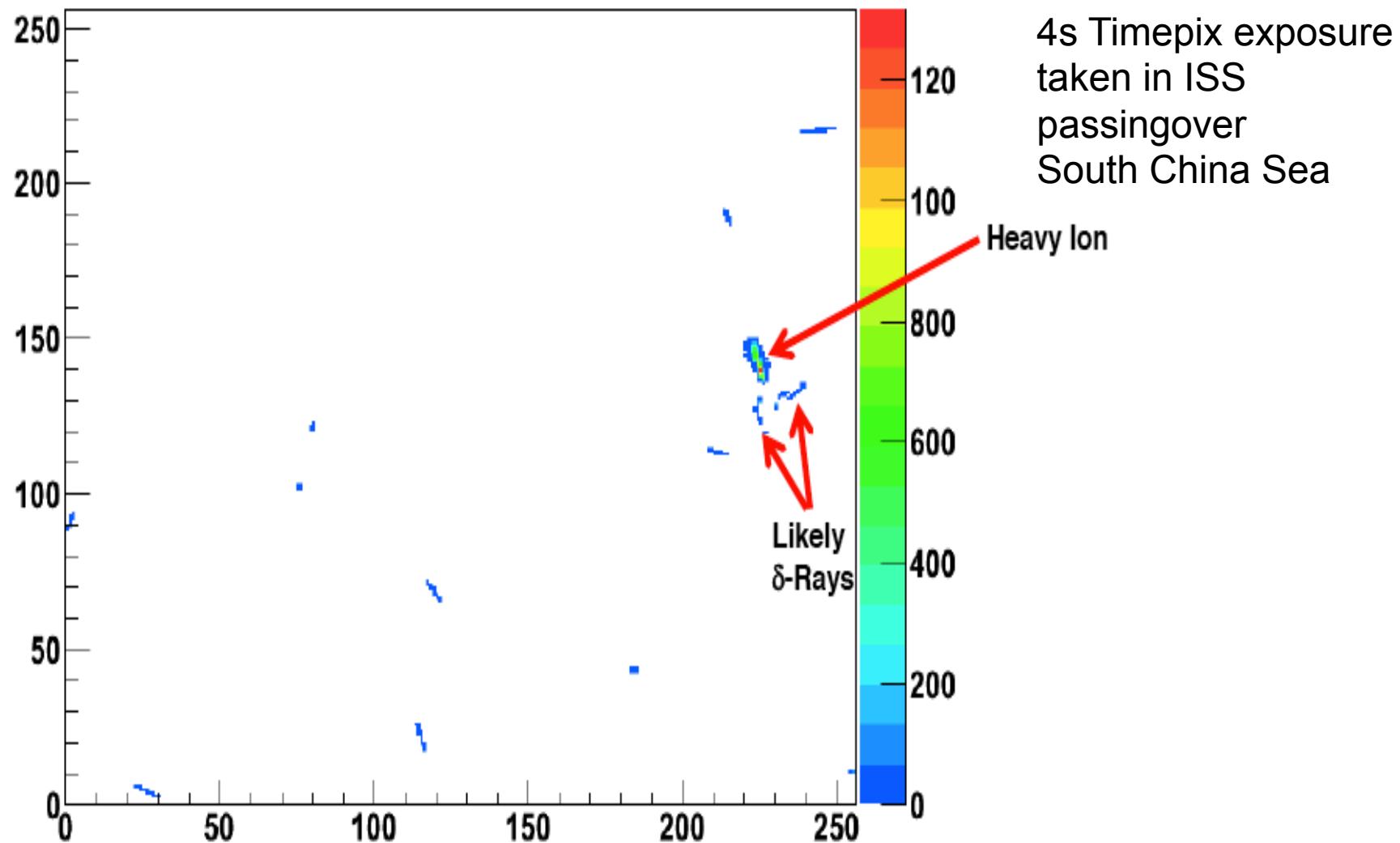


Dosimetry at the Int Space Station ISS



4s Timepix exposure
taken in ISS
passing through SAA
South America Anomaly

Dosimetry at the Int Space Station ISS



SOME CONCLUSIONS

DETECTION  IMAGING TECHNOLOGY


NEED FAST, CONTINUOUS FRAMES

already ~kHz

POTENTIAL for SPECTROSCOPY in IMAGE: MPX3

INTRODUCTION ASICS  NEW DEVICES

MULTIPLE PARTNERS in MEDIPIX2/3

MANY IDEAS PURSUED  MANY RESULTS

JUSTIFIES INVESTMENT in CHIP DESIGN

END

